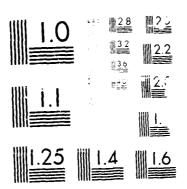
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# NAVAL POSTGRADUATE SCHOOL

Monterey, California



# **THESIS**

NATURAL CONVECTION COOLING OF A 3 BY 3
ARRAY OF RECTANGULAR PROTRUSIONS IN AN
ENCLOSURE FILLED WITH DIELECTRIC LIQUID:
EFFECTS OF BOUNDARY CONDITIONS
AND COMPONENT ORIENTATION

by

Edgardo I. Torres

December 1988

Thesis Advisor:

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# Natural Convection Cooling of a 3 by 3 Array of Rectangular Protrusions in an Enclosure Filled with Dielectric Liquid: Effects of Boundary Conditions and Component Orientation

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Edgardo I. Torres LT. Columbian Navy B.S., Columbian Naval Academy, 1986

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#### **ABSTRACT**

An experimental investigation of natural convection immersion cooling of two configurations of discrete heat sources in an enclosure filled with Fluorinert FC-75 has been conducted. A three by three array of rectangular protrusions was employed.

In the first study, using the same equipment set-up of Benedict [Ref. 13], the influence of changing the enclosure bottom surface boundary condition on flow patterns and heat transfer characteristics was examined. Both insulated and uniform temperature boundary conditions were considered.

In the second set of experiments, a new chamber with the protrusions oriented vertically was assembled and effects of component orientation on the heat transfer characteristics were examined. In addition, timewise variations of temperature in several locations were measured and interpreted at different power levels.

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# TABLE OF SYMBOLS AND ABBREVIATIONS

Symbol	Description	Units
A	Area	$m^2$
α	Thermal diffusivity	m²/sec
β	Volumetric expansion coefficient	1/K
$c_p$	Specific heat	J/kg-°C
emf	Thermocouple voltage	volt
g	Acceleration of gravity	m/sec <sup>2</sup>
Gr	Grashof number	Dimensionless
h	Heat transfer coefficient	$W/m^2$ -°C
k	Thermal conductivity	W/m-°C
L	Characteristic length	m
Ll	Component length in the vertical direction	m
L2	Summation of the ratios of the component fluid exposed areas to their perimeters	m
Nu	Nusselt number	Dimensionless
Nu l	Nusselt number with length scale L1	Dimensionless
Nu2	Nusselt number with length scale L2	Dimensionless
ν	Kinematic viscosity	m²/sec
ω	Uncertainty in the variables	Various

Power	Power dissipated by the heaters	W
Pr	Prandtl number	Dimensionless
Qconv	Energy added to the fluid	W
Qin	Energy input to the heaters	W
$Q_{loss}$	Energy loss by conduction	W
$Q_{ m net}$	Net power dissipated by the heater	W
$R_{c}$	Total thermal resistance	°C\W.
$R_p$	Resistance of the precision resistor	ohms
Raf	Flux-based Rayleigh number	Dimensionless
Rat	Temperature-based Rayleigh number	Dimensionless
D	Density	kg/m <sup>3</sup>
Tavg	Average of component temperature	°C
$T_{b}$	Back surface temperature of board	<sup>c</sup> C
$T_{\rm C}$	Average heat exchanger temperature	°C
$T_f$	Average film temperature	°C
$T_s$	Back surface temperature of the	
	component	°C
$T_{sink}$	Average temperature of the heat	20
	exchangers	°C
$V_h$	Voltage Across the Heaters	Volts
$V_{in}$	Input voltage	Volts
w	Chamber width	m
W	Unit of power	W

#### I. INTRODUCTION

### A. STATEMENT OF THE PROBLEM

With the increase in circuit packaging density associated with the miniaturization of microelectronic components, heat dissipation has become a major problem in the design and construction of digital computers and high-power electronic equipment in general. Several alternatives to the solution of the problem have been studied in the past 10 years, including that of Chu [Ref. 1]. Among these, immersion cooling appears to be one of the most effective for achieving high heat-transfer coefficients.

# B. IMMERSION COOLING: ANALYTICAL AND EXPERIMENTAL STUDIES

From the construction of the first electronic digital computer, the solution to the problem of heat dissipation from high packaging density electronic equipment has not been easy. Even though very interesting forced convection methods have been studied and very frequently used (Chu [Ref. 1] describes several methods of air- and water-forced convection cooling), the hardware that has to be added to supply the additional power and to store and circulate the cooling liquid can be cumbersome in any application.

The direct immersion of the electronic circuitry into dielectric liquids improves its cooling capability significantly. Baker [Ref. 2] found liquid cooling by free convection to be more than three times as

effective as free convective air cooling of the same device. He made heat transfer measurements from thin-film tantalum nitride resistors evaporated on Corning 7059 glass substrates. The substrates were 1.0 by 2.6 by 0.12 cm. All resistors were rectangular, with their height (dimension parallel to the flow) one-half their base. The surface areas of the resistors were 0.0106, 0.104, 0.477, and 2.00 cm<sup>2</sup>. Two liquids were used in the study: freon with a Prandtl number of 3.9, and Dow Corning #200 silicone dielectric liquid with a Prandtl number of 126. The results showed that the heat transfer coefficient is approximately proportional to the cube root of the reciprocal of viscosity. It was also found that the convection coefficient does increase significantly as the source size decreases. The free convection heat transfer coefficient for the smallest source was more than an order of magnitude greater than for the largest source operated under the same conditions.

In a following study, Baker [Ref. 3] also examined different cooling techniques, such as nucleate boiling, forced convection, and bubble-induced mixing for cooling small heat sources.

Park and Bergles [Ref. 4] conducted experimental studies of natural convection from discrete flush-mounted rectangular heat sources on a circuit board substrate. Micro-electronic circuit elements were simulated with thin foil heaters supplied with DC power. Measurements were also made for protruding heaters of varying widths, in water and R-113. They found and documented the increase in heat transfer coefficient with decreasing width. This effect was greater in R-113 than in water. Also, for protruding heaters, the heat transfer

coefficients for the upper heaters in an array were found to be higher than those for the lower heaters. This behavior was not observed for flush-mounted heaters. As the distance between heaters increased, so did the heat transfer coefficients.

Chen, et al. [Ref. 5] made an experimental study of natural convection heat transfer in a liquid-filled rectangular enclosure with 10 protruding heaters from one vertical wall. The top surface of the enclosure maintained at a uniform temperature acted as the heat sink. All other surfaces, except the heater locations, were unheated. The enclosure was 16.7 cm in height, 2.3 cm in width, and 19.6 cm in depth (horizontal z-direction of the heaters). The 10 heaters were 0.8 cm high, 1.11 cm wide, and 19.6 cm deep. The vertical spacing betweer heaters was equal to the heater height. Distilled water and ethylene glycol were used as working fluids. Experimental results show that the bottom heater (heater 1), except for high Rayleigh number runs, has the highest heat transfer coefficient. The heat transfer coefficients at heaters 7, 8, and 9 are nearly the same and present the lowest values among the heaters. It was also shown that heat transfer coefficient decreases up to heater 7. At high Rayleigh numbers, the top heater (10) has the highest heat transfer coefficients. The flow visualization carried out indicates a core flow within the enclosure and a recirculating cell in the gap between heaters. Approximate measurements of the fluid velocity were provided from the particle traces in the flow visualization.

Keyhani et al. [Ref. 6] experimentally studied the buoyancy-driven flow and heat transfer in a vertical cavity with discrete flush heat sources on one vertical wall while the other vertical wall was cooled at a constant temperature. This enclosure contained 11 alternatively unheated and flush-mounted rows of isoflux heated strips. The liquid was ethylene-glycol with a Prandtl number of 150.

To examine the flow structure, visualization experiments were conducted for several power inputs. Finely ground aluminum powder (5 to 20 microns in size) was used to visualize the flow. The observed flow for a power input of 10 watts was highly structured except for small regions near the end walls. A primary flow circulating from the hot wall to the cold wall, a secondary flow with the same sense of circulation as the primary flow, and a tertiary flow in the opposite direction of the secondary flow were observed in the photographs taken at this power level. At a higher power level of 40 watts, the flow pattern above the mid-height region of the cavity showed transition from laminar to turbulent flow along the surface with heaters. The downward flow along the cold wall was still laminar. For a fixed power input, the heat transfer coefficient generally decreased with increase in height (or heater number). The rate at which Nusselt number decreased with the increase in heater number was found to be a strong function of the heater location.

Kelleher, et al. [Ref. 7] and Lee, et al. [Ref. 8] studied experimentally and numerically the cooling by natural convection of a water-filled rectangular enclosure with a long heater protruding from one vertical

wall and conducted flow visualization and heat transfer measurements with the heater at three different elevations. They found the two-dimensional flow to be dual-celled, consisting of a buoyancy-driven upper cell, in which the major part of the fluid motion takes place and which accounts for the majority of the convective heat transfer, and a shear-driven lower cell in which the fluid motion arises due to the viscous drag from the upper cell.

Liu. et al. [Ref. 9] used a three-dimensional finite difference method to study the natural convection cooling of an array of chips mounted on a vertical wall of a three-dimensional rectangular enclosure filled with a dielectric fluid Fluorinert FC 75. They found the long time solution to be oscillatory. Maximum chip temperatures were found on the top surfaces of the three top chips. However, these maximum temperatures did not all occur at the same time, but alternated among these three chips as time proceeded in a rather regular fashion. It was also observed that the bottom sink was quite ineffective in removing heat from the enclosure and that the convective circulation was essentially limited to the chip areas.

Joshi, et al. [Ref. 10] carried out an experimental investigation to study the natural convection cooling of a 3 by 3 array of heated protrusions in a rectangular enclosure filled with dielectric fluid FC-75. They observed that at low power levels (0.1 watts), the flow structure was largely determined by the thermal conditions at the enclosure surfaces. With increasing power levels (0.7 to 3.0 watts), an upward flow developed adjacent to each column of components. The flow away

from the elements became strongly three-dimensional and timedependent with increasing thermal inputs. Component surface temperatures were used to obtain a heat transfer correlation over the range of power levels examined.

Liu, et al. [Ref. 11] carried out a three-dimensional numerical study of immersion cooling of a chip array by laminar natural convection in a rectangular enclosure filled with a dielectric liquid. They determined the local temperature responses on the chip surfaces, their dynamic behaviors, and their dependence on the enclosure gap size. It was found that the temperature responses are decidedly oscillatory with wave forms ranging from simple to complex, and that maximum chip surface temperatures occur on the top row of chips for large gap sizes but oscillate among all three rows of chips for small gap sizes.

#### C. OBJECTIVES

The work reported here is a continuation of thesis research conducted at the Naval Postgraduate School by Pamuk [Ref. 12] and Benedict [Ref. 13]. The numerical studies by Liu, et al. [Ref. 9] and Liu, et al. [Ref. 11] were the motivation for some of the specific investigations carried out.

The objectives of the present investigation are twofold: The first is to examine the effect of bottom surface boundary condition on thermal transport in the natural convection cooling of a 3 by 3 array of horizontally arranged protruding elements on a vertical wall. The second objective is to examine heat transfer, fluid flow characteristics.

and the influence of the width of the chamber during the natural convection cooling of a 3 by 3 array of vertically arranged protruding elements on a vertical wall. Temperature fluctuation measurements were plotted and compared with existing numerical analysis of Liu, et al. [Refs. 9 and 11] and Benedict [Ref. 13]. For both studies, flow visualizations were also carried out.

### II. EXPERIMENTAL SET-UP

### A. GENERAL CONSIDERATIONS

Two different experimental configurations were used for the studies reported here. In the first, a 3 by 3 array of rectangular elements with the largest dimension aligned horizontally was examined. In the second study, the largest dimensions were in the vertical direction. The two experimental configurations are next described.

The details of the experimental procedures are available in Benedict [Ref. 13]. The Data Acquisition Programs were the same as used by Pamuk [Ref. 12] and Benedict [Ref. 13] with minor modifications in output format and number of channels. These programs are collected in Appendix D.

### 1. Experimental Set-Up for the Horizontal Arrangement

A schematic sketch of the arrangement is provided in Figure 2.1 (after Benedict [Ref. 13]). The configuration is the same as the one used by Joshi, et al. [Ref. 9] and Benedict [Ref. 13]. The distribution of the components and the top view of the chamber are illustrated in Figures 2.2 and 2.3 (both after Benedict [Ref. 13]).

This part of the thesis examines the effect of changing the enclosure bottom surface boundary condition on the overall thermal behavior of the system. A more detailed description of the experimental arrangement can be found in Benedict [Ref. 13].

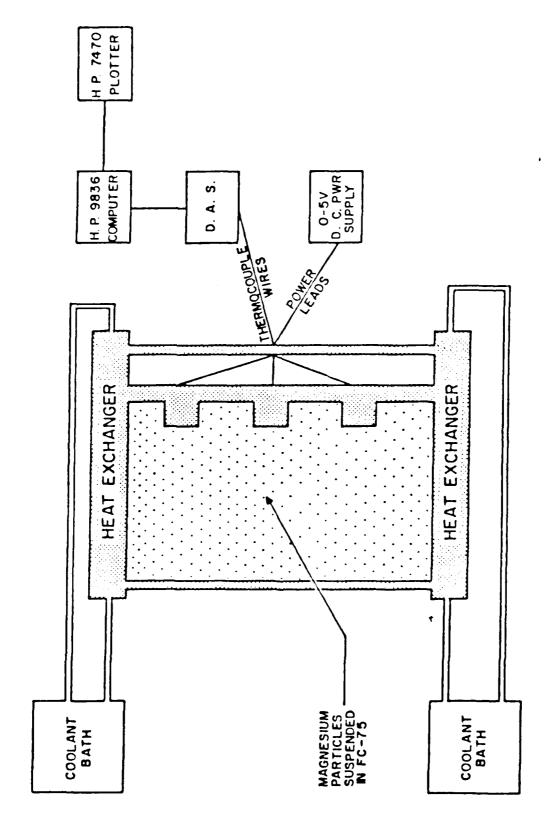


Figure 2.1 Schematic of Entire Assembly

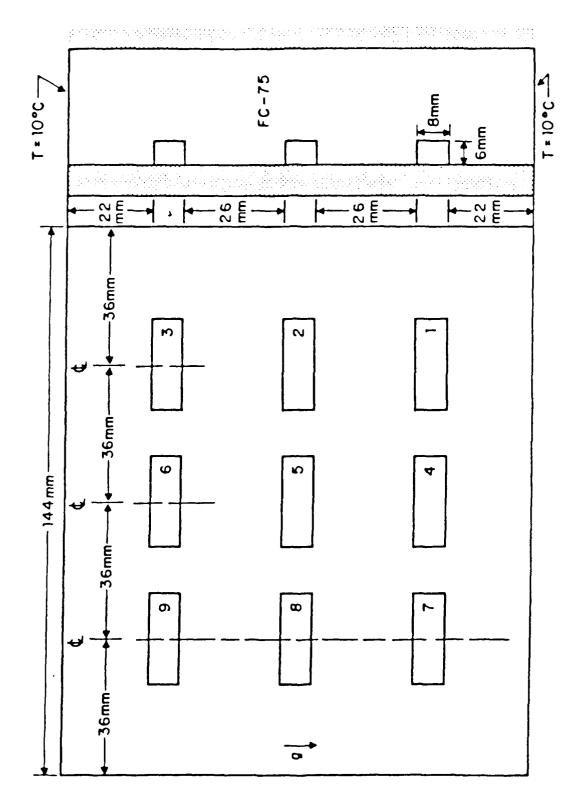


Figure 2.2 Simulated Circuit Card for the Horizontal Arrangement

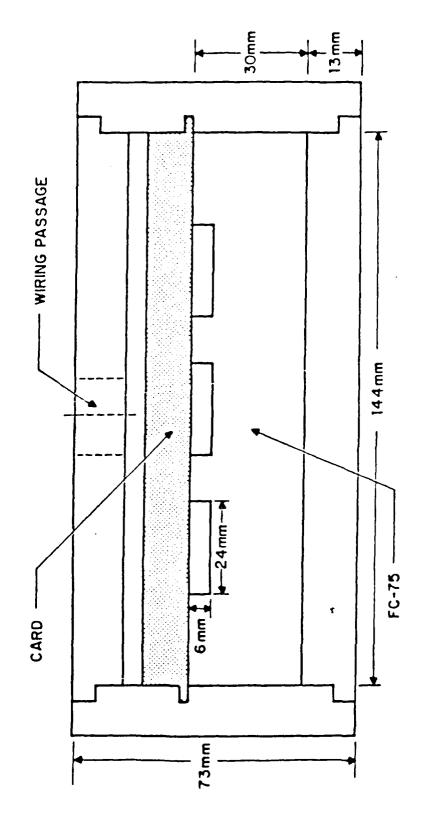


Figure 2.3 Top View of Horizontally Arranged Components Chamber

# 2. Experimental Set-Up for the Vertical Arrangement

The chamber assembly, illustrated in Figure 2.4 was made of 19.05 mm plexiglass with dimensions of 241.13 mm length, 152.0 mm height, and 120.65 mm width. As in the first arrangement, the chamber was filled with FC-75, a dielectric fluid through tubing at the bottom of the chamber.

In both experimental configurations, two heat exchangers, one at the top and one at the bottom, were used (see Figure 2.1). The design of the exchangers for the first configuration is described in Joshi, et al. [Ref. 10]. In the second study, several modifications were made to reduce the heat transfer from the outside environment to the colder circulating water. The resulting design is seen in Figure 2.5. The external walls of both top and bottom heat exchangers were made of plexiglass. The walls acting as the top and bottom of the fluid-filled enclosure were aluminum plates 3 mm thick, chosen to provide an almost isothermal surface condition. Inlet and outlet headers were provided for flow distribution. Three thermocouples, symmetrically placed along the plate length, were used for the calculation of the average surface temperatures. The heat exchangers could be accessed easily to block one or more of the channels to reduce the coolant flow rates.

A 3 by 3 array of discrete protrusions, vertically arranged (see Figure 2.6), was mounted on a 19.05 mm thick plexiglass card. The card was slid into the chamber and was kept in location by plexiglass supports that prevented its linear movement as well as rotation.

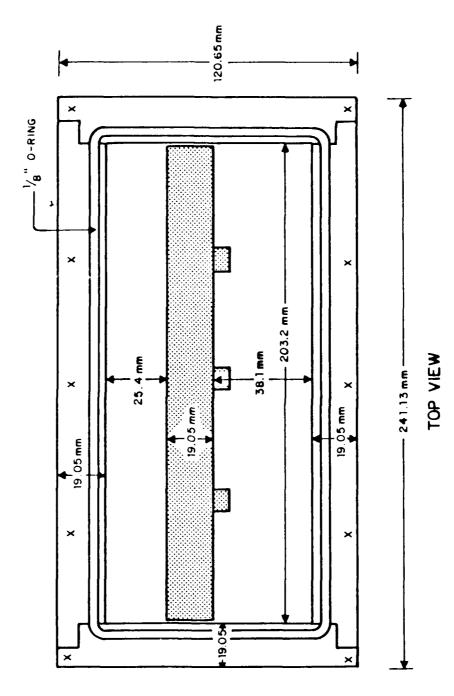


Figure 2.4 Chamber Assembly for the Vertical Arrangement

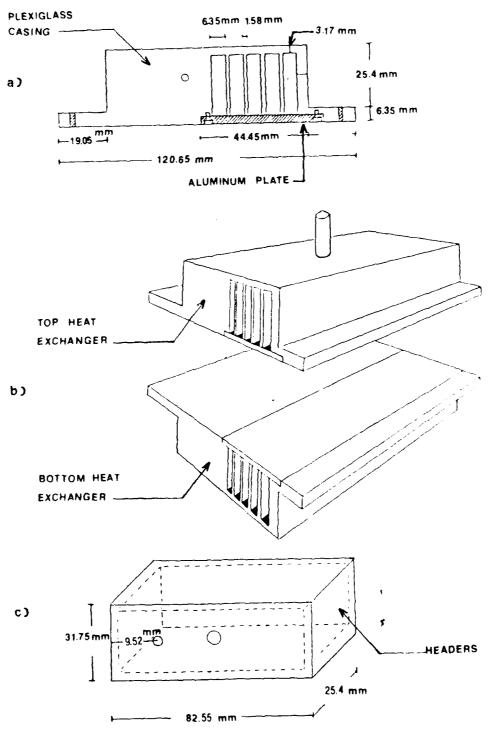


Figure 2.5 Heat Exchangers

(a) Cross-Sectional View; (b) Isometric View; (c) Inlet and Outlet Headers

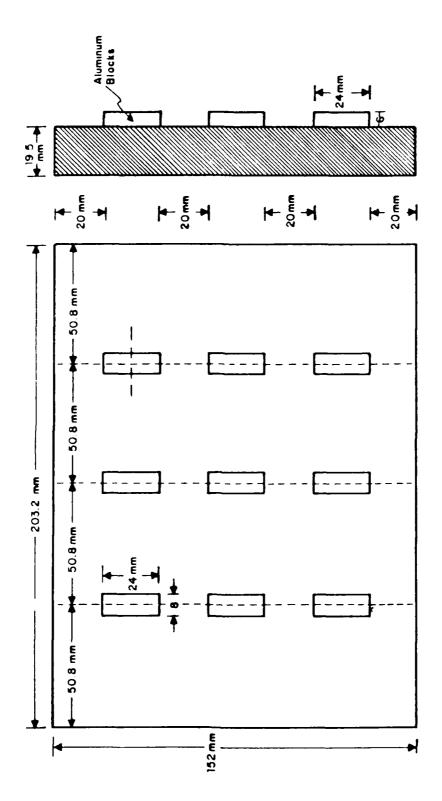


Figure 2.6 Simulated Circuit Card for the Vertical Arrangement

The chamber design allowed the replacement of the card in a simple way. The upper heat exchanger could be removed and the new card could be easily installed. This permits the installation of different card configurations (staggered, flush mounted, etc.) in the future without much additional effort. By moving the card back or forth, the chamber width could be changed. This was done in order to study the effect of this parameter in the overall heat transfer.

The heated components in both studies were aluminum blocks of 8 mm by 24 mm and 6 mm high (see Figure 2.7—after Benedict [Ref. 13]). The dimensions and geometry simulate approximately a 20-pin dual-in-line-package. A nearly uniform heat flux condition was maintained at the base of each block by attaching a foil-type heater with a resistance of about 11 ohms. The foil heaters contained a network of Iconel foil mounted on a Kapton backing and were 23.6 mm by 7.6 mm in dimension and were bonded to the base of each aluminum block using a high thermal conductivity epoxy (Omega Bond 101).

Temperatures at the center of each fluid exposed component face were determined using .127 mm diameter copper-constantan thermocouples. Thermocouple locations on each heater are illustrated in Figure 2.7.

All the thermocouples were connected to an HP-3497 automatic data acquisition system controlled by an HP-9826 microcomputer. Power to the heaters was supplied by a 0-40 volt. 0-1A DC

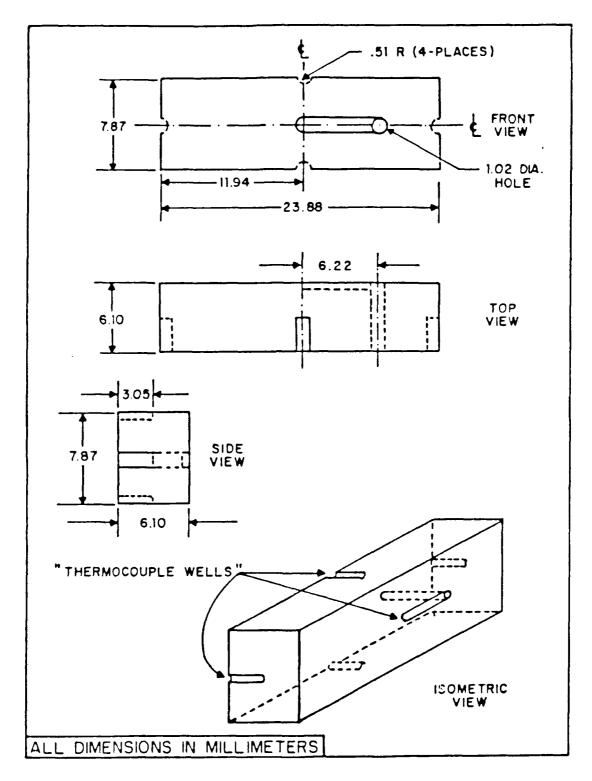


Figure 2.7 Heating Element and Thermocouple Location

power supply. A simultaneous measurement of the overall voltage drop, along with the voltage drop across each heater, allowed the computation of the power dissipation through individual heaters.

Flow visualization was carried out with a 4 mw Helium-Neon laser for illumination. To produce a plane of light, a cylindrical lens was used (see Figure 2.8—after Benedict [Ref. 13]). The laser sheet illuminated magnesium particles (specific gravity of 1.74) that were added to the FC-75 (specific gravity of 1.76 at 25° C). This technique allowed for the visualization of a single two-dimensional plane of the flow field. Time exposure photographs of the flow were obtained using a Nikon F-3 camera with a 50 mm lens, a MD-4 motor drive, and a MT-2 intervalometer.

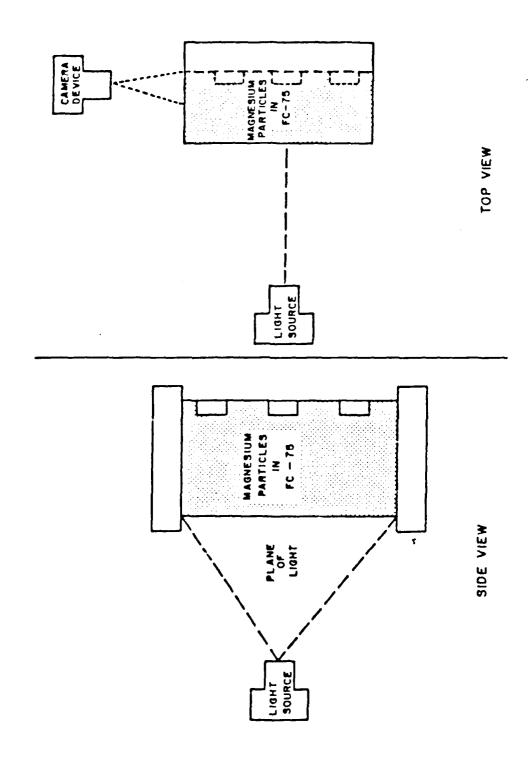


Figure 2.8 Flow Visualization Set-Up

### III. RESULTS AND DISCUSSIONS FOR HORIZONTAL ARRANGEMENT

### A. FLOW PATTERNS

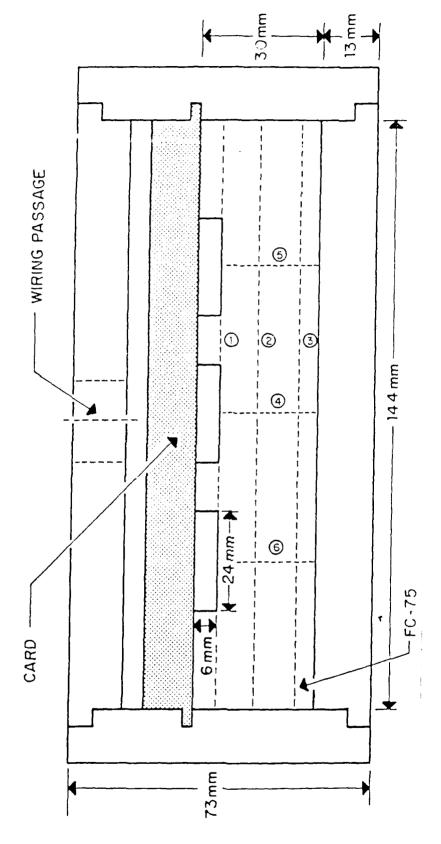
Flow visualization was carried out in six vertical planes, seen in Figure 3.1 (after Benedict [Ref. 13], for the two different bottom boundary conditions: 20° C and insulated. The three-dimensional transport responses, across the range of power dissipation of 0.1 W to 3.0 W, were inferred from these visualizations. In the following, a detailed description of the observed flows is provided.

### 1. Flow Patterns for the Bottom Boundary at 20° C

The flow patterns observed at several power dissipation levels from no dissipation to 3.0 W are collected in Figures 3.2 to 3.7. Visualization with no power (see Figures 3.2 and 3.3) was to examine the natural convection flow due only to the difference in temperature between the two heat exchangers, and its possible influence on the flow patterns, with the heaters turned on.

At no power, the flow consisted of a single clockwise cell that occupied the entire chamber. This overall flow was established as a result of the temperature differences between the enclosure walls. The three-dimensionality of the flow was evident from visualizations in the various planes.

At 0.1 W, the pattern observed at no power in Figures 3.2 and 3.3 was completely distorted and no remains of the strong clockwise



The six vertical flow visualization planes are identified in the sketch.

Figure 3.1 Top View of the Enclosure With the Card Placed in Position

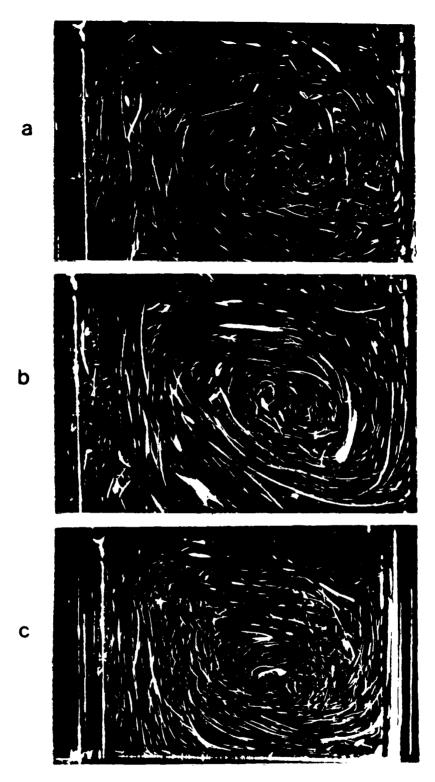


Figure 3.2 Visualization With No Power in Planes 1 (a), 2 (b), and 3 (c)

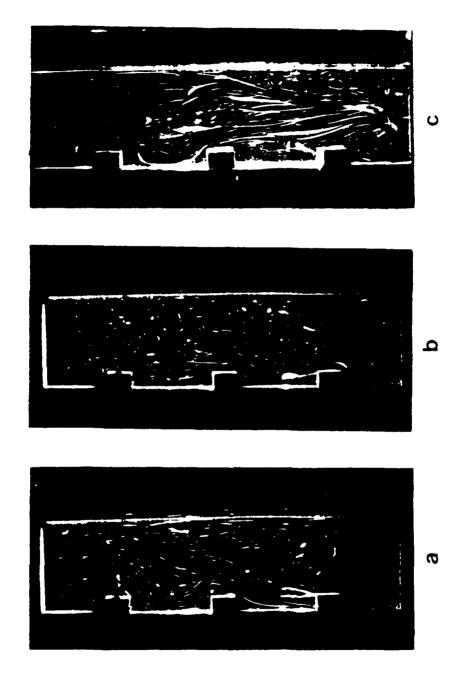


Figure 3.3 Visualization With No Power in Planes 4 (a), 5 (b), and 6 (c)

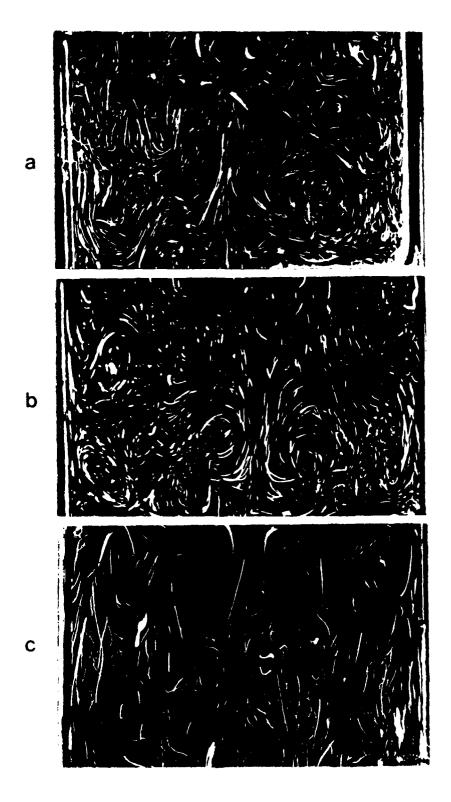


Figure 3.4 Visualization with 1.1 W in Planes 1 (a), 2 (b), and 3 (c)

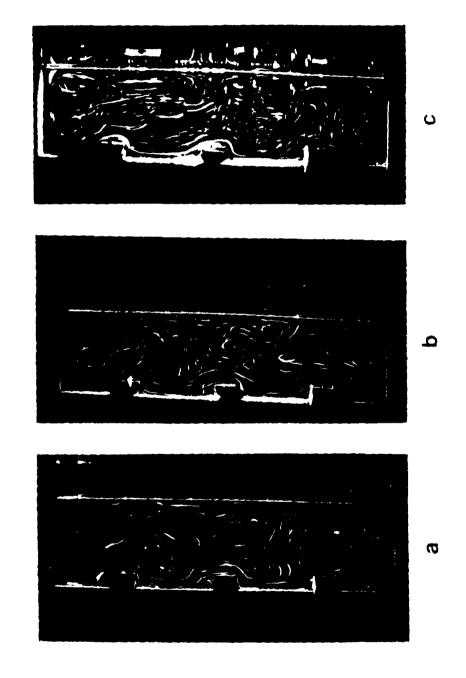


Figure 3.5 Visualization With 1.1 W in Planes 4 (a), 5 (b), and 6 (c)

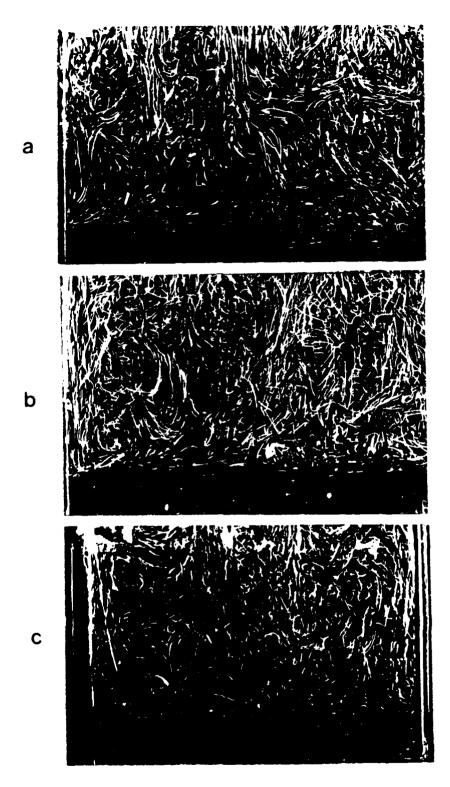


Figure 3.6 Visualization with 3.0 W in Planes 1 (a), 2 (b), and 3 (c)

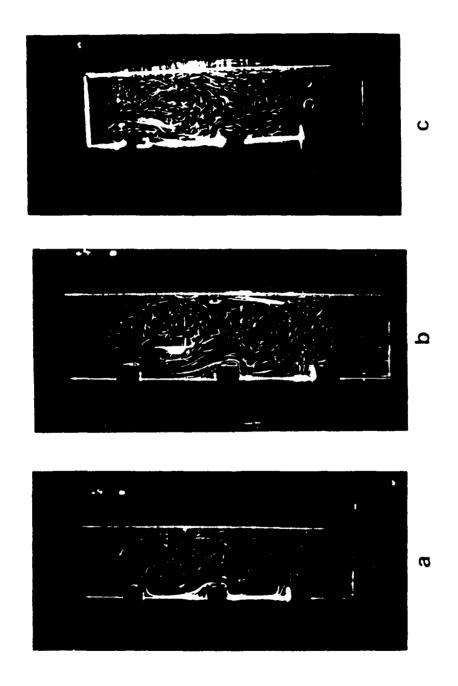


Figure 3.7 Visualization With 3.0 W in Planes 4 (a), 5 (b), and 6 (c)

flow were seen. Joshi, et al. [Ref. 10] at the same power level reported two very well defined large clockwise cells, one on each side of the central component column. The present visualization showed that the flow now was completely dominated by the relatively high temperature of the bottom heat exchanger. The effects of the buoyancy forces due to the power dissipation were small except in plane 1 (close to the heaters), where there was a well defined upflow.

In plane 2, the particle traces showed a decrease in velocity. Also, dark regions, as observed in Joshi, et al. [Ref. 10], were seen. These were, however, thinner and not well defined. These nearly quiescent regions appear due to the stable stratification produced by the bottom heat exchanger. Descending fluid from the top is unable to penetrate the colder layer of fluid at the bottom. In plane 3, a downflow resulted due to an increase in the density of the colder fluid, in contact with the upper heat exchanger, at 10° C.

At 1.1 W (see Figure 3.4), a well defined pattern could be observed in planes 1 and 2. Along the central column of heaters, the upflow was wider and stronger than near the adjacent columns. This flow was the result of the interaction of an upflow along the central column, a clockwise flow around the right column (heaters 1, 2, and 3), and a counterclockwise flow around the left column (heaters 7, 8, and 9). In plane 3, a downflow of cold liquid was seen. In Figure 3.5, flow patterns at 1.1 W in planes 4, 5, and 6 are illustrated. It is possible in these pictures to appreciate in a side view the strong upflow adjacent to the components. The basic difference with the flow

pattern found in the study by Joshi, et al. [Ref. 10] at the same power level is still that the inactive zone in the bottom of the chamber is not well defined.

With further increase in the power level, the flow in plane 1 exhibited stronger upflow near the components. The buoyancy forces generated by the power dissipation here were strong enough to extend their influence to planes 2 and 3. At 3.0 W, a very thin, dark layer was still observed at the bottom of the chamber (see Figure 3.6). A view of the flow patterns in planes 4, 5, and 6 is illustrated in Figure 3.7. This figure shows a buoyant fluid layer adjacent to the components. In the remaining chamber, the motion was completely random.

### 2. Flow Pattern With the Bottom Boundary Insulated

The flow pattern for this condition showed similar trends as discussed in section A.1. The induced flow due to the difference in temperature between the two heat exchangers was not appreciable.

#### B. HEAT TRANSFER MEASUREMENTS

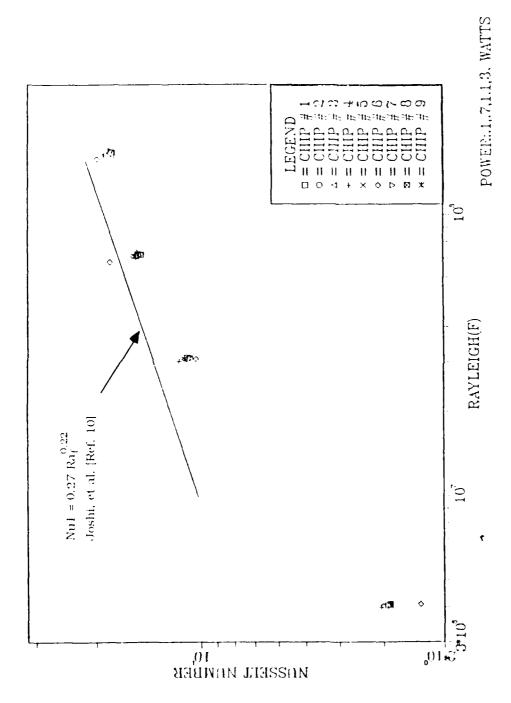
Heat transfer measurements were made at power levels of 0.1, 0.7, 1.1, 1.5, and 3.0 watts for the two bottom surface boundary conditions. The temperature at the top heat exchanger was maintained constant at 10° C in all experiments. Temperature and flux-based Rayleigh numbers (Ra<sub>t</sub> and Ra<sub>f</sub>) were calculated in a manner identical to that discussed in Joshi, et al. [Ref. 10] and plotted versus Nusselt number (Nu1). These are defined in the Table of Symbols and Abbreviations.

## 1. Heat Transfer Measurements With the Bottom Boundary at 20° C

Component surface temperature measurements at various power levels are collected in Tables 1 through 8 in Appendix C. The nondimensional heat transfer parameters in the form of Nusselt versus Rayleigh numbers are illustrated in Figures 3.8 and 3.9. In the same plots, the correlations found by Joshi, et al. [Ref. 10] were also plotted.

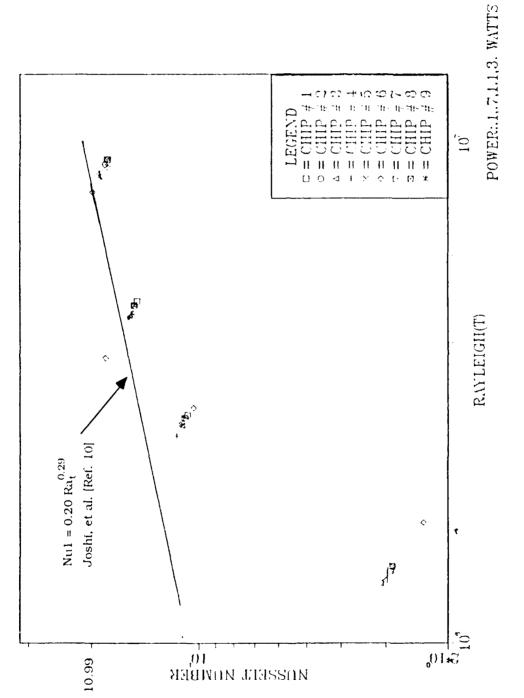
We can see that having the bottom heat exchanger at 20° C results in general in lower Nusselt numbers than those found by Joshi, et al. [Ref. 10] in the range of Rayleigh numbers considered. At higher power levels, when the temperature of the heaters was considerably higher than the bulk temperature of the dielectric fluid, the difference in Nusselt numbers is smaller than at lower power levels. The Nusselt number at a flux-based Rayleigh number of 106 found by Joshi, et al. [Ref. 10] was 20.4, while the Nusselt number obtained here for the same Rayleigh number was 19. At lower power levels 0.1 W and 0.7 W, the differences in Nusselt number were greater, and the decrease in the heat transfer coefficient was significant. The Nusselt number found by Joshi, et al. [Ref. 10] was 10.5 at a flux-based Rayleigh number of 106, while the Nusselt obtained with the present configuration was 2.9.

At power levels of 0.1 W and 0.7 W, a small increase in the upper heaters' temperatures over the lower ones was observed. At higher power levels, the highest temperatures were found irregularly in different components.



Correlation found by Joshi, et al. [Ref.10] is plotted with a continuous line.

Figure 3.8 Plot of Flux-Based Rayleigh Number Versus Nusselt Number



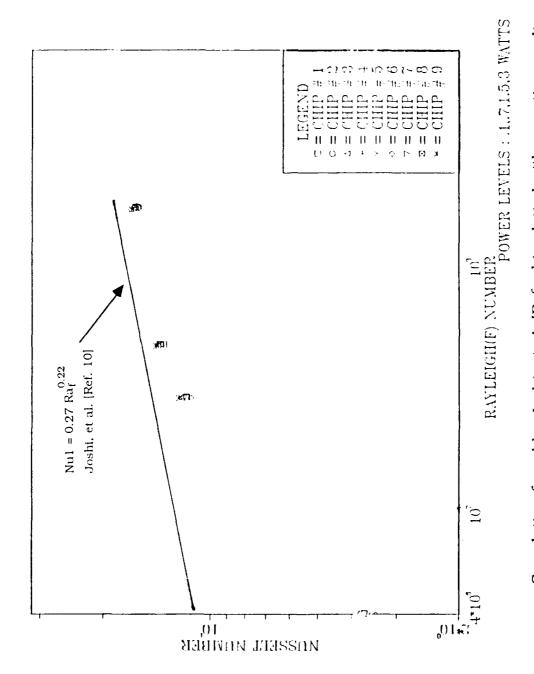
Correlation found by Joshi, et al. [Ref.10] is plotted with a continuous line.

Figure 3.9 Plot of Temperature-Based Rayleigh Number Versus Nusselt Number

The component that presented the largest variations from the mean in the heat transfer coefficients was the upper component in the central column (heater 6). This is evidenced as deviations from the general trend of the obtained data. The variations (lower heat transfer coefficient at low power levels, and higher heat transfer coefficients at higher power levels) are expected because this component receives the influence of the combined upflowing streams (produced by the other heaters), as was observed and documented in the flow visualization results in Section A.1. The effect is greater at higher power levels when the component's temperature is substantially larger than the bottom heat exchanger temperature.

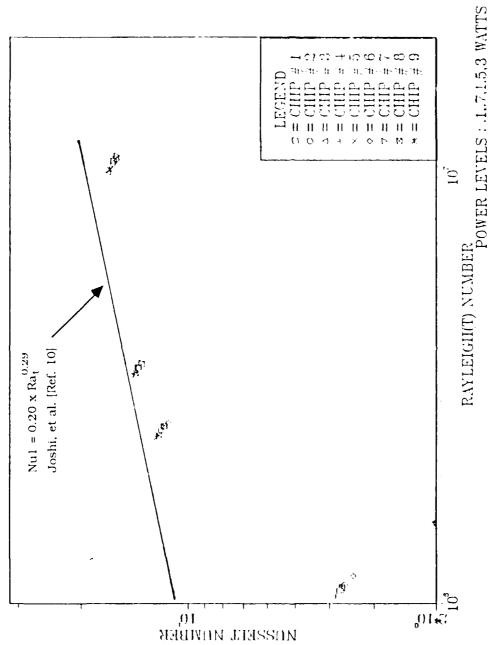
## 2. Heat Transfer Measurements With the Bottom Boundary Insulated

The results of the temperature measurements with the bottom boundary insulated and the reduced dimensionless parameters are collected in Tables 9 through 16 in Appendix C. In Figures 3.10 and 3.11, flux and temperature Rayleigh numbers versus Nusselt numbers were plotted. Correlations found by Joshi, et al. [Ref. 10] were also plotted for comparison. It was seen that having the bottom heat exchanger insulated improved the cooling at low power levels (0.1 W and 0.7 W) over that obtained with the bottom boundary maintained at 20° C. This result is expected because now the temperature of the bottom boundary was 15° C at 0.1 W and 17° C at 0.7 W. At a power level of 3.0 W, no cooling improvement was observed. The temperature for the bottom boundary at 3.0 W was 22° C.



Correlation found by Joshi, et al. [Ref. 10] is plotted with a continuous line.

Figure 3.10 Plot of Flux-Based Rayleigh Number Versus Nusselt Number



Correlation found by Joshi, et al. [Ref. 10] is plotted with a continuous line.

Figure 3.11 Plot of Temperature-Based Rayleigh Number Versus Nusselt Number

Comparisons with the correlation obtained by Joshi, et al. [Ref. 10] show a decrease in the heat transfer coefficient when the lower boundary was insulated. This was evidenced by the lower Nusselt numbers at all power levels.

#### IV. RESULTS AND DISCUSSIONS FOR VERTICAL ARRANGEMENT

#### A. FLOW VISUALIZATION

The visualization for this experiment was tried for a chamber width of 9 mm. As was expected, there was almost no flow in the narrow gap between components and the front wall. A boundary layer-like behavior was observed on the vertical side faces of the components. The photography process was complicated because the thickness of the plane to be illuminated by the laser sheet for this chamber width was only 3 mm.

#### B. HEAT TRANSFER MEASUREMENTS

Component surface temperature measurements were made for chamber widths of 30 mm and 9 mm (see Figure 4.1). The power level range was 0.1 W to 3.0 W. Temperatures of the top and bottom boundaries were maintained constant at  $10^{\circ}$  C. Plots of Nu1 versus  $Ra_f$  are provided for comparisons with data obtained by Benedict [Ref. 13].

#### 1. Heat Transfer Measurement for w = 30 mm

Tables 17 through 28 in Appendix C compile component surface temperature and resulting nondimensional heat transfer data for this gap size with increasing power levels. The mean values of the component averaged temperatures over the nine heated components were  $13^{\circ}$  C for 0.1 W and  $47^{\circ}$  C for 3.0 W. In the range 0.1 W to 1.1 W, the lowest  $T_{avg}$  levels were on the bottom-row components

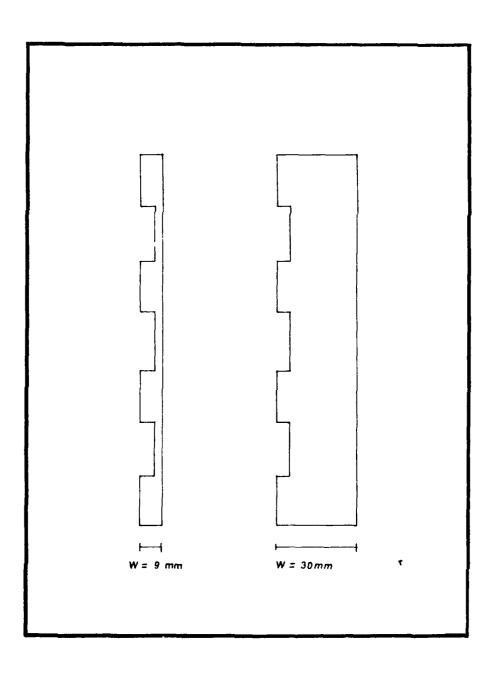
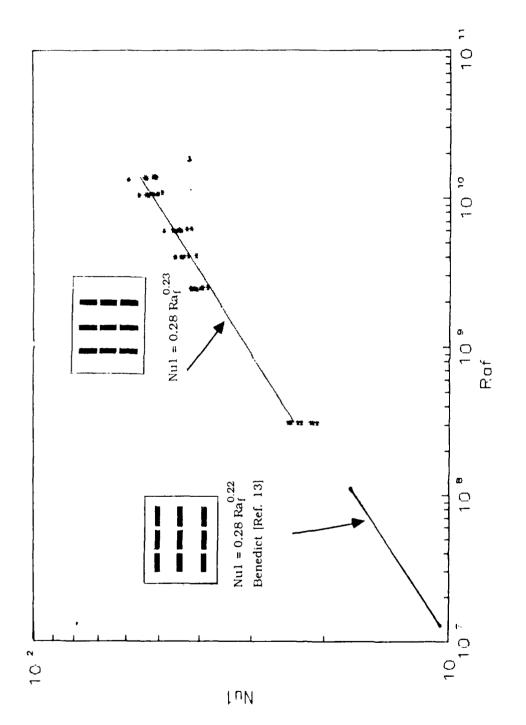


Figure 4.1 Side View Showing the Chamber Widths
Used in the Experiment

(components 1, 4, and 7). The observed tendency was that temperatures on specific locations on the components in the top row were higher than those in the same location on the components in lower rows. As was pointed out by Liu, et al. [Ref. 11], the possible reason for this might be that components in the top row are in contact with warmer liquid, and the upper-row components are located in the heated wake regions of the lower rows. Additionally, the stratified fluid away from the components, which feeds fluid toward the component rows, is also at higher temperature for the upper rows.

Analyzing individual components in the middle and lower rows, for all power levels, the minimum measured temperatures were on the bottom surfaces. This trend is also supported by Liu, et al. [Ref. 9]. On the top row components, the lowest temperatures were on either one of the vertical side faces. Maximum temperatures were found generally on the component surface facing the front chamber wall. Liu, et al. [Ref. 11] obtained numerically maximum temperatures in the surfaces facing upward and attributed this to the fact that the heated flow coming off the vertical surfaces reduced the heat transfer coefficient at the component top surface. At higher power levels, oscillations in temperature changed the locations of the maximum and minimum instantaneous values, but the general tendencies found earlier were still noticed.

In Figure 4.2, a plot of Nu1 versus Ra<sub>f</sub> is seen. Data obtained from Benedict [Ref. 13] is also plotted. A linear least squares fit to the present measurements in Figure 4.2 was performed. This is given by:



The curve fit for the horizontal arrangement is from Benedict [Ref. 13]. Present measurements and curve fit are for the vertical arrangement.

Figure 4.2 Comparison of the Nondimensional Heat Transfer Measurements for Two Different Component Orientations

Nu1 = 
$$0.28 \text{ Ra}_{\mathrm{f}}^{0.23}$$
 in the range  $3*10^8 < \text{Ra}_{\mathrm{f}} < 10^{10}$  and  $15 < \text{Pr} < 30.2$  (4.1)

and the one obtained with the data from Benedict [Ref. 13] was:

Nul = 0.28 Ra
$$_{\rm f}^{0.22}$$
 in the range  $10^7 < {\rm Ra}_{\rm f} < 2*10^8$  and  $15 < {\rm Pr} < 30.2$  (4.2)

Comparisons between Equations 4.1 and 4.2 indicate that Nu appears not to depend on the orientation of the components in the range of  $Ra_{\rm f}$  and Pr considered. This is illustrated in Figure 4.2

#### 2. Heat Transfer Measurement for w = 9 mm

In Tables 29 through 40 in Appendix C, component temperatures and resulting nondimensional heat transfer data are compiled. Decreasing the chamber width from 30 mm to 9 mm produced some increase in the average temperature of the components  $T_{avg}$ . This behavior was expected considering that now the surface of both top and bottom heat exchangers has been reduced to 30 percent of its former value. The mean value of the component averaged temperatures over the nine heaters for a power of 0.1 W was  $14.5^{\circ}$  C,  $1.5^{\circ}$  C higher than the average temperature obtained with 30 mm width. For a dissipation level of 3.0 W, the mean value of the components' averaged temperature over the nine heaters was  $51^{\circ}$  C,  $4.0^{\circ}$  C higher than the average observed for the 30 mm width. The  $T_{avg}$  value increased from the bottom to the top row, as was also found for w=30 mm.

Analyzing individual components on the bottom row (components 1, 4, and 7), minimum temperatures were found on the bottom surfaces.

Plots of Nul versus  $Ra_f$  are illustrated in Figure 4.3. The correlation obtained for this chamber width was:

Nu1 = 0.073 
$$Ra_f^{0.28}$$
 in the range 3 \*  $10^8 < Ra_f < 10^{10}$   
and  $15 < Pr < 30.2$  (4.3)

This correlation indicates the expected decrease in Nu1 for the same  $Ra_f$ , when compared with Equation 4.1 for w=30 mm.

#### C. TEMPERATURE FLUCTUATIONS IN STEADY STATE

Oscillations in component surface temperatures following achievement of nominally steady conditions were measured in the dissipation range of 0.1 W to 3.0 W. Three thermocouples were scanned at a rate of approximately three times per second for a period of 200 seconds. Plots of surface temperature variations were made in order to display the long-time temperature fluctuations and compare with results of Liu, et al. [Ref. 11] and Benedict [Ref. 13]. Figure 4.4 is a vertical arrangement diagram which portrays the location of the scanned thermocouples.

### 1. Surface Temperature Fluctuations for a w = 30 mm

Temperature oscillations for this chamber width are illustrated in Figures 4.5 through 4.7. It was observed that at all power

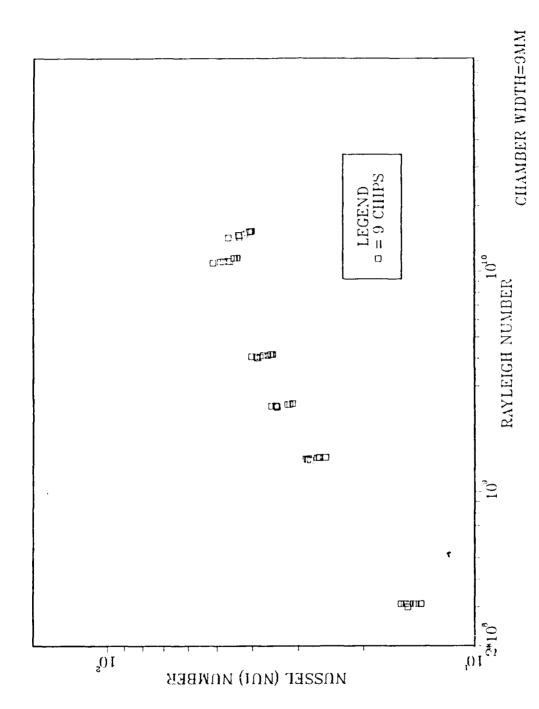


Figure 4.3 Plot of Nul vs. Ra for a Chamber Width = 9 mm

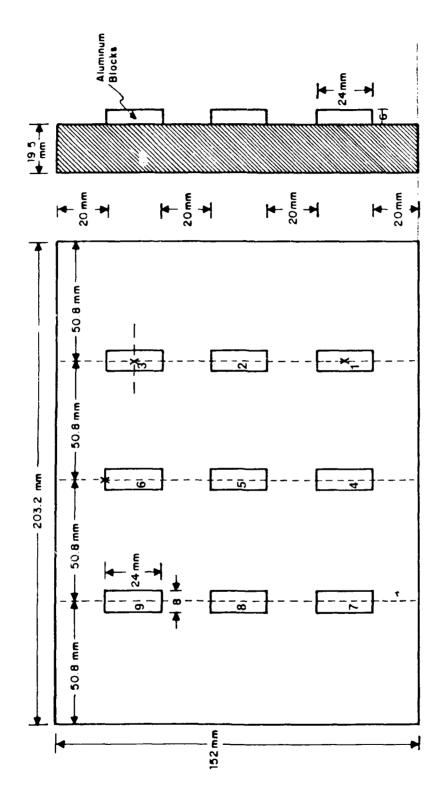


Figure 4.4 Location of Thermocouples Scanned for Measurements of Fluctuations

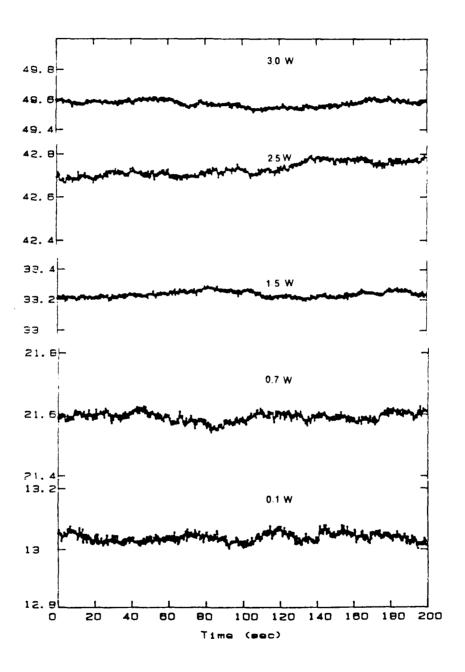


Figure 4.5 Temperature Fluctuations for Thermocouple No. 0 at Different Power Levels

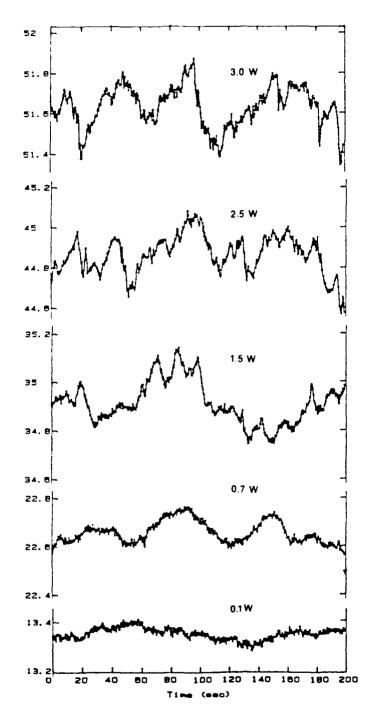


Figure 4.6 Temperature Fluctuations for Thermocouple No. 12 at Different Power Levels

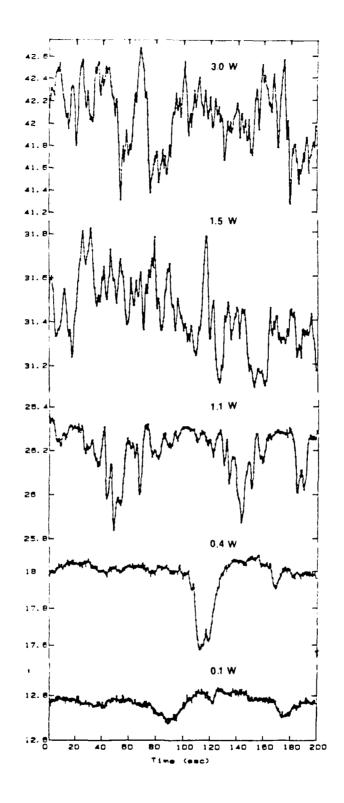


Figure 4.7 Temperature Fluctuations for Thermocouple No. 31 at Different Power Levels

levels considered, there were no temperature fluctuations on the components in the lower row. Benedict [Ref. 13] documented with heat transfer measurement and flow visualizations that the stagnant fluid layer above the bottom heat exchanger prevented the penetration of warmer fluid, resulting in conduction-dominated transport for the bottom row of components.

At 0.1 W, a spread in temperature of less than 0.5° C was observed between the six thermocouples that were scanned. Increasing the power level to 0.7 W, oscillation amplitudes with a mean of 0.7° C were observed in component 6. At 1.1 W, the amplitude increased to 0.8° C. Benedict [Ref. 13] found that a component at the same relative location and power level in a horizontal arrangement had almost no oscillations. At 2.5 W, oscillations of about 1.6° C were found. At 3.0 W, oscillations rose to almost 1.7° C at the same location. Benedict [Ref. 13] found at 3.1 W for the equivalent thermocouple an amplitude of 0.85° C.

### 2. Surface Temperature Fluctuations for w = 9 mm

Plots of temperature oscillations are illustrated in Figures 4.8 through 4.10. At 0.1 W, no fluctuations were found in any of the thermocouples scanned. At 0.4 W, fluctuations of  $0.3^{\circ}$  C were observed in the top row components. No fluctuations were observed in the middle and bottom row components.

Increasing the power dissipation level to 0.7 W, no fluctuations were observed in either the middle or the bottom rows, but

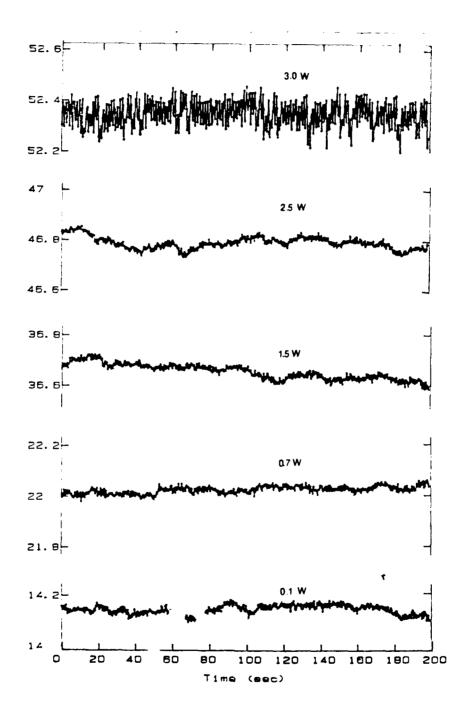


Figure 4.8 Temperature Fluctuations for Thermocouple No. 0 at Different Power Levels

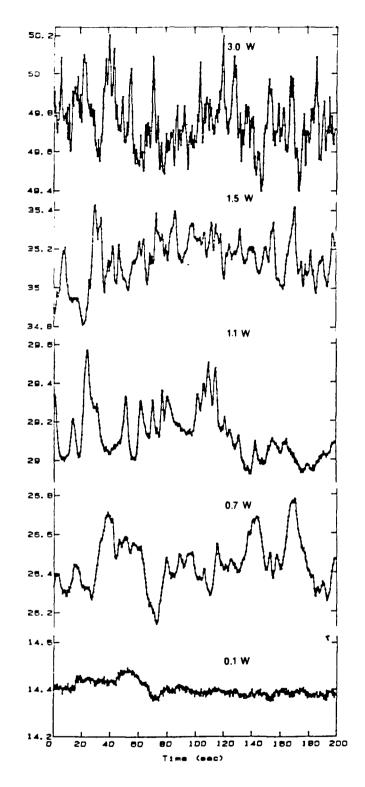


Figure 4.9 Temperature Fluctuations for Thermocouple No. 12 at Different Power Levels

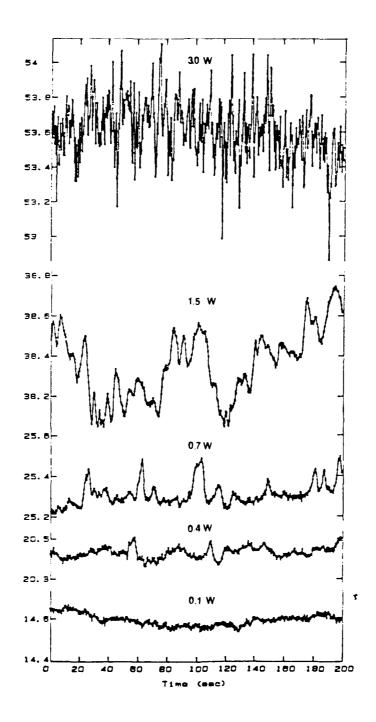


Figure 4.10 Temperature Fluctuations for Thermocouple No. 31 at Different Power Levels

fluctuations of 0.7° C were observed in the top row. At 1.1 W, fluctuations in the top-row components were about 0.9° C. No fluctuations were observed at the middle and bottom rows. At 1.5 W, fluctuations of 0.2° C appeared in the components in the middle row and reached values of 1.1° C in the top-row components. At 3.0 W, the highest power level utilized in the experiments, fluctuation amplitudes on the top-row components were recorded at 2.0° C. It is interesting to note that no significant increase in the amplitude of the fluctuations was observed when the chamber width was changed from 30 mm to 9 mm. Liu, et al. [Ref. 11] calculated temperature oscillations peak to valley of 8° C for the 9 mm chamber width. They attributed the increase in the oscillation amplitude to the fact that now the flow is highly confined.

#### V. RECOMMENDATIONS

The design of the present chamber can be improved in many ways to give more versatility in the following experiments. The recommended changes that can be made to software and hardware include:

- Placement of the blocks can be done by screwing or attaching them to the board in a different way to the one used intil now, which is bonding the chips to the board with glue. This would allow the experimenter to change a defective heater or change the orientation of the chips for a different set of experiments, using the same board and the same equipment set-up.
- To avoid the flow of dielectric liquid to the back of the chamber through the gaps between the board and the chamber walls that can alter the heat transfer results or the flow visualization, a small diameter O-ring can be used. A groove should be engraved in the board to allow the O-ring installation.
- Temperature measurements within the fluid and on the board surfaces should also be performed.
- a Fast Fourier Transform algorithm should be developed to perform frequency analysis on the surface temperature fluctuations data. In addition, improvements in the plotting programs can be made.
- With the present set-up, different combinations of heaters could be powered, row-wise or column-wise or staggered, instead of the entire array. This variation might help better to explain the heat transfer and flow characteristics of the chamber.

#### APPENDIX A

#### SAMPLE CALCULATIONS

## A. CONVERSION OF THERMOCOUPLE VOLTAGES TO TEMPERATURES

(Channels 0 to 60 and 71 to 76, in the data acquisition system)

$$T = D1 + D2 * Emf + D3 * Emf^2 + D4 * Emf^3 + D5 * Emf^4 + D6 * Emf^5 + D7 * Emf^6 + D8 * Emf^7$$

where D1 to D9 are the calibration coefficients of the Omega thermocouples and are: 0.10086091, 25727.9, -767345.8, 7802-5596, -9247486589, 6.98E11, -2.66E13, and 3.94E14.

Calculating the temperature found in the thermocouple connected to channel 0 at 1.1 W gives:

$$Emf = 0.995E-3 V$$
  
 $T = 24.48^{\circ} C$ 

#### B. CALCULATION OF HEATER POWER

Channels 61 to 70 in the data acquisition system are used to measure the supply voltage (61) and voltage to the heaters.

Power = 
$$Emf * (Volt - Emf)/Rp$$

Calculating the power dissipated by the heater #3:

Power = 
$$3.408 * (4.085 - 3.408)/2.07$$
  
Power =  $1.114 \text{ W}$ 

#### C. CALCULATION OF THE DIMENSIONLESS PARAMETERS

#### 1. Calculation of the Block Faces Areas

Dimensions of the aluminum blocks are: length 24 mm, width 8 mm, and thickness 6 mm.

$$A_{cen} = 24 \text{ mm} * 8 \text{ mm} = 192 \text{ mm}^2 = 1.92\text{E-4 m}^2$$
 $A_{lef} = 24 \text{ mm} * 6 \text{ mm} = 144 \text{ mm}^2 = 1.44\text{E-4 m}^2$ 
 $A_{rig} = 24 \text{ mm} * 6 \text{ mm} = 144 \text{ mm}^2 = 1.44\text{E-4 m}^2$ 
 $A_{top} = 6 \text{ mm} * 8 \text{ mm} = 48 \text{ mm}^2 = 4.8\text{E-5 m}^2$ 
 $A_{bot} = 6 \text{ mm} * 8 \text{ mm} = 48 \text{ mm}^2 = 4.8\text{E-5 m}^2$ 
 $A_{tot} = \Sigma A = 576 \text{ mm}^2 = 5.76\text{E-4 m}^2$ 
 $T_{avg} = \Sigma (T(I) * A(I))/A_{tot}$ 

Calculating for component 3 at 1.1 W:

$$T_{avg} = (27.67 * 1.92E-4 + 25.73 * 4.8E-5 + 26.08$$
  
 $* 1.44E-4 + 26.69 * 4.8E5) / 5.76E-4$   
 $T_{avg} = 26.63^{\circ} C$ 

# 2. Calculation of the Temperatures at the Back of the Components

Due to problems in the placement of the thermocouples that measure the temperature at the heaters, these temperatures were calculated with a calibration curve for w=30 mm from data obtained in Benedict [Ref. 13]. This calibration cannot be applied to the case where the width of the chamber is very small. In such a case, when w=9 mm, a one-dimensional conduction analysis was applied to find the back temperature.

The best fit for the calibration points was:

$$T(K) = 14.003957 * Power + 14.517501$$

So, for 1.1 W,

$$T = 29.92^{\circ} C$$

### 3. To Calculate the Conduction Losses Through the Circuit Card

$$Q_{loss} = \Delta T/Rc = 1/N \Sigma (T(I) - Tb(J))/Rc$$
 $R_c = L/kA$ 
 $R_c = 19.5E-3/(0.195 * 8E-3 * 24E-3) = 520.83 K/W$ 
 $L = 19.5E-3 m$ 
 $k = 0.195 W/m.K (plexiglass conductivity [Ref. 14])$ 
 $A = (24E-3 * 8E-3) m^2 = 1.92E-4 m^2$ 
 $Q_{loss} = (29.92 - 17.31)/520.83$ 
 $= 0.024 W$ 

### 4. To Find the Average Sink Temperature

Channels 58, 59, and 60 in the bottom heat exchanger and channels 61, 72, and 73 in the top heat exchanger.

$$T_{sink} = 1/N (\Sigma T_{tc} + \Sigma T_{bc})$$
 
$$T_{sink} = (10.05 + 10.1 + 10.02 + 10.11 + 10.12 + 10.13)/6$$
 
$$T_{sink} = 10.08^{\circ} C$$

To find the net power dissipated by the heater,  $Q_{net}$ :

$$Q_{net} = Power - Q_{loss}$$

For 1.1 W and component 3:

$$Q_{\text{net}} = (1.1 - 0.024) \text{ W}$$
  
= 1.076 W

To find the convection coefficient h (from Newton's law of cooling):

$$Q_{net} = h * A_{tot} * \Delta T$$
 $\Delta T = T_{avg} - T_{sink}$ 
 $\Delta T = (26.63 - 10.08)^{\circ} C$ 
 $T = 16.55^{\circ} C$ 
 $h = Q_{net} / (A_{tot} * \Delta T)$ 

### 5. For 1.1 W and Component 3

$$h = 1.09 / (16.55 * 5.76E-4)$$
  
 $h = 114.342 W/m^2 K$ 

### 6. To Calculate the Thermal Conductivity of the FC-75

$$k = (0.65 - 7.8947E-4 * T_{film})/10$$

where 
$$T_{film} = (T_{avg} + T_{sink})/2$$
.

At 1.1 W and chip 3:

$$T_{film} = (26.63 + 10.08)^{\circ} C/2$$

$$T_{\text{film}} = 18.35^{\circ} \text{ C}$$

$$k = 0.0645 \text{ W/m K}$$

## 7. To Calculate the Vertical Length Based Nusselt Number, Nu1

$$Nul = h * L1/k$$

$$Nul = 114.342 * 24E-3/0.0645$$

$$Nul = 42.54$$

## 8. To Calculate the Ratio Area/Perimeter Based Nusselt Number, Nu2

$$L2 = \Sigma(A(i)/P(i))$$

$$L2 = (24 * 8)/64 + (2 * 8 * 6)/(2 * 14) + (2 * 24 * 6)/(2 * 60)$$

$$L2 = 11.229E-3 \text{ m}$$

$$L2 = 19.905$$

9. To Calculate the Density of the FC-75, p (Kg/m<sup>3</sup>)

$$\rho = (1.825 - 0.00246 * T_{film}) * 1000$$

$$\rho = 1779.86 \text{ Kg/m}^3$$

10. To Calculate the FC-75 Specific Heat, Cp (J/Kg K)

$$Cp = (.241111 + 3.7037E-4 * T_{film}) * 4180$$
  
 $Cp = 1036.25 \text{ J/Kg K}$ 

11. To Calculate the FC-75 Viscosity,  $v(m^2/s)$ 

$$v = (1.4074 - 2.964E-2 * T_{film} + 3.8018E-4$$
 
$$* T_{film}^2 - 2.7308E-6 * T_{film}^3 + 8.1679E-9 * T_{film}^4)E-6$$
 
$$v = .97557E-6 \text{ m}^2/\text{s}$$

12. To Find the FC-75 Thermal Expansion Coefficient,  $\beta(K^{-1})$ 

$$\beta = 0.00246/(1.825 - 0.00246 * T_{\rm film})$$

For 1.1 W and component 3:

$$\beta = 1.382E-3 K-1$$

13. To Calculate the FC-75 Thermal Diffusivity  $\alpha(m^2/s)$ 

$$\alpha = k/\rho * Cp$$

For 1.1 W and component 3:

$$\alpha = 3.497E-8 \text{ m}^2/\text{s}$$

14. To Calculate the Grashof Number

$$Gr = g * \beta * 1^3 * \Delta T/v^2$$

For 1.1 W and component 3:

15. To Calculate the Prandtl Number

$$Pr = v/\alpha$$

$$Pr = 27.89$$

16. To Find the Temperature Based Rayleigh Number

$$Ra = Gr * Pr$$

For 1.1 W and component 3:

$$Ra = 9.08E7$$

17. To Calculate the Flux Based Rayleigh Number

$$Ra_f = g * B * 1^4 * Q_{net}/(k * v * \alpha * A_{tot})$$

$$Ra_f = 3.9E9$$

### APPENDIX B

#### **UNCERTAINTY ANALYSIS**

The uncertainty analysis was done using the method of Kline and McClintock, presented in Holman [Ref. 15]. The calculations will be done for the end values 0.1 W and 3.0 W, for a chamber width of 30 mm.

#### A. UNCERTAINTIES IN THE NET POWER ADDED TO THE FLUID

$$Q_{net} = Power - Q_{loss}$$

Power = 
$$emf(I) * (Volt - emf(I))/Rp$$

Power = 
$$f(emf(l), Volt, Rp)$$

$$\frac{\partial \text{Power}}{\partial \text{emf(1)}} = \frac{\text{Volt} - 2 \cdot \text{emf(1)}}{\text{Rp}}$$

$$\frac{\partial \text{Power}}{\partial \text{Volt}} = \frac{\text{emf(I)}}{\text{Rp}}$$

$$\frac{\partial \text{Power}}{\partial \text{Rp}} = -\frac{\text{emf(I)} \cdot (\text{Volt} - \text{emf(I)})}{\text{Rp}^2}$$

$$W_{\text{power}} = \left[ \left( \frac{\partial_{\text{power}}}{\partial_{\text{emf(I)}}} \right)^{2} W_{\text{emf(I)}}^{2} + \left( \frac{\partial_{\text{power}}}{\partial_{\text{Volt}}} \right)^{2} W_{\text{Volt}}^{2} + \left( \frac{\partial_{\text{power}}}{\partial_{\text{Rp}}} \right)^{2} W_{\text{Rp}}^{2} \right]^{\frac{1}{2}}$$

$$W_{\rm emf} = 0.001 \ {
m V}$$

(by Resolution in the reading and precision of measuring devices)

$$W_{\text{Volt}} = 0.001 \text{ V}$$

(by Resolution in the reading and precision of measuring devices)

$$W_{\rm Rp} = 0.05~\Omega$$

(including the added resistances)

For 0.1 W and chip 3:

$$emf(I) = 1.022 V$$

$$Volt = 1.225 V$$

$$Rp = 2.06 \Omega$$

(measured resistance including resistances in the junctions, etc.)

$$\frac{\partial Power}{\partial emf(1)} = -0.397$$

$$\frac{\partial \text{Power}}{\partial \text{Volt}} = 0.496$$

$$\frac{\partial \text{Power}}{\partial \text{Rp}} = -0.0488$$

$$W_{\text{power}} = \left[ (-0.397)^{2} \cdot (0.001)^{2} + (0.496)^{2} \cdot (0.001)^{2} + (-0.0488)^{2} \cdot (0.05)^{2} \right]^{\frac{1}{2}}$$

$$W_{power} = 0.00252 \text{ W}$$

$$\frac{W_{\text{power}}}{\text{Power}} = \frac{0.00252 \text{ W}}{0.1 \text{ W}} = 2.5 \%$$

$$Q_{loss} = \frac{\Delta T}{RC}$$

where  $\Delta T$  is the difference in temperature between the back surface of the chip and the back of the board.

$$Q = f(\Delta T, Rc)$$

$$\frac{\partial Q_{loss}}{\partial \Delta T} = \frac{1}{Rc} = \frac{Q_{loss}}{\partial Rc} = \frac{\Delta T}{Rc^2}$$

For 0.1 W and component 3:

$$\frac{\partial Q_{loss}}{\partial \Delta T} = \frac{1}{520.83 \text{ K/W}} = 0.00192$$

$$\frac{\partial Q_{loss}}{\partial Rc} = -\frac{0.12^{\circ} K}{(520.83)^{2}} = -4.424 \times 10^{-7}$$

$$WQ_{loss} = \left[ \left( \frac{l}{Rc} \right)^2 W_{\Delta T} + \left( \frac{-\Delta T}{Rc^2} \right) W_{Rc} \right]$$

$$W_{\Delta T} = 10\% = 0.012^{\circ} \text{ C}$$

$$W_{Rc} = 10\% = 52.083 \text{ K/W}$$

$$WQ_{loss} = \left[ (0.00192)^{2} \cdot 0.012^{2} + (-4.424 \times 10^{-7})^{2} \cdot (52.083)^{2} \right]^{\frac{1}{2}}$$

$$WQ_{loss} = (5.352 \times 10^{-10})^{\frac{1}{2}} = 3.258E-5$$

$$\frac{WQ_{loss}}{Q_{loss}} = 0.14 = 14\%^{1}$$

$$WQ_{\text{net}} = \left[ \left( W_{\text{power}} \right)^2 + \left( WQ_{\text{loss}} \right)^2 \right]^{\frac{1}{2}}$$

$$WQ_{\text{net}} = \left[ (0.00252)^2 + (3.258 \times 10^{-5})^2 \right]^{\frac{1}{2}}$$

$$WQ_{\text{net}} = \pm 0.025 \text{ W}$$

$$\frac{WQ_{\text{net}}}{Q_{\text{net}}} = \pm 2.5\%$$

<sup>&</sup>lt;sup>1</sup>The uncertainties in the losses are relatively big, but they do not have a large effect on the final undertaking.

## For 3.0 W and component 3:

emf(I) = 
$$5.647 \text{ V}$$
  
Volt =  $6.762$   
Rp =  $2.06\Omega$ 

$$\frac{\partial \text{Power}}{\partial \text{emf(I)}} = -2.2$$

$$\frac{\partial \text{Power}}{\partial \text{Volt}} = 2.74$$

$$\frac{\partial \text{Power}}{\partial \text{Rp}} = 1.484$$

$$W_{\text{power}} = \left[ (-2.2)^2 \cdot (0.001)^2 + (2.74)^2 \cdot (0.001)^2 + (1.484)^2 \cdot (0.05)^2 \right]^{\frac{1}{2}}$$

$$W_{\text{power}} = 0.74 \text{ W}$$

$$\frac{W_{\text{power}}}{\text{power}} = \frac{0.074}{3.0} = \pm 2.5\%$$

$$\frac{\partial Q_{loss}}{\partial \Delta T} = \frac{1}{520.83} k/w = 0.00192$$

$$\frac{\partial Q_{loss}}{\partial Rc} = -\frac{21.68}{(520.83)^2} = -7.993E - 5$$

$$WQ_{loss} = \left[ (0.00192^{2} \cdot (2.168)^{2} + (-7.992E - 5)^{2} \cdot (52.083)^{2} \right]^{\frac{1}{2}}$$

$$WQ_{loss} = 0.059 \text{ W}$$

$$\frac{WQ_{loss}}{Q_{loss}} = 14.14\%$$

$$WQnet = \left[ \left( W_{power} \right)^{2} + \left( WQ_{loss} \right)^{2} \right]^{\frac{1}{2}}$$

$$WQnet = \left[ (0.074)^{2} + (0.0059)^{2} \right]^{\frac{1}{2}}$$

$$WQ_{\text{net}} = \pm 0.0742 \text{ W}$$

$$\frac{WQ_{\text{net}}}{Q_{\text{net}}} = \pm 2.5\%$$

### B. UNCERTAINTY IN RAYLEIGH AND NUSSELT NUMBERS

Starting with:

$$Q_{net} = hA_{tot} (T_{avg} - T_{sink})$$

$$h = \frac{Q_{net}}{A_{tot}(T_{avg} - T_{sin k})}$$

$$h = f(Q_{net}, A_{tot}, \Delta T)$$

$$\frac{\partial h}{\partial Q_{\text{net}}} = \frac{1}{A_{\text{tot}}(\Delta T)}$$

$$\frac{\partial h}{\partial A_{tot}} = \frac{Q_{net}}{A_{tot} (\Delta T)^2}$$

$$\frac{\partial h}{\partial \Delta T} = \frac{Q_{\text{net}}}{A_{\text{ret}} (\Delta T)^2}$$

for 0.1 W and component 3:

$$A_{tot} = 5.76 \times 10^{-4} \text{m}^2$$
 (for all components)

$$\frac{\partial h}{\partial Q_{\text{not}}} = \frac{1}{(5.76 \times 10^{-4})(3.02)} = 574.87$$

$$\frac{\partial h}{\partial A_{tot}} = \frac{0.1}{(5.76 \times 10^{-4})(3.02)} = -99804.03$$

$$\frac{\partial h}{\partial \Delta T} = -\frac{-0.1}{(5.76 \times 10^{-4})(3.02)^2} = -19.035$$

$$Wh = \left[ \left( \frac{\partial h}{\partial Q_{\text{net}}} \right)^2 W Q_{\text{net}}^2 + \left( \frac{\partial h}{\partial \Delta_{\text{tot}}} \right)^2 W_{A_{\text{tot}}}^2 + \left( \frac{\partial h}{\partial \Delta T} \right)^2 W_{\Delta T}^2 \right]^{\frac{1}{2}}$$

$$WQ_{\text{net}} = \pm 0.0025 \text{ W}$$

$$W_{\rm L} = \pm 10^{-5} {\rm m}$$

$$W_{\rm A} = \left[ \left( 10^{-5} \right)^2 + \left( 10^{-5} \right)^2 \right]^{\frac{1}{2}} = 1.4 \, \text{1E } -5 \, \text{m}^2$$

$$W_{\Delta T} = \pm 1\% = 0.03^{\circ} \text{ C}$$

$$W_{h} = \left[ (574.87)^{2} \cdot (0.0025)^{2} + (99804)^{2} \cdot (1.4 \text{ lE } -5)^{2} + (19.035)^{2} \cdot (0.03)^{2} \right]^{\frac{1}{2}}$$

$$W_{\rm h} = (2.065 + 0.019 + .3260)^{\frac{1}{2}}$$

$$= \pm 2.09 \text{ W/m}^2 \text{ K}$$

$$\frac{W_h}{h} = \frac{2.09}{57.487} = \pm 3.64\%$$

For 3.0 W and component 3:

$$\frac{\partial h}{\partial Q_{\text{net}}} = \frac{1}{(5.76 \times 10^{-4})(38.38)} = 45.52$$

$$\frac{\partial h}{\partial A_{tot}} = \frac{3.0}{(5.76 \times 10^{-4})^2 (38.38)} = 235597.84$$

$$\frac{\partial h}{\partial \Delta T} = \frac{3.0}{(5.76 \times 10^{-4})(38.38)^2} = 3.536$$

$$W_{h} = \left[ (45.52)^{2} \cdot (0.0742)^{2} + (235597.8)^{2} \cdot (1.4 \text{ IE } -5)^{2} + (3.54)^{2} \cdot (.38)^{2} \right]^{\frac{1}{2}}$$

$$W_{\rm h} = \pm 4.92 \text{ w/m}^2 \text{ K}$$

$$\frac{W_h}{h} = \frac{4.92}{135.7} = 3.63\%$$

To find the uncertainty of Nusselt Number:

$$Nu = \frac{h_L}{k}$$

$$Nu = f(h, L, k)$$

$$\frac{\partial Nu}{\partial h} = \frac{L}{k}$$

$$\frac{\partial Nu}{\partial L} = \frac{h}{k}$$

$$\frac{\partial Nu}{\partial k} = -\frac{hL}{k^2}$$

Since the thermal properties of the FC-75 (dielectric liquid) are values that depend on film temperatures, it is considered that there are no uncertainties in these values.

$$K = (0.65 - 7.89474E - 4 \cdot T_{film})/10$$

$$T_{\text{film}} = \frac{T_{\text{avg}} + T_{\sin k}}{2}$$

For 0.1 W and component 3:

$$K = 0.064 \frac{W}{m \ K}$$

$$T_{film} = 11.51^{\circ} C$$

$$\frac{\partial \text{Nu}}{\partial k} = \frac{24 \times 10^{-3} \text{m}}{0.064 \text{ w/m K}} = 0.374$$

$$\frac{\partial Nu}{\partial k} = \frac{57.487}{24 \times 10^{-3}} = 2395.29$$

$$\frac{\partial \text{Nu}}{\partial \text{k}} = \frac{57.487 \times 24 \times 10^{-3}}{(0.064)^2} = 336.84$$

$$WNu = \left[ \left( \frac{\partial Nu}{\partial h} \right)^2 Wh^2 + \left( \frac{\partial Nu}{\partial L} \right)^2 W_L^2 + \left( \frac{\partial Nu}{\partial k} \right)^2 Wk^2 \right]^{\frac{1}{2}}$$

$$WNu = \left[ (0.374)^{2} \cdot (2.09)^{2} + (2395.29)^{2} \cdot (10^{-5})^{2} \right]^{\frac{1}{2}}$$

$$WNu = \pm 0.78$$

$$\frac{W\text{Nu}}{\text{Nu}} = \frac{0.78}{21.55} = 0.036 = 3.6\%$$

For 3.0 W and component 3:

$$k_f = 0.0627 \frac{W}{m k}$$

$$T_{\text{film}} = 29.2^{\circ} \text{ C}$$

$$\frac{\partial \text{Nu}}{\partial \text{h}} = \frac{24 \times 10^{-3} \text{m}}{0.0627} = 0.382$$

$$\frac{\partial Nu}{\partial L} = \frac{135.7}{24 \times 10^{-3}} = 5654.16$$

WNu = 
$$\left[ (0.382)^2 \cdot (4.92)^2 + (5654.16)^2 \cdot (10^{-5})^2 \right]^{\frac{1}{2}}$$

$$WNu = \pm 1.88$$

$$\frac{WNu}{Nu} = \frac{1.88}{51.94} = 3.62\%$$

$$Ra_f = Gr_f \cdot Pr$$

$$Gr_f = \frac{g\beta L^4 Q_{net}}{k_f v^2 A_{tot}}$$

$$Pr = \frac{v}{\alpha}$$

$$Gr_f = f(g,\beta,L^4,Q_{net},k_f,v^2,A_{tot})$$

Consider fluid properties without uncertainties.

$$\frac{\partial Gr_f}{\partial L^4} = \frac{g\beta Q_{\text{net}}}{k_f v^2 A_{\text{tot}}}$$

$$\frac{\partial Gr_f}{\partial Q_{\text{net}}} = \frac{g\beta L^4}{k_f v^2 A_{\text{tot}}}$$

$$\frac{\partial Gr_f}{\partial A_{tot}} = \frac{g\beta L^4 Q_{net}}{k_f v^2 A_{tot}^2}$$

For 0.1 W and component 3:

$$\beta = 0.00137 \text{ K}^{-1}$$

$$k_f = 0.064 \frac{W}{m.k}$$

$$v = 1.11259E-6\frac{m^2}{s}$$

$$\frac{\partial Gr_f}{\partial L^4} = 2.94E13$$

$$\frac{\partial Gr_f}{\partial Q_{net}} = 9.76E7$$

$$\frac{\partial Gr_f}{\partial A_{tot}} = -1.69E10$$

$$WGr_{f} = \left[ \left( \frac{\partial Gr_{f}}{\partial L^{4}} \right)^{2} W^{2} L^{4} + \left( \frac{\partial Gr_{f}}{\partial Q_{\text{net}}} \right)^{2} W^{2} Q_{\text{net}} + \left( \frac{\partial Gr_{f}}{\partial A_{\text{tot}}} \right)^{2} WA_{\text{tot}} \right]^{\frac{1}{2}}$$

$$WGr_f = \left[ \frac{(2.94E13)^2 \cdot (5.5 E-10)^2 + (9.76E7)^2 \cdot (0.0025)^2}{+ (1.69E10)^2 \cdot (4.8 E-7)^2} \right]^{\frac{1}{2}}$$

$$WGr_f = [2.6E8 + 5.9536E10 + 6.5E7]^{\frac{1}{2}}$$

$$W_{\rm Gr_f} = \pm 243569$$

$$\frac{W_{Gr_f}}{Gr_f} = \frac{243569}{9.67E6} = 2.5\%$$

$$W_{\text{Ra}_{\text{f}}} = 2.5\%$$

For 3.0 W and component 3:

$$\beta = 0.014 \text{ K}^{-1}$$

$$v = 0.80402 \times 10^{-6} \frac{\text{m}^2}{\text{S}}$$

$$k_f = 0.0627 \frac{W}{m.K}$$

$$\frac{\partial Gr_f}{\partial L^4} = 17.6E15$$

$$\frac{\partial Gr_f}{\partial Q_{\text{net}}} = 19.5E7$$

$$\frac{\partial Gr_{f}}{\partial A_{tot}} = 1.0E12$$

$$WGr_{f} = (17.6E15)^{2} + (5.5E-10)^{2} + (19.5E7)^{2} + (0.0742)^{2} + (1.0E12)^{2} + (4.8E-7)^{2}$$

$$WGr_f = [9.3E13 + 2.09E14 + 2.38E11]^{\frac{1}{2}}$$

$$\frac{WGr_f}{Gr_f} = \frac{17405183}{584920180} = 2.9\%$$

$$W_{Raf} = 2.9\%$$

#### APPENDIX C

#### **TABLES**

### TABLE 1

# TEMPERATURE DATA FOR INPUT POWER 0.1 W BOTTOM BOUNDARY AT 20° C

RESULTS HERE STORED IN FILE: 08021485

PMFIENT TEMP : [4.3 C POLIMETER PEAKING : 1.705 V HEAT EXCHAUGER TEMP.: 10-20 C

ALL TEMPERATURES ARE IN DEGREES CELCIUS

	CENTER	10P	BIGHT	LEFT	BOTTOM	Bedi
: HIP NOT:	17.46E+00 (WATTS):	17.49E+00 10.01E-02	17.48E+H0	17.47E+00	17.54E+90	18.94E+99
- HIR MQ2: POWEE	17,40E+00 (WATTEY:	17.448+90 10.005-02	17.47E+00	17.41E+00	17.47E+00	17.96E+NA
HIF WYER	17+13E+10 (WATTS):	17.98E+00 33.84E-03	17.16E+00	17.22E+00	17.23E+00	17.51E+00
CHIR MAA: FOWER	17.57E-00 CWATTS::	17.565+00 98.345-03	17.4 <i>n</i> E+00	15.60E+nn	17.48E+00	17.89E •00
CHIR MOS: FONER	17,49E+00 (WATTS):	17.525+00 99.246-03	17.56E+00	17.51E+00	17.586+00	17.925-00
	20.63E+00 (WATTE):	17.39E+00 33.125-03	17,43E+00	17.38E+00	17.558+90	18.42E-00
IP NOZ: PGWEF	17,535.00 (MATT51:	17.62E+00 16.04E-32	17.60E+00	17.558+00	17.74E-00	19,22 <b>E</b> +00
	17.59E+00 (WALTS):	17.646+00 10.87E-02	17.67E+00	17.588+00	17.63E+00	10,275×99
HIF MOR: FOWER	17.33E+00 (NOTTS::	17.158+00 99.325-03	17,34E+00	:7.30E+00	17.362 • 00	17.53E • 60

BOTTOM: 13.97E+00

PH K FLAME TEMPERATURE HARE :

7 (56.1) (7.0% +0.0)
1 (50.1) 18.0 6 + 3.0
1 (57.1) 17.54E +0.0
1 (77.1) 19.0 E +0.0
1 (77.1) 19.0 E +0.0
1 (77.1) 10.0 E +0.0

# TEMPERATURE DATA FOR INPUT POWER 0.7 W BOTTOM BOUNDARY AT 20° C

RESULTS ARE STORED IN FILE: 08021717

AMPIENT TEMP: 24.4 C VOLTMETER READING: 3.213 V HEAT EXCHANGER TEMP: 10-20 C

#### ALL TEMPERATURES ARE IN DEGREES CELCIUS

	CENTER	TOP	RIGHT	LEFT	BOTTOM	BACK.
CHIP NO!: POWER	24.74E+00 (WATTS):	24.02E+00 70.97E-02	23.96E+00	24.00E+00	54.03E+00	27.01E+0A
CHIP NO2: POWER	24.71E+00 (WATTS):	23.91E+00 70.93E-02	23.95E+00	23.54E+00	23.80E÷00	26.568+00
CHIP MO3: POWER	23.93E+00 (WATTS):	23,69E+00 70.79E-02	23.59E+00	23.55E+00	23.60E+00	25.11E-90
CHIP MO4: POWER	24.30E+00 (WATTS):	23.71E+00 76.03E-02	23.60E+00	20.65E+00	23.60E+00	25.74E+0U
CHIP NOS: POWER	24.25E+00 (WATTS):	23.46E+00 70.38E-02	23.44E+U0	20.37E+00	23.69E+00	25.455+00
	25.78E+00 (WATTS):	24.05E+00 70.26E-02	23.44E+00	23.518+00	24.08E+00	27.57E+00
	24.35E+00 (WATTS):	24.47E+90 71.19E-02	24.02E.+00	23.81E+00	24.14E+00	27.5%8+00
	24.27E+00 (WATTS):	24.14E+00 71.40E-02	24.07E+00	23.85E+00	23.79E+00	79.43E+13
	23.90E+00 (WATTS):	23.70E+00 70.84E-02	23.62E+00	23.508+00	23.44E+00	26.7HE+9H

AMERAGE HEAT EXCHANGERS TEMPERATURES: 10.00E+80 TOP: 20.00E+80

#### BACK PLANE TEMPERATURES ARE :

T(55): 20.83E+00 T(56): 21.22E+00 T(57): 20.72E+00 T(72): 21.38E+00 T(73): 21.10E+00 T(74): 21.50E+00 T(75): 21.03E+00 T(76): 21.18E+00 T(77): 21.23E+00

# TEMPERATURE DATA FOR INPUT POWER 1.5 W BOTTOM BOUNDARY AT 20° C

RESULTS ARE STORED IN FILE: 08030205

AMFIEUT TEMP : 24.4 ° VOLTMETER READING : 4.7082 V HEAT EXCHANGER TEMP.: 10-20 C

#### ALL TEMPERATURES ARE IN DEGREES CELCIUS

	CENTER	TOP	RIGHT	LEFT	BOTTOM	BACK
	33.28E+00 (WATTS):	31.29E+00 15.17E-01	31.67E+00	31.83E+00	31.81E+00	37.53E+00
	33.22E+90 (MATTS):	31.21E+00 15.16E-01	31.50E+00	30.688+00	31.25E+00	36.83E+00
		31.25E+00 15.13E-01	30.99E+00	30.7 <b>6E+</b> 00	30.63E±00	34.16E+90
CHIP MO4: FOWER	33.06E+00 (WATTS):	31.52E+00 14.38E-01	31.54E+00	27.88E+00	31.60E+00	35.83E+00
CHIP NOS: POWER	32.56E+00 (MATTS):	30.25E+00 15.04E-01	30.505+00	30.44E+00	31.30E+00	34.65E+A0
	20.87E+00 (WATTS):	32.795+00 15.01E-01	00.75E+00	31,13E+00	32.43E+NN	43.50E+00
	30.79E+00 (W4ITS):	32.54E+00 15.21E-01	31.808+00	31.298+00	31.37E+00	33.87E+00
		31.64E+06 15.26E-01	31.72E+00	31.45E+00	31.25E+01	43.11£+ijii
	31.47E+00 (WATTS):	31.25E+00 15.14E-01	31.12E+00	30.90E+0 <b>0</b>	31.01E+00	37.418+00

AVERAGE HEAT EXCHANGERS TEMPERATURES:
80110M: 10.09E+00
70P: 20.04E+90

#### BACK PLANE TEMPERATURES ARE :

T(56): 23.97E+00 T(56): 24.51E+00 T(57): 25.06E+00 T(72): 24.93E+00 T(73): 24.57E+00 T(74): 24.85E+00 T(75): 25.10E+00 T(76): 24.49E+00 T(77): 24.61E+00

# TEMPERATURE DATA FOR INPUT POWER 3.0 W BOTTOM BOUNDARY AT 20° C

REBULTS ARE STURED IN FILE: 08041795

AMBIENT TEMP: 24.5 C VOLTMETER READING: 6.601 V HEAT EXCHANGER TEMP: 10-20 C

### ALL TEMPERATURES ARE IN DEGREES CELCIUS

	CENTER	10b	RIGHT	LETT	BOTTOM	BACK
CHIP NO1: POWER	49.47E+00 (WATTS):	45.65E+00 29.74E-01	46,44E+01)	46.13E+00	45.75E+00	56.26E+00
CHIP NO2: POWER	48.99E+00 (WATTS):	45.37E+00 29.73E+01	46.33E+00	44.51E+90	46.02E+00	56.925+90
CHIP NO3: POWER		45.57E+00 29.68E-01	45.04E+00	44.58E+00	44.60E+00	51,20E+00
CHIP NO4: POWER	49.59E+00 (WATTS):	46.17E+00 29.38E-01	46.77E+00	42.62E+00	46.97E+00	54.89E+00
CHIP MOS: POWER	48.59E+00 (WATTS):	43.32E+00 23.51E-01	45.13E+00	44.75E+00	46.43E+00	52.53E+00
CHIP NO6: POWER	37.90E+00 (WATTS):	48.64E+00 23.40E-01	45.04E+00	45.78E+00	47.85E+00	68.62E+9U
'IF NO7: POWER	51.18E+00 (WATTS):	48.27E+00 29.82E-01	47.495+00	46.51E+00	47.28E+00	\$5.40F+90
	42.93E+A0 (WATTS):	47.05E+00 29.31E-01	47.09E+00	46.58E+90	45.33E+0N	67.34E+00
	44.37E+00 (WATT5):	45.78E+00 29.69E-01	45.57E+00	45.11F+00	44.73E+00	58.25E+U0

AVERAGE HEAT EXCHANGERS TEMPERATURES:
BOTTOM: 10.38E+00
TOP: 20.08E+00

### BACK PLANE TEMPERATURES ARE :

T(55): 31.46E+00 T(56): 32.62E+00 T(57): 34.30E+00 T(72): 33.38E+00 T(73): 32.78E+00 T(74): 33.27E+00 T(75): 33.39E+00 T(76): 32.43E+00 T(77): 32.42E+00

# REDUCED DATA FOR INPUT POWER 0.1 W BOTTOM BOUNDARY AT 20° C

THE SAN EAR DATA ARE FROM THE FILE: 03021455 THE FONER SETTING PER CHIP NAS: 0.1 N

HHE	QNET(W)	lavo-ls	140	zunc In 🖘
•	39.93E-03 TEMPERATURE BASED % UNCERTAINTY IN FLUX BASED RAYLEI % UNCERTAINTY IN	THE TEMPERATURE GH NUMBER + E-8	+ E-7 IS: 13 BASED RAYLEIGH IS: 406.58E-0	4 NUMBER IS :134.16E-02 14
2	99.54E-03 TEMPERATURE BASEL % UNCERTAINTY IN FLUX BASED RAYLED % UNCERTAINTY IN	THE TEMPERATURE [GH NUMBER * E-8]	BASED RAYLEIGH IS: 405.97E-	38.74E-03 4 NUMBER IS :105.03E-02 14
<u>.</u>	99.64E-03 TEMPERATURE BASED % UNCERTAINTY IN FLUX TASED RAYLES % UNCERTAINTY IN	THE TEMPERATURE GH NUMBER * E-8	BASED RAYLEIGH IS: 403.97E-4	73.57E-03 + NUMBER IS :133.85E-00 14
4	TEMPERATURE BASED	) RAYLEIGH NUMBER THE TEMPERATURE [GH NUMBER ← E-8	BASED RAYLEIGH IS: 399.29E-0	HINUMBER IS :142.58E-02 94
5	TEMPERATURE BASEL	THE TEMPERATURE GH NUMBER + E-8	* E-7 IS: 1/ BASED RAYLEIGH IS: 403.22E-6	00.78E-03 4 NUMBER IS :133.03E-90 94
Ę	TEMPERATURE BASED	THE TEMPERATURE GH NUMBER * E-8	→ E-7 IS: 17 BASED RAYLEIGH IS: 410.50E-6	74.756-03 KINUMBER IC :109.295 03 74
7	TEMPERATURE BASED	THE TEMPERATURE GH NUMBER * E-8	* E-7 IS: 10 BASED RAYLEIGH IS: 408.40E-0	:2.19E-03 H NUMBER IS :132.01E-03 14
3	10.05E-02 TEMPERATURE BASET % UNCERTAINTY IN FLUX BASED RAYLET % UNCERTAINTY IN	RAYLEIGH NUMBER THE TEMPERATURE GH NUMBER * E-8	→ E-7 IS: 14 BASED RAYLEIGH IS: 409.59E-0	HINUMBER IS :131.78E-02 14
ā	99.72E-03 TEMPERATURE BASED % UNCERTAINTY IN FLUX BASED RAYLEI % UNCERTAINTY IN	RAYLEIGH NUMBER THE TEMPERATURE GH NUMBER + E-8	* E-7 IS: 13 BASED RAYLEIGH IS: 404.94E-0	26.42E-03 H NUMBER IS :137.15E-07 14

# REDUCED DATA FOR INPUT POWER 0.7 W BOTTOM BOUNDARY AT 20° C

THE RAW EMF DATA ARE FROM THE FILE: 08021717
THE POWER SETTING PER CHIP WAS: 0.7 WATTS

JEIP	ONET (W)	Tavg-Ts	flu	WONC IN No
1	TEMPERATURE BASEL % UNCERTAINTY IN FILIX BASED RAYLET	14.24E+00 ) RAYLEIGH NUMBER THE TEMPERATURE B IGH NUMBER * E-8 I' FLUX BASED RAYLEI	+ E-7 IS: 29) ASED RAYLEIGH S: 308.85E-0)	7.08E-03   NUMBER   IS   :703.04E-03 
2	% UNCERTAINTY IN	14.08E+00 D RAYLEIGH NUMBER THE TEMPERATURE BO IGH NUMBER ➤ E-3 IN FLUX BASED RAYLEIO	* E-7 IS: 28. ASED RAYLEIGH S: 308.10E-0.	3.28E-03 NUMBER IS :711.21E-03 3
3	% UNCERTAINTY IN FLUX RASED RAYLE!	13.66E+00 RAYLEIGH NUMBER THE TEMPERATURE B IGH NUMBER * E-8 I FLUX BASED RAYLEI	+ E-7 IS: 271 ASED RAYLEIGH S: 306.03E-0	7.69E-03   NUMBER IS :732.84E-03 
4	TEMPERATURE BASEL % UNCERTAINTY IN FLUX BASED RAYLE	I3.10E+00 D RAYLEIGH NUMBER THE TEMPERATURE BO IGH NUMBER * E-8 I FLUX BASED RAYLEIG	* E-7 IS: 25 ASED RAYLEIGH S: 301.00E-0	NUMBER IS :/64,356-93   3
5	TEMPERATURE BASEL % UNCERTAINTY IN FLUX BASED RAYLE	13.71E+00 D PAYLEIGH NUMBER THE TEMPERATURE B IGH NUMBER * E-8 I FLUX BASED RAYLEI	* E-7 IS: 274 ASED RAYLEIGH S: 204.27E-01	NUMBER IS :730,236-01. 3
5	TEMPERATURE BASE! % UNCERTAINTY IN FLUX BASED RAYLE	14.67E+00 D RAYLEIGH NUMBER THE TEMPERATURE B IGH NUMBER * E-8 I FLUX BASED RAYLEI	→ E-7 I5: 29 ASED RAYLEIGH S: 307.22E-0	7.03E-03  NUMBER IS :582.63E 95
7	TEMPERATURE BASEL % UNCERTAINTY IN FLUX BASED RAYLE	14.32E+00 D RAYLEIGH NUMBER THE TEMPERATURE B IGH NUMBER * E-8 I FLUX BASED RAYLEI	+ E-7 IS: 284 ASED RAYLEIGH S: 310.07E-03	NUMBER IS :639.10E-03. 3
9	TEMPERATURE BASES % UNCERTAINTY IN FILIX BASED RAYLE	14.06E+00 D RAYLEIGH NUMBER THE TEMPERATURE B IGH NUMBER * E-8 I FLUX BASED RAYLEI	* E-7 IS: 28 ASED RAYLEIGH S: 310.07E-0	NUMBER 15 ://2.1/E-03
ġ	TEMPERATURE BASEL % UNCERTAINTY IN FLUX BASED RAYLE	13.67E+00 D RAYLEIGH NUMBER THE TEMPERATURE B IGH NUMBER * E-8 I FLUX BASED RAYLEI	* E-7 IS: 27 ASED RAYLEIGH 5: 306.23E-0	3.90E-03   NUMBER IS :732.34E-03 

# REDUCED DATA FOR INPUT POWER 1.5 W BOTTOM BOUNDARY AT 20° C

THE ROW EAR DATA ARE FROM THE FILE: 08030205 THE POWER SETTING PER CHIP WAS: 1.5 WATTS

	THE PO	HER SETTING PER CH	IP WAS: 1.5	WATIS
this	OHE LCH)	Tavg-Ts	Du	winc In his
î	% UNCERTAINTY IN T	DAZI ETCH HIMBER 4	ED RATLEIGH NU 722.22E-03	5E-03 MBER IS :453.37E-0?
2	% UNCERTAINTY IN T	DAYLETCH NUMBER +	ED RATLEIGH NU 719.11E-03	RE-03 MBER IS :460.71E-03
?	W UNCERTAINTY IN	DAYLETCH HUMBER +	711.25E-03	0E-03 MBER IS :478.68E-03
á	" UNCERTAINTY IN TO THE POST OF THE	21.04E+00 RAYLEIGH NUMBER * THE TEMPERATURE BAS HH NUMBER * E-P IS: FLUX BASED RAYLEIGH	E-7 IS: 457.0 ED RAYLEIGH NU 705.05E-03	MBER IS :475.76E-03
Ę,	. % UNCERTAINTY IN	21.15E+DD RAYLEIGH NUMBER + THE TEMPERATURE BAS SH NUMBER + E-P IS: FLUX BASED RAYLEIGH	E-7 IS: 459.8 ED RAYLEIGH NU 708.81E-03	MEER IS :472.296-03
i,	TEMPERATURE BASED to UNICERTATUTY IN FILLY BASED RAYLET	17.77E+00 RAYLEIGH NUMBER * THE TEMPERATURE BAS GH NUMBER * E-8 IS: FLUX BASED RAYLEIGH	E-7 15: 372.7 ED RAYLEIGH MU . 680.72E-03	56.38E 02 79E-03 MMBER IS :563.375-02 227.65E-04
7	TEMPERATURE BASED  Z UNCERTAINTY IN FLUX BASED RAYLET	22.33E+00 RAYLEIGH NUMBER * THE TEMPERATURE BAS GH NUMBER * E-8 IS: FLUX BASED RAYLEIGH	E-7 IS: 491.4 GED RAYLEIGH NU : 726.23E-03	44.90E-02 19E-03 JMBER IS :448.39E-03 224.56E-04
8	TEMPERATURE BASED  X UNCERTAINTY IN  ELLY BASEN BAYLET	21.76E+00 RAYLEIGH NUMBER + THE TEMPERATURE BAS GH NUMBER + E-8 IS: FLUX BASED RAYLEIGH	E-7 15: 476. SED RAYLEIGH NU : 723.92E-03	JMBER 15 :460.086-03
3	Z UNCERTAINTY IN	DAYLETCH NUMBER *	5ED RAYLEIGH NO • 712.92E-03	MBER 12 .4/2.220 0.

# REDUCED DATA FOR INPUT POWER 3.0 W BOTTOM BOUNDARY AT 20° C

THE ROW EMF DOTA ARE FROM THE FILE: 090/41705 THE FUNER SETTING PER CHIP NAS: 3.0 MATTS

	:rit r	CMER BELLING LEW S	. 111 1111011		
	ONETCHY	Tavg~Ta	No	Minic Itt Ta	,
1	% UNCERTAINTY IN	36.28E+00 RAYLEIGH NUMBER + THE TEMPERATURE BA GH NUMBER + E-S IS FLUX BASED RAYLEIG	• E-7 IS: 936 ASED RAYLEIGH S• 168.286-02	)	3
2	% UNCERTAINTY IN	35.66E+00 RAYLEIGH NUMBER ( THE TEMPERATURE BA GH NUMBER * E-8 IS FLUX BASED RAYLEIG	95ED RATLE16A S: 167.20E-02	5.94E-03 NUMBER IS :290.60E-0 2	3
\$	. INCERTAINTY IN	33.82E+NN ) RAYLEIGH NUMBER   THE TEMPERATURE BI   IGH NUMBER * E-8 I   FLUX BASED RAYLEI	95ED RAYLEIGH 5: 183.66E-03	0,29E-03   NUMBER IS :296.05E-0 2	3
۲۱	" UNCERTAINTY IN	25.66E+00 RAYLEIGH NUMBER THE TEMPERATURE B IGH NUMBER + E-8 I FLUX BASED RAYLEIG	* E-7 IS: 919 ASED RAYLEIGH S: 165.19E-00	5.27E-03  NUMBER IS :290.75E-0  2	3
5	" UNCERTAINTY IN	35.27E+00 RAYLEIGH NUMBER THE TEMPERATURE B IGH NUMBER * E-8 I FLUX BASED RAYLEI	* E-7 IS: 90 ASED RAYLEIGH 5: 165.19E-0	1.625-03   NUMBER IS :290.895-0 2	( );
6	TEMPERATURE BASE % UNCERTAINTY IN	32.37E+00 D RAYLEIGH NUMBER THE TEMPERATURE B IGH NUMBER * E-8 I FLUX BASED RAYLEI	* E-7 IS: 80 ASED RAYLEIGH S: 159.62E-0	4.05E-03   NUMBER IS :309.21E-0 2	٤١
7	" UNCERTAINTY IN	N DAVECTOU NUMBER	* E-7 IS: 98 ASED RAYLEIGH S* 170.99F-0	1,44E-03   NUMBER*IS :256,69E-0 2	) }
8	WUNCERTAINTY IN	D DAVETCH MIMPER	* E-7 IS: 93 ASED RAYLEIGH S: 169.15E-0	4.88E-03   NUMBER IS :276.38E-0  2	13
9	" UNCERTAINTY IN	D DAVLETCH NUMBER	* E-7 IS: 86 MASED RAYLEIGH S: 164.42E-0	6.10E-03   NUMBER IS :292.51E-1  2	)3

# TEMPERATURE DATA FOR INPUT POWER 0.1 W BOTTOM BOUNDARY INSULATED

THERE SERVETS ARE STORED IN FILE: DECORDES

AMPIENT TEME NAS: 23.0 ( USE METER PERING NAS: 1.2134 V JUNY 2 () : SAN 9M2T HTES

ALL TEMPERATURES ARE IN DEGREES CELCIUS

	CENTER	105	RIGHT	<b>Litt</b>	5011CM	₽.AÇ.⊁
CHIP MOTE POWER	15.83E+00 (WATTS):	00+340.21 50-350.01	15.85E+00	15.92£+90	15.376+00	rg, Grey
CHIF MOS: POWER	15.32E+88 (WATTS):	15.958+00 10.078-12	15.38F+00	15.87E+1111	15,466+00	क्षा, वर्ग २०५०
CHIP NO3:	15.7'E+80 (MATT5):	15.66E÷00 10.05E÷01	1E 134E + UU	1८ ८८६ स्मित्	က ့တွင်ငေ့ နေသ	***
CHIP MOA: POWER	19.775.00 (MATTS):	15.30E+00 33.43E-03	16.27.8.49	the factorial	15,218,600	16.1.1.1.4.5
	15.77E+00 (WATTS):	15,97F+ya 99,88E-03	15,90£+99	15,775.00	15. FE-111	tell of ex
	17.30E+00 (MATTE):	15.73E+08 9+.74E-0	15.778+90	:€,71E+90	12,7%(+0/1	ाक,हिंगु€्रा स
	15.75E+00 (WATTE::	15.23F+94 18.11E-82	15. 758 +an	16,718+00	15.54€ •ाम	telate ess
:80M PINS FINDA	15, 55.00 [###15]:	15. 65.41 10.145-00	15.915.00	15,925+00	40.338+00	*5,5*(***
CHIP 403: POWER	15.575+00 (MAITS):	15.49E+99 18.95E-01	15.825+90	15.59E+05	15.64E+#H	\$5.45f · 8

≀હ્લ⊺	SICHAMGERS BOTTOM: TOP:	TEMPERATURES:	RIGHT 15.27E+00 10.20E+00	

#### BACK PLANE TEMPERATURES ARE :

1(55): 1(56): 1(57): 1(72): 1(74): 1(75):	16.01E+00 16.41E+00 16.01E+00 16.73E+00 16.78E+00 17.24E+00 16.42E+00
1(75):	16.75E+00 16.75E+00

# TEMPERATURE DATA FOR INPUT POWER 0.7 W BOTTOM BOUNDARY INSULATED

THELE RESULTS ARE STORED IN FILE: 08222257

AMPTENT TEMP NAS: 01.00 THETHETER READING WAS: 0.00 V EATH TEMP NAS: 10 C-INS

ALL TEMPERATURES ARE IN DEGREES CELCIUS

	CENTER	TOP	RIGHT	LEFT	BOTTOM	BACK.
		22.35E+00 70.88E-02	22.94E+00	22.84E+00	22.85E+00	25.33E+00
	23.52E+ng (WATTE):	22.57E+00 70.83E-02	22.766+90	22.30E+00	22.588+00	25.39E+00
		20.52E+00 70.53E-02	22.515+00	22.47E+00	22.24E+00	24.008+00
	23.35E+00 (Walib):	22.31E+00 53.33E+02	22.73E+90	22.17E+00	22.67E+00	24.758+90
	23.29£+00 (WAIT:):	22.20E+00 70.28E-02	22.27E+9H	22.14E+00	22.606+00	24.21E+nn
	16.57.400 16.41.000	22.70E-00 70.15E 02	22.23E+00	22.308+00	18.888+00	26.38E+00
	13.75F+90 CWATTEN:	23.15E+01 71.09E-02	22.80E+00	22.60E+00	22.338+00	25.208+00
	23.12E+00 (MATTEL:	71.30E-02	22.85E+HU	22.70[+90	22,608+00	28.666+00
	12.70E+00 (WAT15):	00.48E+00 70.72E-02	22.498+00	22.068+00	22.24E+80	25.80E+00
HEAT E	CYCHANGERS	TEMPERATURE:	S: RIGH	L LEFT		

HEAT EYCHANGERS TEMPERATURES: RIGHT LEFT 17.35E+00 17.35E+00 10.28E+00 37.63E-01

### EACK PLANE TEMPERATURES ARE :

T(5): 19.3%E+00 T(5): 19.81E+00 T(5): 19.74E+00 T(72): 20.01E+00 T(72): 20.01E+00 T(74): 71.3%E-01 T(74): 19.99E+00 T(75): 19.5%E+00 T(75): 19.76E+00 T(77): 19.88E+00

# TEMPERATURE DATA FOR INPUT POWER 1.1 W BOTTOM BOUNDARY INSULATED

THESE RESULTS ARE STORED IN FILE: 08231010

AMBLEHI JEMP WAS: 21.23 C VOLIMETER READING WAS: 4.00 V BATH TEMP WAS: 10 CHINS

#### ALL TEMPERATURES ARE IN DEGREES CELCIUS

	CENTER	105	RIGHT	LEFT	BOITOM	BACK
	28.35E+00 (WATTS):	25.73E+0 <b>0</b> 10.96E-01	27.12E+90	27.11E+00	27.13E+00	30.32E+na
	28.15E+00 (WATTS):	25.70E+00 10.95E-01	25.936+00	26.29E+0U	25.905+00	3 <b>n</b> .97E+40
	28.985+00 (WATTS):	25.97E+00 10.93E-01	26.70 <u>E</u> +nn	26.57E+00	26.26E+00	29.94E+40
	28.21E+00 (WATTS):	27.02E+00 10.82E-01	27.14E+00	26.29E+0#	27.07E+00	30.175+00
	27.75E+00 (WATTS):	25.13E+00 10.87E-01	26.25E+00	26.09E+00	25.868+00	29.208+40
	27.17E+00 (WATTS):	27.20 <u>E+00</u> 10.84E-01	26,33E+mi	26.45E+00	25.8nE+na	32.61E++0
	29.65E+00 (WAITS):	27.60E+00 10.93E-01	27.075+00	26.77E+9n	22.15E+90	31.298+11
THIP MOS: POWER	27.55E+00 (WATTE):	26.33E+00 11.02E-01	27.88 <u>E</u> +89	26.92E+90	26.57E+H0	20.878+03
CHIP NOS: POWER	25.81E+00 (WATTS):	25.65E+00 10.93E-01	26.538+40	26.062+00	26.238+00	De Contracto

HEAT EXCHANGERS TEMPERATURES: BOTTOM: TOP:

RIGHT LEFT 18.43E+00 18.43E+00 10.21E+00 97.3EF-01 \$

#### BACK PLANE TEMPERATURES ALE :

T(55): 21.49E+00 T(55): 22.00F+00 T(57): 22.27E+00 T(72): 22.32E+00 T(73): 21.34E+00 T(74): 22.22E+00 T(75): 22.04E+00 T(76): 21.97E+00 T(77): 22.12E+00

# TEMPERATURE DATA FOR INPUT POWER 3.0 W BOTTOM BOUNDARY INSULATED

THERE RESULTS HAS STORED BY FILE: 08221310

AMBIEUT TEUR HAS: CO C COLTMETOS READING HAS: 4.00 V BATH TEMP HAS: 10 C-105

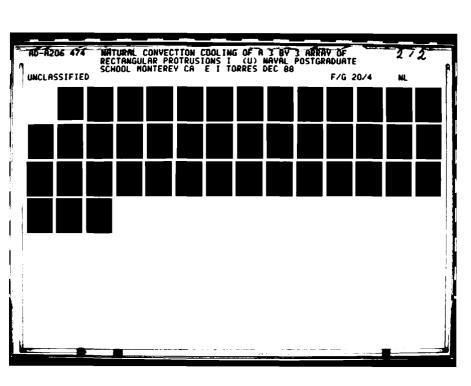
ALL TEMPERATURES ARE IN DEGREES CELCING

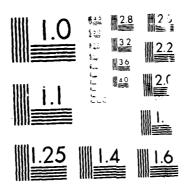
	CENTER	10F	RIGHT	FEET	BOILOM	BPO
	54.235+00 (WATTS):	აც.გგნ+ეე ვი.125-01	50.728+00	50.63E+00	50.34E+00	59.54E+00
	53.84E+00 (H4175):	a9.73€+00 30.11€-01	50.528+00	48.65£+00	50.06E+00	E4.00E+36
	50.25E+00 (HOTTS):	50.05E+00 30.06E-01	49.568+00	49.03E+00	47.38E+00	55.225-8n
	53.56E+00 (WHT15):	49.30E+00 23.77E-01	50.54F+00	48.37E+00	50.35E+df)	59.12E-40
	52.76E+00 (WATTS):	47.94E+00 29.898-01	48.,1E+00	48.29E+00	49.81E+00	စွင့်. ကရုန္ မကု
	55.75E+00 (WATTS):	51.995+89 23.78E-01	48.858+00	49.14E-00	50.78 <b>E</b> +00	ଅପ୍ୟୁଲ୍ଲ ଅନ୍ୟୁଲ୍ଲ ଅନ୍ଲ
:107: F_MO4	55.44€+ûn (WATT§!:	51.67 <b>E</b> +00 30.21 <b>E</b> -01	50.7FE+NO	șa,≀șE+n∩	50.57E+00	83.75F-14
	53.45E+00 (MATIS):	51.07E+00 20.20E-01	51,602+00	50.00E+00	50.316+46	
	En.77E+00 (WATIS):	50.34E+00 30.005-01	49.915+00	a).40E+69	) <u>),59€+00</u>	61,4,8*,5

PEAT EXCHANGERS TEMFERATURES: POTTOM: TOP: RIGHT LEFT 21.94E+9" 21.06E+00 11.02E+00 38.01E+01

#### BACK PLANE TEMPERATURES ARE :

1(55): 32.74E+00 1(56): 34.26E+00 1(57): 36.45E+00 1(72): 35.41E+00 1(70): 34.76E+00 1(74): 35.10E+00 1(75): 35.96E+00 1(76): 34.20E+00 1(77): 34.30E+00





# REDUCED DATA FOR INPUT POWER 0.1 W BOTTOM BOUNDARY INSULATED

THE RAW EAR SATA ARE FROM THE FILE: 08221255
THE FOWER SETTING PER CHIP WAS: 0.1 WATES

THIF	OHET'W)	Tavg-Tg	Nu	AUNC IN Nu	,
1	TEMPERATURE BASEL	THE TEMPERATURE [GH_NUMBER * E-8]	k + E-7 IS: 1 BASED RAYLEIG IS: 401.14E-	08.69E-03 H NUMBER I5 :169.28E 04	E - 0 <i>2</i>
2	!0.05E-02 TEMPERATURE BASE % UNCERTAINTY IN FLUX BASED RAYLE % UNCERTAINTY IN	THE TEMPERATURE IGH NUMBER * E-8	BASED RAYLEIG	H NUMBER IS :166.74E 04	E-02
3	TEMPERATURE BASE!	THE TEMPERATURE  GH NUMBER * E-8	R * E-7 IS: 1 BASED RAYLEIG IS: 399.54E-	07.28E-03 H NUMBER IS :171.38E 04	Ē - 0 <i>2</i>
ជ	TEMPERATURE BASEI	THE TEMPERATURE [GH NUMBER * E-8]	R + E-7 I3: 1 BASED RAYLEIG IS: 395.51E-	06.58E-03 H NUMBER IS :172.43E 04	E-02
ین	TEMPERATURE BASES	THE TEMPERATURE  [GH NUMBER + E-8]	:	H NUMBER IS :170.276 04	E - 0 2
5	99.58E-03 TEMPERATURE BASE! & UNCERTAINTY IN FLUX BASED RAYLE & UNCERTAINTY IN	THE TEMPERATURE [GH_NUMBER * E-8]	BASED RAYLEIG IS: 398.81E-	H NUMBER IS :158.90E 04	E-02
7	TEMPERATURE BASEL	THE TEMPERATURE GH NUMBER * F-8	* E-7 IS: 1 BASED RAYLEIG IS: 402.00E-	07.04E-03 H NUMBER IS :171.73E 04	E-02
8	TEMPERATURE BASEL	THE TEMPERATURE  [GH NUMBER * E-8]	! * E-7 IS: 1 BASED RAYLEIG IS: 403.56E-	09.12E-03 H NUMBER IS :168.66E 04	:-02
9	10.04E-02 TEMPERATURE BASEL % UNCERTAINTY IN FLUX BASED RAYLE! % UNCERTAINTY IN	THE TEMPERATURE	BASED RAYLEIG	H NUMBER IS :176.77E 94	[-02

# REDUCED DATA FOR INPUT POWER 0.7 W BOTTOM BOUNDARY INSULATED

THE RAN EMF DATA ARE FROM THE FILE: 08222257 THE POWER SETTING PER CHIP WAS: 0.7 WATTS

CHIP	ONET(W)	Tavg-Ts	Nu	XONC IN No.
1	TEMPERATURE BASED F	HE TEMPERATURE B 1 NUMBER * E-8 I	* E-7 IS: 261 BASED RAYLEIGH S: 304.66E-03	.03E-03 NUMBER IS :764.35E-03
2	TEMPERATURE BASED I	HE TEMPERATURE B H NUMBER ► E-8 I	* E-7 IS: 255 ASED RAYLEIGH   S: 303.54E-03	.36E-03 NUMBER IS :779.20E-03
3	TEMPERATURE BASED (	HE TEMPERATURE B H NUMBER + E-8 I	* E-7 IS: 249 BASED RAYLEIGH S: 302.04E-03	.47E-03 NUMBER IS :795.34E-00
4	TEMPERATURE BASED I	HE TEMPERATURE B H NUMBER * E-8 I	* E-7 IS: 254 ASED RAYLEIGH   5: 299.83E-03	.59E-03 NUMBER IS :781.28E-03
<u>Ē</u> ,	TEMPERATURE BASED F	HE TEMPERATURE B H NUMBER * E-8 I	* E-7 IS: 248 MASED RAYLEIGH S: 300.13E-03	.36E-03 NUMBER IS :798.47E-03
6	TEMPERATURE BASED F	HE TEMPERATURE B H NUMBER * E~8 I	* E-7 IS: 266 ASED RAYLEIGH   S: 302.30E-03	.31E-03 NUMBER IS :751.07E-03
7	TEMPERATURE BASED F	1E TEMPERATURE B 1 NUMBER + E-8 I	+ E-7 IS: 261 PASED RAYLEIGH   S: 305.62E-03	.31E-03 NUMBER IS :763.62E-03
9	TEMPERATURE BASED F	HE TEMPERATURE B H NUMBER + E-8 I	* E-7 IS: 255 ASED RAYLEIGH 1 S: 305.69E-03	.86E-03 NUMBER IS :777.86E-03
9	TEMPERATURE BASED F	HE TEMPERATURE B 1 NUMBER * E-8 I	* E-7 IS: 246 ASED RAYLEIGH ( S: 301.64E-03	.04E-03 NUMBER IS :805.10E-03

# REDUCED DATA FOR INPUT POWER 1.1 W BOTTOM BOUNDARY INSULATED

THE RAW EMF DATA ARE FROM THE FILE: U8231010 THE FOHER SETTING FER CHIP WAS: 1.1 WATTS

CHIP	ONET (N)	Tavg-Ts	tty	WONC IN No
1	TOWNCOATURE DACED	HE TEMPERATURE : H NUMBER → E-9	→ E-7 IS: 365 BASED RAYLEIGH IS: 494.53E-03	NUMBER IS :571.25E-03
2	TEMPERATURE BACER	HE TEMPERATURE : SH MUMBER * E-8	* E-7 IS: 357 BASED RAYLEIGH IS: 432.30E-00	7.49E-03 NUMBER IS :582.43E-03
3	10.81E-01 IEMPERATURE BASED % UNCERTAINTY IN TELUX BASED RAYLEIG % UNCERTAINTY IN F	RAYLEIGH NUMBER THE TEMPERATURE THE NUMBER + F-8	* E-7 IS: 347 BASED RAYLEIGH IS: 489.01E-03	7.17E-03 NUMBER IS :597.04E-03 3
4	TEMPEDATURE RACER	THE TEMPERATURE	-+ E-/ IS: 350 BASED RAYLEIGH IS: 487.09E-03	1.14E-03 NUMBER IS :578.80E-03
5	TEMPEDATURE RASED	THE TEMPERATURE	→ E-7 IS: 340 BASED RAYLEIGH IS: 486.30F-00	7.42E-03   NUMBER   IS   1596.67E-03       3
5	10.73E-01 TEMPERATURE BASED % UNCERTAINTY IN FLUX BASED RAYLET % UNCERTAINTY IN	RAYLEIGH NUMBER THE TEMPERATURE	BASED RATLEISH TS: 484 82F-0	5.45E-03   NUMBER IS :539.56E-03 
7	TEMPERATURE DACER	THE TEMPERATURE	* E-7 IS: 35  BASED RAYLEIGH   IS: 496.47E-0	7.76E303 NUMBER IS :568.68E-03 3
8	TOMORDATUDE DACED	THE TEMPERATURE	R * E-7 IS: 35 BASED RAYLEIGH TS: 495 81E-0	8.03E-03 NUMBER IS :581.69E-03
9	TEMPEDATURE DACED	THE TEMPERATURE	R * E-7 IS: 34 BASED RAYLEIGH TS: 488.34E-0	3.28E-03 NUMBER IS :602.77E-03 3

# REDUCED DATA FOR INPUT POWER 3.0 W BOTTOM BOUNDARY INSULATED

THE RAW EMF DATA ARE FROM THE FILE: 08231310 THE POWER SETTING PER CHIP WAS: 3.0 WATTS

CHIP	ONET(W)	Tavg-Ts	Niu	XUNC IN Nu
1	TEMPERATURE BASED (	HE TEMPERATURE   H NUMBER * E-8	* E-7 IS: 11: BASED RAYLEIGH IS: 177.54E-0:	0.90E-02 NUMBER IS :242.30E-03 2
2	29.77E-01 TEMPERATURE BASED I % UNCERTAINTY IN TH FLUX BASED RAYLEIGH % UNCERTAINTY IN FL	RAYLEIGH NUMBER HE TEMPERATURE I H NUMBER * E-8 :	BASED RAYLEIGH IS: 176,18E-0	8.25E-02 NUMBER IS :246.54E-03 2
3	29.72E-01 TEMPERATURE BASED F % UNCERTAINTY IN TH FLUX BASED RAYLEIGH % UNCERTAINTY IN FE	RAYLEIGH NUMBER HE TEMPERATURE I H NUMBER * E-8 1	BASED RAYLEIGH IS: 173.21E-02	2.84E-02 NUMBER IS :255.82E-03 2
4	TEMPERATURE BASED F	HE TEMPERATURE E H NUMBER * E-8 1	* E-7 IS: 10 BASED RAYLEIGH IS: 173.98F-0	7.92E-02 NUMBER IS :247.08E-03
5	TEMPERATURE BASED R	IE TEMPERATURE E ! NUMBER * E-8 I	* E-7 IS: 104 BASED RAYLEIGH IS: 172.94E-02	4.27E-02 NUMBER IS :253.28E-03
5	TEMPERATURE BASED F	IE TEMPERATURE B † NUMBER 7 F-8 I	* E-7 IS: 110 BASED RAYLEIGH IS: 175.19E-02	0.27E-02 NUMBER IS :243.29E-03
	TEMPERATURE BASED R	IE TEMPERATURE B I NUMBER * E-8 I	* E-7 IS: 112 BASED RAYLEIGH S: 178.94E-02	%.63E- <b>0</b> 2 NUMBER IS :239.64E-03
	TEMPERATURE BASED R	IE TEMPERATURE B I NUMBER * E-8 I	* E-7 IS: 109 ASED RAYLEIGH S: 177.96E-02	0.55E-02 NUMBER IS :244.43E-03 ?
	29.72E-01 TEMPERATURE BASED R % UNCERTAINTY IN TH FLUX BASED RAYLEIGH % UNCERTAINTY IN FL	AYLEIGH NUMBER BE TEMPERATURE B NUMBER * E-8 I	* E-7 IS: 104 BASED RAYLEIGH S: 174,11E-02	.65E-02 NUMBER IS :252.60E-03

# TEMPERATURE DATA FOR INPUT POWER 0.1 W CHAMBER WIDTH = 30 mm

```
RESULTS ARE STORED IN FILE: 10161810
    EXPERIMENT CARRIED OUT AT
    AMBIENT TEMP (CELSIUS) OF:
                                    24.33
                   10 C-10 C
    BATH TEMP :
    TEMPERATURE READINGS IN DEGREES CELSIUS
                                            B0110M
                                                       BACK
          CENTER
                    TUP
                          RIGHT
                                   LEFT
                                           12.616
                 12.761 12.736
                                                      15.431
                                  12.771
CHIP NO1: 12.806
    POHER (WATTS):
                      .0983
                                                      15.438
                                           12.816
CHIP NO2: 12.954 12.894 12.591
                                   12.861
                     .099
    POWER (WATTS):
                                                      15.451
CHIP NO3: 13.099 12.956 00.000
                                           13.076
                                   12.986
    POWER (WATTS):
                      .0996
CHIP NO4: 12.764 12.731 12.536 POWER (WATTS): .0990
                                                      15.441
                                           12.484
                                   12.574
                                           12.801
                                                      15.446
CHIP_NOS: 12.831 12.894
                                   12.824
                      .0993
    POWER (WATTS):
                                                      15.448
CHIP NO6: 13.019 12.914 12.979
                                           12.746
                                   11.858
                     .0995
    POWER (WATTS):
                                                      15.445
                                           12,559
CHIP NO7: 12.689 12.686 12.706
                                   12,684
                     .0992
    POWER (WATTS):
                                                      15,442
                                            12,901
                                   00.000
CHIP NO8: 13.039 12.941 12.966
    POWER (WATTS):
                     .0990
                                                      15,445
CHIP NO9: 13.256 13.114 12.834
                                   13.144
                                            13.144
                      .0992
    POWER (WATTS):
                                                         LEFT
                                                CENTER
    HEAT EXCHANGERS TEMPERATURES:
                                       RIGHT
                                                       09.937
                                               10.012
                                       09.967
         BOTTOM:
                                                       10.042
                                               00.000
                                       10.037
         TOP:
    BACK PLANE TEMPERATURES :
    1(55):
            12.656
    T(56):
             12.961
             12.709
    1(57):
    1(74):
             13.131
             13.561
    1(75):
             13.571
     1(76):
     1(77):
             13.366
    SOURCE VOLTAGE: 1.225
    VOLTAGE TO THE HEATERS :
                 .972
     CHIP #1:
                 1.027
     CHIP #2:
                 1.022
     CHIP #3:
     CHIP #4:
                 1.024
                  .968
     CHIP #5:
CHIP #6:
                 1.022
     CHIP #7:
                 1.023
     CHIP #B:
                 1.023
     CHIP #9:
                 1.023
```

# TEMPERATURE DATA FOR INPUT POWER 0.7 W CHAMBER WIDTH = 30 mm

RESULTS ARE STORED IN FILE: 1	10170950		
BATH TEMP : 10 C-10 C	24.78		,
TEMPERATURE READINGS IN DEGREE	ES CELSIV	JS DOLLON	BUCK
CEIVIER TO THE	LEFT 21.31	BOTTOM 20.01	24.28
CHIP NO1: 21.48 21.22 21.08 POWER (WATTS): .708	21.31	20,01	2 // 2
CHIP NO2: 22.18 21.50 18.45	21.41	20.88	24.34
POWER (WATTS): .712	21 50	21 00	24.44
CHIP NO3: 22.65 21.48 00.00 POWER (WATTS): .719	21.56	21.98	24.44
CHIP NO4: 21.68 21.26 20.78	21.12	20.37	24.39
POWER (WATTS): .715			0.4 .4.0
CHIP NOS: 21.93 21.19 21.53	21.74	21.48	24.42
POWER (WATTS): .718 CHIP NO6: 22.75 21.81 22.07	29.73	20.12	24.48
POWER (WATTS): .721	20110	20112	<del>-</del>
CHIP NO7: 21.14 20.83 21.34	20.95	19.34	24.44
POWER (WATTS): .719	00 00	20.87	24.43
CHIP NO8: 22.00 21.42 21.32 POWER (WATTS): .718	00.00	20.07	24.40
CHIP NO9: 22.65 20.64 18.15	22.02	21.83	24.42
POWER (WATTS): .717			
HEAT EVOLUNIOUR TEMPERATURES	ptc	UT CENTER	IFFT
HEAT EXCHANGERS TEMFERATURES:	RIG 93.9	HT CENTER 22 10.017	
BOTTOM:	RIG 03.9 09.9	22 10.017	
B0110M: 10P:	99.9	22 10.017	09.972
BOTTOM: TOP: BACK PLANE TEMPERATURES :	99.9	22 10.017	09.972
BOTTOM: TOP: BACK PLANE TEMPERATURES : T(55): 15.191	99.9	22 10.017	09.972
BOTTOM: TOP: BACK PLANE TEMPERATURES : T(55): 15.191 T(56): 15.611	99.9	22 10.017	09.972
BOTTOM: TOP: BACK PLANE TEMPERATURES : T(55): 15.191	99.9	22 10.017	09.972
BOTTOM: TOP: BACK PLANE TEMPERATURES : T(55): 15.191 T(56): 15.611 T(57): 14.265 T(74): 15.651 T(75): 16.079	99.9	22 10.017	09.972
BOTTOM: TOP: BACK PLANE TEMPERATURES : T(55): 15.191 T(56): 15.611 T(57): 14.265 T(74): 15.651 T(75): 16.079 T(76): 16.521	99.9	22 10.017	09.972
BOTTOM: TOP: BACK PLANE TEMPERATURES : T(55): 15.191 T(56): 15.611 T(57): 14.265 T(74): 15.651 T(75): 16.079	99.9	22 10.017 77 00.000	09.972
BOTTOM: TOP: BACK PLANE TEMPERATURES : T(55): 15.191 T(56): 15.611 T(57): 14.265 T(74): 15.651 T(75): 16.079 T(76): 16.521	99.9	22 10.017 77 00.000	09.972
BOTTOM: TOP: BACK PLANE TEMPERATURES : T(55): 15.191 T(56): 15.611 T(57): 14.265 T(74): 15.651 T(75): 16.079 T(76): 16.521 T(77): 15.350 SOURCE VOLTAGE: 3.288 VOLTAGE TO THE HEATERS:	99.9	22 10.017 77 00.000	09.972
BOTTOM: TOP: BACK PLANE TEMPERATURES : T(55): 15.191 T(56): 15.611 T(57): 14.265 T(74): 15.651 T(75): 16.079 T(75): 16.521 T(77): 15.350 SOURCE VOLTAGE: 3.288 VOLTAGE TO THE HEATERS : CHIP #1: 2.610	99.9	22 10.017 77 00.000	09.972
BOTTOM: TOP: BACK PLANE TEMPERATURES: T(55): 15.191 T(56): 15.611 T(57): 14.265 T(74): 15.651 T(75): 16.079 T(76): 16.521 T(77): 15.350 SOURCE VOLTAGE: 3.288 VOLTAGE TO THE HEATERS: CHIP #1: 2.610 CHIP #2: 2.756	99.9	22 10.017 77 00.000	09.972
BOTTOM: TOP: BACK PLANE TEMPERATURES: T(55): 15.191 T(56): 15.611 T(57): 14.265 T(74): 15.651 T(75): 16.079 T(76): 16.521 T(77): 15.350 SOURCE VOLTAGE: 3.288 VOLTAGE TO THE HEATERS: CHIP #1: 2.610 CHIP #2: 2.756 CHIP #3: 2.743	99.9	22 10.017 77 00.000	09.972
BOTTOM: TOP:  BACK PLANE TEMPERATURES: T(55): 15.191 T(56): 15.611 T(57): 14.265 T(74): 15.651 T(75): 16.079 T(76): 16.521 T(77): 15.350 SOURCE VOLTAGE: 3.288 VOLTAGE TO THE HEATERS: CHIP #1: 2.610 CHIP #2: 2.756 CHIP #3: 2.743 CHIP #4: 2.747	99.9	22 10.017 77 00.000	09.972
BOTTOM: TOP:  BACK PLANE TEMPERATURES: T(55): 15.191 T(56): 15.611 T(57): 14.265 T(74): 15.651 T(75): 16.079 T(76): 16.521 T(77): 15.350 SOURCE VOLTAGE: 3.288 VOLTAGE TO THE HEATERS: CHIP #1: 2.610 CHIP #2: 2.756 CHIP #3: 2.743 CHIP #4: 2.747 CHIP #5: 2.597 CHIP #6: 2.741	99.9	22 10.017 77 00.000	09.972
BOTTOM: TOP:  BACK PLANE TEMPERATURES: T(55): 15.191 T(56): 15.611 T(57): 14.265 T(74): 15.651 T(75): 16.079 T(76): 16.521 T(77): 15.350  SOURCE VOLTAGE: 3.288  VOLTAGE TO THE HEATERS: CHIP #1: 2.610 CHIP #2: 2.756 CHIP #3: 2.743 CHIP #4: 2.747 CHIP #6: 2.741 CHIP #7: 2.743	99.9	22 10.017 77 00.000	09.972
BOTTOM: TOP:  BACK PLANE TEMPERATURES: T(55): 15.191 T(56): 15.611 T(57): 14.265 T(74): 15.651 T(75): 16.079 T(76): 16.521 T(77): 15.350 SOURCE VOLTAGE: 3.288 VOLTAGE TO THE HEATERS: CHIP #1: 2.610 CHIP #2: 2.756 CHIP #3: 2.743 CHIP #4: 2.747 CHIP #5: 2.597 CHIP #6: 2.741	99.9	22 10.017 77 00.000	09.972

## TEMPERATURE DATA FOR INPUT POWER 1.1 W CHAMBER WIDTH = 30 mm

```
RESULTS ARE STORED IN FILE: 10171720
    EXPERIMENT CARRIED OUT AT
                                       25.94
    AMBIENT TEMP (CELSIUS) OF:
    BATH TEMP : 10 C-10 C
TEMPERATURE READINGS IN DEGREES CELSIUS
    BATH TEMP
           CENTER
                      TOP
                                      LEFT
                                                BOTTOM
                                                            BACK
                             RIGHT
CHIP NO1: 26.38
                                      26.17
                    25.79
                             25.94
                                               24.21
                                                            29.857
    POWER (WATIS): 1,092
CHIP NO2: 27.34 26.00
                             22.01
                                               25.62
                                                            29.96
                                      26.17
POWER (WATTS): 1.099
CHIP NO3: 27.67 25.73 00
POWER (WATTS): 1.1093
                             00.00
                                      26.08
                                               26.69
                                                            30.11
CHIP NO4: 26.74 26.07
                             25.51
                                      26.00
                                               24.85
                                                            30.02
    POWER (WATTS):
                      1.103
CHIP NO5: 29.78 25.86
                             26.40
                                      26.71
                                               26.35
                                                            30.08
POWER (WATTS): 1.107
CHIP NOG: 27.51 25.54
                             26.74
                                      25.65
                                               24.17
                                                            30.16
    POWER (WATTS): 1.113
CHIP NO7: 25.80 25.40
                                      25.63
                                               22.98
                                                            30.10
                             26.18
    POWER (WATTS): 1.109
CHIP NOB: 27.06 25.80 7 POWER (WATTS): 1.109
                             26.15
                                      00.00
                                               25.29
                                                            30.11
CHIP NO9: 27.79 24.71 2
POWER (WAITS): 1.110
                             21.36
                                      26.94
                                               26.60
                                                            30.11
    HEAT EXCHANGERS TEMPERATURES:
                                          RIGHT
                                                    CENTER
                                                             LEFT
                                                  10.015 09.987
          BOTTOM:
                                          09.924
          TOP:
                                          10.010 00.000 10.068
    BACK PLANE TEMPERATURES :
    1(55): 16.88
             17.48
    1(56):
    1(57):
             15.70
    1(74):
             17.57
             18.00
    T(75):
    T(76):
             18.49
    1(77):
            17.08
    SOURCE VOLTAGE: 4.085
   - VOLTAGE TO THE HEATERS :
    CHIP #1:
                  3.244
    CHIP #2:
                  3.424
    CHIP #3:
                  3.408
    CHIP #4:
                  3.413
    CHIP #5:
                  3.228
    CHIP #6:
                  3.406
    CHIP #7:
                  3.408
    CHIP #8:
                  3.408
    CHIP #9:
                  3.408
```

# TEMPERATURE DATA FOR INPUT POWER 1.5 W CHAMBER WIDTH = 30 mm

```
RESULTS ARE STORED IN FILE: 10181020
    EXPERIMENT CARRIED OUT AT
    AMBIENT TEMP (CELSIUS) OF:
                                      23.34
    BATH TEMP
               :
                    10 C-10 C
    TEMPERATURE READINGS IN DEGREES CELSIUS
           CENTER
                     TOP
                                              BOTTOM
                            RIGHT
                                     LEFT
                                                         BACK
CHIP NO1: 33.07
                   32.50
                                     32.72
                                              29.91
                                                      35.55
                            32.62
    POWER (WATTS):
                     1.484
                  32.62
CHIP NO2: 34.32
                            27.17
                                     32.75
                                             31.80
                                                      35.68
    POWER (WATTS):
                     1.493
CHIP NO3: 34.63 32.10 0
PONER (WATIS): 1.5077
                            00.00
                                             33.39
                                                      35.89
                                     32.62
CHIP NO4: 33.56
                   32,40
                            31,90
                                     32.49
                                             30.83
                                                      35.79
    POWER (WATTS): 1.501
CHIP NOS: 33.39
                   32.19
                                             32.64
                            32.67
                                     33,16
                                                      35.87
    POWER (WATTS): 1.506
CHIP NO6: 34.02
                  31.20
                            33.07
                                     32,41
                                             29.59
                                                      35.97
    POWER (WATTS):
                     1.513
                  30.79
CHIP NO7:
          32.02
                            32.47
                                     31.73
                                             27.98
                                                      35,89
    POWER (WATTS): 1.508
CHIP NOR: 33.89 32.28 POWER (WATTS): 1.507
                                    00,00
                            32.71
                                             31.39
                                                      35.89
                  31.22
CHIP NO9: 34.69
                            26.04
                                     33,41
                                             33.00
                                                      35.88
    POWER (WATTS):
                     1.507
    HEAT EXCHANGERS TEMPERATURES:
                                         RIGHT
                                                 CENTER
                                                           LEFT
         BOTTOM:
                                        10.027
                                                 10.098
                                                         10.073
         TOP:
                                        10.108
                                                00.000
                                                         10.126
    BACK PLANE TEMPERATURES :
    1(55):
            19.59
    T(56):
             20.25
    T(57):
             17.80
    T(74):
            21.09
            20.76
    T(75):
    T(76):
             21.47
    1(77):
            19.69
    SOURCE VOLTAGE: 4.767
    VOLTAGE TO THE HEATERS:
    CHIP #1:
                3,787
    CHIP #2:
                 3.997
    CHIP #3:
                 3.979
   CHIP #4:
CHIP #5:
CHIP #6:
                 3.983
                 3.767
                 3.975
3.979
    CHIP #7:
    CHIP #8:
                 3.979
    CHIP #9:
                 3.979
               THESE RESULTS ARE NOW STORED ON DISK 'FASTSCAN
```

FILE: 30MM10R

# TEMPERATURE DATA FOR INPUT POWER 2.5 W CHAMBER WIDTH = 30 mm

```
RESULTS ARE STORED IN FILE: 10182338
    EXPERIMENT CARRIED OUT AT
    AMBIENT TEMP (CELSIUS) OF:
                                      23.17
    BATH TEMP :
                   - 10 C
    TEMPERATURE READINGS IN DEGREES CELSIUS
                                     LEFT
           CENTER
                     TOP
                            RIGHT
                                             BOTTOM
                                                      RACK
                                     42.04
                                                      49.73
CHIP NO1: 42,47
                   41.80
                            41.39
                                             37.20
    POWER (HATTS):
                     2.461
                                                       49.93
CHJP NO2: 44.31
                   40.93
                            41.68
                                     41.68
                                              40.14
    POWER (WATTS):
                     2.475
CHIP NO3: 44.77
                  41.10
                            00.00
                                     41.43
                                              42.66
                                                      50.28
    POWER (WATTS):
                     2.4985
CHIP NO4: 42.78 40.79
POWER (WAITS): 2.485
                            40.47
                                     41.00
                                              38.73
                                                      50.08
CHIP NO5: 42.58
                  42.08
                                                      50.20
                            41.60
                                     42.36
                                              41.83
    POWER (WATTS):
                    2.494
CHIP NO6: 42.77
                  38.65
                                     41.37
                                              35.79
                                                      50.41
                            41.30
    POWER (WATTS):
                     2.507
CHIP NO7: 40.63 39.59
                                              34.17
                                                      50.25
                            41.08
                                     40.51
    POWER (WATTS):
                       2.497
CHIP NOB: 42.02 39.95 4
POWER (WATTS): 2.498
                           40.79
                                     00.00
                                              37.88
                                                      50.27
CHIP NO9: 42.77 37.10 41.32
POWER (WATTS): 2.496
                                     41.32
                                              40.60
                                                      50.24
    HEAT EXCHANGERS TEMPERATURES.
                                         RICHI
                                                  CENTER
                                                           LEFT
                                        10.020
          BOTTOM:
                                                 10.110
                                                         10.065
          TOP:
                                        09.748
                                                 00.000
                                                         10.015
    BACK PLANE TEMPERATURES
    T(55):
            21.28
             22.30
    T(56):
    1(57):
             19.47
    T(74):
             23.34
    T(75):
             22.77
             23.81
    1(76):
    T(77):
             21.70
    SOURCE VOLTAGE: 6.142
    VOLTAGE TO THE HEATERS:
    CHIP #1:
                 4,881
    CHIP #2:
                 5.152
    CHIP #3:
                 5.128
    CHIP #4:
                 5.135
    CHIP #5:
                 4.859
    CHIP #6:
                 5.124
    CHIP #7:
CHIP #8:
                 5.129
                 5.129
    CHIP #9:
                 5.129
```

### TEMPERATURE DATA FOR INPUT POWER 3.0 W CHAMBER WIDTH = 30 mm

```
RESULTS ARE STORED IN FILE: 10232224
    EXPERIMENT CARRIED OUT AT
     AMBIENT TEMP (CELSIUS) OF:
                                        22.83
    BATH TEMP
     BATH TEMP: 10 C
TEMPERATURE READINGS IN DEGREES CELSIUS
            CENTER
                              RIGHT
                                       LEFT
                                                BOTTOM
                                                          BACK
                      10P
CHIP NO1: 50.66
                                        49.97
                    49.62
                              49.07
                                                 43.61
                                                          57.87
     POWER (WATTS): 3.022
CHIP NO2: 52.71 47.72
                              49.42
                                        49.42
                                                 46.37
                                                          58.10
     POWER (WATTS): 3.038
CHIP NO3: 52.51 48.65
                                        47.22
                                                 49.87
                                                          58.53
                              00.00
    POWER (WATTS): 3.0672
CHIP NO4: 51.15 47.96 4
POWER (WATTS): 3.051
CHIP NO5: 50.48 48.36 4
POWER (WATTS): 3.053
CHIP NO6: 51.67 42.15 4
POWER (WATTS): 3.079
                                        48.79
                                                 46.00
                                                          58.30
                              48.59
                                        50.54
                                                 48.61
                                                          58.47
                              49.36
                                        47.63
                                                 46.09
                                                          58.70
                              48.38
CHIP NO7: 48.27 46.25
                                        48.07
                                                 39.78
                                                          58.52
                              48.70
     POWER (WATTS):
                       3.066
CHIP NOS: 49.10 45.58
                                        00.00
                                                 44.02
                                                          58.53
                              48.05
POWER (WATTS): 3.067
CHIP NO9: 50.71 41.39 4
                              43.01
                                        43.01
                                                 45.34
                                                          58.49
     POWER (WATTS):
                        3.064
    HEAT EXCHANGERS TEMPERATURES: RIGHT
                                                           LEFT
                                                 CENTER
                                        10.057
                                                 10.166
                                                          10.176
          BOTTOM:
           TOP:
                                        10.073 09.000
                                                         10.163
     BACK PLANE TEMPERATURES :
     I(55): 24.75
     1(56):
              26.51
              22.64
     T(57):
     T(74):
              28.00
     1(75):
              26.95
     1(76):
              28.63
     T(77):
              25.41
     SOURCE VOLTAGE: 6.807
     VOLTAGE TO THE HEATERS:
                  5.411
     CHIP #1:
     CHIP #2:
                  5.712
                  5.685
     CHIP #3:
     CHIP #4:
                  5.692
     CHIP #5:
                  5.385
     CHIP #6:
                  5.680
     CHIP #7:
                   5.685
     CHIP #8:
                   5.685
    CHIP #9:
                  5,686
```

# REDUCED DATA FOR INPUT POWER 0.1 W CHAMBER WIDTH = 30 mm

THE	RAH [m FOWER 'DISTAN	5 1 1 1 1 T.	IG: 1'F	16 ( 14   17	141112		, 14	1810
CHIP	OHE T	(11)	avā.	Īş	tut		Hu2	
A S	VERAGE INK TEM	TEMPER PERATU	RATUR JRE:	E: 12. 10.104	861			
A S	LUX BAS VERAGE INK TEM	PERAT	KATUR JRE:	(E: 12 10.104	. 925 4			
C	LUX BAS NVERAGE SINK TEM		RRHU	(E: 13	.144	32 F-9 I	9.98 S:	.31
(	LUX BAS NVERAGE SINK TEM	SED RA TEMPE	YLET( RATUI	SH NUM RE: 12	BER *	48 E-9 I	11.46 5:	.31
•	LUX BAS AVERAGE SINK TEN	SED RA TEMPE	YLET( RATUI	3H NUM RE: 12	BER * .934	82 E-9 I	10.68 S:	.31
1	TEUX BAS AVERAGE STAK TEI	SED RA TEMPE MPERAT	RATU URE:	кн пуп RE: 12 10,10	BER ₹ 1,788 4	£-3 1		• 1</td
	FLUX BAS AVERAGE SINK TE	TEMPE	RATU	RE: 12	.782	10 E-9 1	11.28 IS:	.31
	FLUX BA AVERAGE SINK TE	SED RA TEMPE	YVET RATU	GH NUM IRE: 10	IBER * 3.089	58 E-9	10.10 IS:	.31
9	FLUX BA AVERAGE SINK TE	SED RA TEMPI	TYLET FRATE	GH 11U1 1RF: 1	1868 * 3.202	,84   E-9	9.75 IS:	.31

# REDUCED DATA FOR INPUT POWER 0.7 W CHAMBER WIDTH = 30 mm

- 11	₹E 1	ՐՕՒ	IER.	SE	TI	ING	FE	: R	CH	IL.	MAS	F II. S: _ WO	- 0	. 7	И	170	1950
CHI	P	Ç	ME	1 ()	1)	Ta	۸ġ.	- ] e	:		Νι	11			Nu2		
1	AV	F, R f	1GE	TE	MPI	AYL ERA TUR	TUF	₹Е:	2	1.2	40 . R = 294	.87 ► E~	9	1 15:	9.1	2 2.	41
2	AV	F.R£	<b>IGE</b>	ΙĘ	,HPI	AYL ERA TUR	TU	₹E :	2	0.0	42. R → 990	.23 F E-	9	1 15:	19.7	'6 2.	42
3	FU	ERF	BA: AGE	SEL Te	) Ri Mel	AYL ERA TUR	E I ( Tur	3H RE :	. 2 NU	MBE 2.1	R→	. 48 I E-	9	1 IS:	18.0	)0 2.	. 48
4	AV	ERF	AGE.	16	MPI	AYL ERA TUR	TUF	RE:	2	1.2	41. R + 273	.37 • E-	ģ	1 15	19.3	2.	44
5	FLI	UX E. <b>R</b> F	BA:	SET Te	) RA MPI	AYL	E.I.( TUF	3H RE :	NUI 2	MBE 1	39. R • 83	.73   E-	9	1 15:	18.5	.9 2.	46
6	.∴∨	ERI	<b>IGE</b>	1.5	MP	AYL ERA TUR	TU	₹ :	: 2	1.8	39. R ₹ ₹78	.61   E-	9	1 15:	18.5	3 2,	. 48
7	ΑV	UX F <i>Rf</i>	BA: IGE	1 [	MP	AYL ERA TUR	101	₹E :	: 2	1.0	42. R • 966	, 38 • E-	9	15:	19.8	3 2.	45
8	FLI	ERF	BA:	SEL Te	RA MPI	AYL ERA TUR	E I ( TUF	GH RE:	1UN 2	MBE 1.E	R →	,07   E-	9	1 [5	18.7	'5 2.	46
9	AV	FRF	BA:	SEU Te	RA MPI	AYL ERA TUR	E I ( TUI	3H ₹E :	NUI S	MRE 1.2	R →	, 64 F. F	9	1 15:	19.4	18 2.	44

### REDUCED DATA FOR INPUT POWER 1.1 W CHAMBER WIDTH = 30 mm

THE RAN EMF DATA ARE FROM THE FILE: 10171720 THE POWER SETTING PER CHIP WAS: 1.1 WITHE DISTANCE TO THE FRONT WALL WAS 30 MM

CHIP ONET(N) Tava-Ts Nul Nu2

- 1 1.08 16.00 44.33 20.74 FLUX BASED RAYLEIGH NUMBER \* E-9 IS: 3.93 AVERAGE TEMPERATURE: 26.089 SINK TEMPERATURE: 10.085
- 2 1.09 15.48 46.12 21.58 FLUX BASED RAYLEIGH NUMBER \* E-9 IS: 3.94 AVERAGE TEMPERATURE: 25.562 SINK TEMPERATURE: 10.085
- 3 1.10 16.83 42.84 20.04 FLUX BASED RAYLEIGH NUMBER \* E-9 IS: 4.03 AVERAGE TEMPERATURE: 26.917 SINK TEMPERATURE: 10.085
- 4 1.09 16.05 44.67 20.90 FLUX BASED RAYLEIGH NUMBER \* E-9 IS: 3.98 AVERAGE TEMPERATURE: 26.136 SINK TEMPERATURE: 10.085
- 5 1.10 17.57 40.98 19.17 FLUX BASED RAYLEIGH NUMBER \* E-9 IS: 4.06 AVERAGE TEMPERATURE: 27.657 SINK TEMPERATURE: 10.085
- 6 1.10 16.42 44.03 20.60 FLUX BASED RAYLEJGH NUMBER \* E-9 IS: 4.03 AVERAGE TEMPERATURE: 26.509 SINK TEMPERATURE: 10.085
- 7 1.10 15.60 46.18 21.60; FLUX BASED RAYLEIGH NUMBER \* E-9 IS: 3.98 AVERAGE TEMPERATURE: 25.688 SINK TEMPERATURE: 10.085
- 8 1.10 16.43 43.88 20.53 FLUX BASED RAYLEJGH NUMBER \* E-9 IS: 4.02 AVERAGE TEMPERATURE: 25.519 SINK TEMPERATURE: 10.085
- 9 1.10 15.63 46.12 21.58 FLUX BASED RAYLEIGH NUMBER \* E-9 IS: 3.98 AVERAGE TEMPERATURE: 25.717 SINK TEMPERATURE: 10.085

### REDUCED DATA FOR INPUT POWER 1.5 W CHAMBER WIDTH = 30 mm

THE RAN Emf DATA ARE FROM THE FILE: 10211130
THE POWER SETTING PER CHIP WAS: 1.5 W
THE DISTANCE TO THE FRONT WALL WAS 30 MM

CHIP ONET(W) Tavg-Is Nul Nu2

- 1 1.52 22.39 44.65 20.89 FLUX BASED RAYLEIGH NUMBER \* E-9 IS: 5.94 AVERAGE TEMPERATURE: 32.569 SINK TEMPERATURE: 10.180
- 2 1.53 21.80 46.10 21.57 FLUX BASED RAYLEIGH NUMBER \* E-9 IS: 5.94 AVERAGE TEMPERATURE: 31.978 SINK TEMPERATURE: 10.180
- 3 1.54 24.07 42.22 19.75 FLUX BASED RAYLEIGH NUMBER \* E-9 IS: 6.15 AVERAGE TEMPERATURE: 34.252 SINK TEMPERATURE: 10.180
- 4 1.54 22.27 45.37 21.23 FLUX BASED RAYLEIGH NUMBER \* E-9 IS: 6.00 AVERAGE TEMPERATURE: 32.450 SINK TEMPERATURE: 10.180
- 5 1.54 23.39 43.35 20.28 FLUX BASED RAYLEJGH NUMBER \* E-9 IS: 6.09 AVERAGE TEMPERATURE: 33.574 SINK TEMPERATURE: 10.180
- 6 1.55 22.61 45.06 21.08 FLUX BASED RAYLEIGH NUMBER \* E-9 IS: 6.07 AVERAGE TEMPERATURE: 32.788 SINK TEMPERATURE: 10.180
- 7 1.54 21.66 46.86 21.92 FLUX BASED RAYLEIGH NUMBER \* E-9 IS: 5.99 AVERAGE TEMPERATURE: 31.837 SINK TEMPERATURE: 10.180
- 8 1.54 22.30 45.54 21.30 FLUX BASED RAYLEIGH NUMBER \* E-9 IS: 6.03 AVERAGE TEMPERATURE: 32.482 SINK TEMPERATURE: 10.180
- 9 1.54 20.60 49.26 23.05 FLUX BASED RAYLEIGH NUMBER \* E-9 IS: 5.92 AVERAGE TEMPERATURE: 30.782 SINK TEMPERATURE: 10.180

# REDUCED DATA FOR INPUT POWER 2.5 W CHAMBER WIDTH = 30 mm

THE RAN EMF DATA ARE FROM THE FILE: 10182338
THE POHER SETTING PER CHIP HAS: 2.5 H
THE DISTANCE TO THE FRONT WALL WAS 30 MM

CHIP ONET(H) Tavg-Ts Nut Nu2

- 1 2.44 31.61 51.08 23.90 FLUX BASED RAYLEIGH NUMBER \* E-9 IS: 10.54 AVERAGE TEMPERATURE: 41.698 SINK TEMPERATURE: 10.087
- 2 2.45 30.24 53.65 25.10
  FLUX BASED RAYLEJGH NUMBER \* E-9 IS: 10.44
  AVERAGE TEMPERATURE: 40.331
  SINK TEMPERATURE: 10.087
- 3 2.48 33.03 49.69 23.25 FLUX BASED RAYLEIGH NUMBER \* E-9 IS: 10.86 AVERAGE TEMPERATURE: 43.113 SINK TEMPERATURE: 10.087
- 4 2.46 31.27 52.14 24.39
  FLUX BASED RAYLEIGH NUMBER \* E-9 IS: 10.60
  AVERAGE TEMPERATURE: 41.356
  SINK TEMPERATURE: 10.087
- 5 2.47 32.19 50.86 23.79 FLUX BASED RAYLEIGH NUMBER \* E-9 IS: 10.74 AVERAGE TEMPERATURE: 42.277 SINK TEMPERATURE: 10.087
- 6 2.49 31.14 52.84 24.72 FLUX BASED RAYLEIGH NUMBER \* E-9 15: 10.68 AVERAGE TEMPERATURE: 41.225 SINK TEMPERATURE: 10.087
- 7 2.48 30.10 54.39 25.44
  FLUX BASED RAYLEIGH NUMBER \* E-9 IS: 10.52
  AVERAGE TEMPERATURE: 40.189
  SINK TEMPERATURE: 10.087
- 8 2.48 30.94 52.97 24.78 FLUX BASED RAYLEIGH NUMBER \* E-9 IS: 10.62 AVERAGE TEMPERATURE: 41.023 SINK TEMPERATURE: 10.087
- 9 2.48 28.94 56.51 26.44 FLUX BASED RAYLEIGH NUMBER \* E-9 IS: 10.39 AVERAGE TEMPERATURE: 39.028 SINK TEMPERATURE: 10.087

### REDUCED DATA FOR INPUT POWER 3.0 W CHAMBER WIDTH = 30 mm

THE RAW Emf DATA ARE FROM THE FILE: 10191310 THE POWER SETTING PER CHIP WAS: 3.0 H THE DISTANCE TO THE FROMT WALL WAS 30 MM

CHIP QNET(N) Tavg-Ts Nu1 Nu2

- 1 2.96 38.29 51.36 24.03 FLUX BASED RAYLEIGH NUMBER \* E-9 IS: 13.73 AVERAGE TEMPERATURE: 48.440 SINK TEMPERATURE: 10.154
- 2 2.98 36.50 54.14 25.33
  FLUX BASED RAYLETGH NUMBER \* E-9 IS: 13.56
  AVERAGE TEMPERATURE: 46.657
  SINK TEMPERATURE: 10.154
- 3 3.01 38.80 51.50 24.10 FLUX BASED RAYLEJGH NUMBER \* E-9 IS: 14.03 AVERAGE TEMPERATURE: 48.959 SINK TEMPERATURE: 10.154
- 4 2.99 38.03 52.27 24.46 FLUX BASED RAYLEIGH NUMBER \* E-9 IS: 13.85 AVERAGE TEMPERATURE: 48.185 SINK TEMPERATURE: 10.154
- 5 3.00 38.62 51.66 24.17 FLUX BASED RAYLEIGH NUMBER \* E-9 IS: 13.98 AVERAGE TEMPERATURE: 48.777 SINK TEMPERATURE: 10.154
- 5 3.02 36.60 54.74 25.61 FLUX BASED RAYLEIGH NUMBER \* E-9 IS: 13.76 AVERAGE TEMPERATURE: 46.755 SINK TEMPERATURE: 10.154
- 7 3.01 36.49 54.71 25.60 FLUX BASED RAYLEIGH NUMBER \* E-9 IS: 13.69 AVERAGE TEMPERATURE: 46.642 SINK TEMPERATURE: 10.154
- 8 3.01 36.62 54.55 25.52 FLUX BASED RAYLEIGH NUMBER \* E-9 IS: 13.72 AVERAGE TEMPERATURE: 46.771 SINK TEMPERATURE: 10.154
- 9 3.01 33.27 59.88 28.01 FLUX BASED RAYLEIGH NUMBER \* E-9 IS: 13.23 AVERAGE TEMPERATURE: 43.421 SINK TEMPERATURE: 10.154

### TEMPERATURE DATA FOR INPUT POWER 0.1 W CHAMBER WIDTH = 9 mm

```
RESULTS ARE STORED IN FILE: 11050029
    EXPERIMENT CARRIED OUT AT
    AMBIENT TEMP (CELSIUS) OF:
                                    22.78
    BATH TEMP : 10 C
TEMPERATURE READINGS IN DEGREES CELSIUS
          CENTER
                   10P
                          RIGHT
                                   LEFT
                                          BOTTOM
                                                   BACK
CHIP NO1: 14.34
                  14.25
                          14.16
                                   14.24
                                                   14.40
                                           14.08
    POWER (WATTS):
                     .097
CHIP NO2: 14.48
                 14.33
                           14.32
                                   14.32
                                           14.22
                                                   14.54
    POWER (WATTS):
                     .098
CHIP NO3: 14,58
                 14.53
                          14.49
                                   14.48
                                           14.54
                                                   14.64
    POWER (WATIS): .0989
CHIP NO4: 14.39 14.25
                          14.10
                                   14.12
                                           14.02
                                                   14.45
    POWER (WATTS): .099
CHIP NO5: 14.43 15.89
                          14.33
                                   14.37
                                           14.26
                                                   14.49
    POWER (WATTS): .039
CHIP NO6: 14.65 14.37
                          00.00
                                   14.24
                                           14.58
                                                   14.71
    POWER (WATTS): .099
CHIP NO7: 14.13 14.14
                          14.19
                                   14.17
                                           14.08
                                                   14.19
    POWER (WATTS): .099
CHIP NO8: 14.59 14.41
                          14.42
                                   00.00
                                           14.24
                                                   14.65
    POWER (WATTS): .099
CHIP NO9: 14.71 14.28
                          16.01
                                   16.01
                                           14.45
                                                   14.77
    POWER (WATTS):
    HEAT EXCHANGERS TEMPERATURES: RIGHT
                                           CENTER
                                                    LEFT
         BOTTOM:
                                   09.914
                                           09,967
                                                   09.965
         TOP:
                                   10.011
                                           00,000
                                                   10.392
    BACK PLANE TEMPERATURES :
           12.97
    T(55):
    1(56):
            13.12
    T(74):
            13.52
    T(75):
            13.83
    1(76):
            13.99
    T(77):
            13.25
    SOURCE VOLTAGE: 1.219
    VOLTAGE TO THE HEATERS:
    CHIP #1:
                .967
    CHIP #2:
                1.021
    CHIP #3:
                1.015
    CHIP #4:
                1.017
    CHIP #5:
                .952
    CHIP #6:
                1.015
    CHIP #7:
                1.015
    CHIP #8:
                1.015
   CHIP #9:
                1.016
```

### TEMPERATURE DATA FOR INPUT POWER 0.7 W CHAMBER WIDTH = 9 mm

```
RESULTS ARE STORED IN FILE: 11062057
    EXPERIMENT CARRIED OUT AT
                                       20.61
    AMBIENT TEMP (CELSIUS) OF:
    BATH TEMP : 10 C
    TEMPERATURE READINGS IN DEGREES CELSIUS
           CENTER
                     TOP
                             RIGHT
                                      LEFT
                                              BOTTOM
                                                        BACK
CHIP NOT: 23.48 2
POWER (WATTS):
                    23.27
                             22.85
                                      23,21
                                               21.49
                                                        23.88
                     .696
CHIP NO2: 24.85
                    23.75
                                      23.74
                                               23.07
                                                        25.26
                             23.74
    POWER (WATTS): .701
CHIP NO3: 24.78 24.57 24
POWER (WATTS): .7050
                                                        25.19
                             24.32
                                      23.70
                                               24.51
CHIP_N04: 23.92 22.97
                                      22.78
                                               21.97
                                                        24.32
                             22.82
POWER (WATTS): .703
CHIP NOS: 24.77 23.82 2
POWER (WATTS): .705
                             24.12
                                      24.42
                                               23.69
                                                        25.17
CHIP NO6: 25.92 23.76
                                      23.15
                                               25.35
                                                       26.33
                             00.00
    POWER (WATTS): .709
CHIP NO7: 23.12 22.57
                             23.13
                                      22.84
                                               21.02
                                                       23.53
    POWER (WATTS): .707
CHIP NO8: 24.84 23.90
                                      00.00
                                               22.83
                                                       25.25
    POWER (WATTS): .707
CHIP NO9: 25.78 22.75
POWER (WATTS): .706
                                      23.34
                                               24.30
                                                        25.19
                            19.26
                                               CENTER
    HEAT EXCHANGERS TEMPERATURES: RIGHT
                                                        LEFT
                                      09.972
                                               10.070
                                                        10.088
          BOTTOM:
          TOP:
                                      10,047
                                               00.000
                                                       10.137
    BACK PLANE TEMPERATURES :
    T(55):
            15.17
    1(56):
             15.45
    1(74):
             15.92
             15.99
16.29
    1(75):
    1(76):
                                                  4
    T(77):
             15.68
    SOURCE VOLTAGE: 3.259
    VOLTAGE TO THE HEATERS:
    CHIP #1:
                 2.587
    CHIP #2:
CHIP #3:
                  2.731
                  2.720
    CHIP #4:
CHIP #5:
                  2.722
                  2.575
    CHIP #6:
                  2.717
    CHIP #7:
                 2.718
    CHIP #8:
                  2.718
    CHIP #9:
                 2.720
```

## TEMPERATURE DATA FOR INPUT POWER 1.1 W CHAMBER WIDTH = 9 mm

```
RESULTS ARE STORED IN FILE: 11022255
    EXPERIMENT CARRIED OUT AT
    AMBIENT TEMP (CELSIUS) OF: BATH TEMP : 10 C
                                        21.11
    TEMPERATURE READINGS IN DEGREES CELSIUS
                                                          BACK
                                       LEFT
                                               BOTTOM
           CENTER
                       TOP
                              RIGHT
                                                          29,87
                    28.61
                                       28.57
                              28.26
                                                25.77
CHIP NOT: 28.92
POWER (WATTS): 1.0
CHIP NO2: 31.27 29.86
POWER (WATTS): 1.1
                        1.093
                                       29.60
                                                 28.52
                                                          29.97
                              29.60
                      1.100
                                                 30.37
                                                          30.08
CHIP NO3: 30.49
                   30.42
                                       28.65
                              30.02
    POWER (WATTS): 1.1071
                                                 26.78
                                                          30.04
CHIP NO4: 29.63 28.45
                                       27.89
                              28.11
    POWER (WATTS):
                    1,104
29.79
                                                          30.08
                                       30.53
                                                 29.54
CHIP NOS: 31.16 29.79
POWER (WATTS): 1.107
                              30.20
                                                          30.18
                                                 31.17
CHIP NOG: 31.91 28.89 (POWER (WAITS): 1.114
                                       28.72
                              00.00
                                                          30.15
                              28.46
CHIP NO7: 28.48 2
POWER (WAITS):
                   27.51
                                       29.34
                                                 25.07
                      1.112
CHIP NOB: 31.20 30.08 POWER (WATTS): 1.111
                                       00.00
                                                 28.01
                                                          30.14
                              30.00
                                                          30.11
                                                 30.57
CHIP NO9: 32.68 28.26
                              31.03
                                        31.03
     POWER (WATTS): 1.110
                                                           LEFT
    HEAT EXCHANGERS TEMPERATURES: RIGHT
                                                 CENTER
                                                          10.241
                                        09.839
                                                 10.128
           BOTTOM:
                                                          09,952
                                                 00.000
           TOP:
                                        09.863
     BACK PLANE TEMPERATURES : 1(55): 17.38
     1(56):
              17.58
     1(74):
              18.00
     T(75):
              18.02
     1(76):
              18.41
              17.63
     1(77):
     SOURCE VOLTAGE: 4.086
     VOLTAGE TO THE HEATERS:
     CHIP #1:
                   3.244
     CHIP #2:
                   3.425
     CHIP #3:
                   3.411
                   3.413
     CHIP #4:
     CHIP #5:
                   3.229
                   3.406
     CHIP #6:
                   3.407
     CHIP #7:
     CHIP #8:
                   3.408
                   3.409
     CHIP #9:
```

### TEMPERATURE DATA FOR INPUT POWER 1.5 W CHAMBER WIDTH = 9 mm

```
RESULTS ARE STORED IN FILE: 11091225
           EXPERIMENT CARRIED OUT AT
                                                                                                             21.83
            AMBIENT TEMP (CELSIUS) OF:
                                                          10 C
           BATH TEMP
            TEMPERATURE READINGS IN DEGREES CELSIUS
                                                                                                                                 BOTTOM
                                                                                                                                                             BACK
                                                                                                          LEFT
                               CENTER
                                                             TOP
                                                                               RIGHT
                                                                                                          36.25
                                                                                                                                                             37.56
                                                                                                                                   32.76
                                                        36.38
                                                                                 35.78
CHIP NOT: 36.71
                                                       1.489
36.79
            POWER (WATTS):
                                                                                                                                   35.88
                                                                                                                                                             39.83
CHIP NO2: 38.97 36.79
POWER (WATTS): 1.497
                                                                                                           37.06
                                                                                 37.06
                                                                                                                                   37.83
                                                                                                                                                             39.20
CHIP NO3: 38.33 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37.92 37
                                                        37.92
                                                                                 37.67
                                                                                                           34.98
                                                                                                                                   33.41
                                                                                                                                                             37.92
CHIP NO4: 37.06 35.37
                                                                                                          34.59
                                                                                 35.16
             POWER (WATTS): 1.504
CHIP NOS: 38.29 36.57
POWER (WATTS): 1.5
                                                                                                                                    36.20
                                                                                                                                                             39.16
                                                                                                           37.75
                                                                                 37.19
CHIP NO6: 39.40 35.38 (POWER (WATTEL)
                                                                                                                                                             40.27
                                                                                                                                    38.23
                                                                                 00.00
                                                                                                           34.97
POWER (WATTS): 1.516
CHIP NO7: 34.94 33.67
POWER (WATTS): 1.512
                                                                                                           34.46
                                                                                                                                    30.18
                                                                                                                                                             35.81
                                                                                 35.04
                                                                                                                                                             39.05
CHIP NO8: 38.18 35.83 CHIP NO8: 38.18 35.83 CHIP NO8: 38.18 35.83
                                                                                                                                    34.50
                                                                                  36.98
                                                                                                           00.00
                                                                                                                                    36.89
                                                                                                                                                             40.58
CHIP NO9: 39.71 34.80
                                                                                  28.60
                                                                                                            36.52
             POWER (WATTS): 1.511
            HEAT EXCHANGERS TEMPERATURES: RIGHT
                                                                                                                                    CENTER
                                                                                                                                                                LEFT
                                                                                                                                                              10.040
                                                                                                            09.828
                                                                                                                                     09.977
                             BOTTOM:
                                                                                                                                    00.000
                                                                                                                                                             10.295
                                                                                                            10.007
                             TOP:
             BACK PLANE TEMPERATURES
              1(55):
                                     20.82
              1(56):
                                       21.73
                                      22.48
              1(74):
              1(75):
                                       22.33
                                      22.64
              1(76):
              1(77):
                                      21.31
             SOURCE VOLTAGE: 4.771
              VOLTAGE TO THE HEATERS:
                                                   3.789
              CHIP #1:
              CHIP #2:
                                                   4.000
             CHIP #3:
                                                   3.983
              CHIP #4:
CHIP #5:
                                                    3.987
                                                    3.772
              CHIP #6:
                                                    3.979
                                                   3.981
              CHIP #7:
                                                    3.982
              CHIP #8:
              CHIP #9:
                                                   3.983
```

### TEMPERATURE DATA FOR INPUT POWER 2.5 W CHAMBER WIDTH = 9 mm

```
RESULTS ARE STORED IN FILE:
                                  11082020
    EXPERIMENT CARRIED OUT AT
    AMBIENT TEMP (CELSIUS) OF:
                                    21.28
    BATH TEMP
                   10 C
    TEMPERATURE READINGS IN DEGREES CELSIUS
          CENTER
                    TOP
                           RIGHT
                                   LEFT
                                           BOTTOM
                                                    BACK
CHIP NO1: 46.62
                  45.93
                           45.41
                                   46.08
                                            40.22
                                                    48.05
    POWER (WATTS):
                    2.504
CHIP NO2: 50.04 46.15
                           47.23
                                   47.23
                                            43.85
                                                    51.48
    POWER (WATTS):
                     2.520
CHIP NO3: 48.91 48.75
                          48.04
                                   45.63
                                            48.30
                                                    50.37
    POWER (WATTS):
                     2.5388
CHIP NO4: 47.00 43.52
                          44.22
                                   42.84
                                           41.35
                                                    48.45
    FOWER (WATTS):
                    2.531
CHIP NO5: 48.77
                46.61
                           47.23
                                   48.29
                                            45.89
                                                    50.23
    POWER (WATTS):
                      2.538
CHIP NO6: 49.99
                 44.34
                          00.00
                                   44.08
                                           48.13
                                                    51.45
                ): 2.552
41.13
   -POWER (WATTS):
CHIP NO7: 43.36
                           43.65
                                   42.69
                                           35.63
                                                    44.82
                    2.544
    POWER (WATTS):
CHIP NO8: 48.86
                 45,42
                           47.09
                                   00,00
                                           43.17
                                                    50.32
    POWER (WATTS):
                    2.544
CHIP NO9: 49.89 42.54
                                   45.52
                                           45.93
                                                    51.35
    POWER (WATTS):
                     2.541
   HEAT EXCHANGERS TEMPERATURES: RIGHT
                                           CENTER
                                                    LEFT
         BOTTOM:
                                   09.859
                                           10.037
                                                    10.110
         TOP:
                                   09.803
                                           00,000
                                                    10.073
    BACK PLANE TEMPERATURES
    T(55):
            22.95
            24.01
    T(56):
    T(74):
            24.80
            24.59
24.97
    T(75):
    1(76):
    T(77):
            23.67
   SOURCE VOLTAGE: 6.193
   VOLTAGE TO THE HEATERS:
   CHIP #1:
                4.921
   CHIP #2:
                5.193
   CHIP #3:
                5.172
   CHIP #4:
                5.176
   CHIP #5:
                4.897
   CHIP #6:
                5.165
   CHIP #7:
                5.169
   CHIP #8:
                5.169
   CHIP #9:
                5.171
```

### TEMPERATURE DATA FOR INPUT POWER 3.0 W CHAMBER WIDTH = 9 mm

```
RESULTS ARE STORED IN FILE:
                                    11072058
    EXPERIMENT CARRIED OUT AT
    AMBIENT TEMP (CELSIUS) OF: BATH TEMP : 10 C
                                       21.00
    TEMPERATURE READINGS IN DEGREES CELSIUS
                                              BOTTOM
                      10P
                                      LEFT
           CENTER
                                                        BACK
                             RIGHT
CHIP NO1: 55.97
                   54.45
                             55.08
                                      55.59
                                               45.61
                                                        57.66
    POWER (WATTS): 2.938
                  57.34
CHIP NO2: 61.12
                             58.19
                                      58.19
                                               54.57
                                                        62.82
    POWER (WATTS): 2.957
CHIP NO3: 58.47
                  58.54
                             57.89
                                      55.35
                                               58.30
                                                        60.18
                       2.9774
    POWER (WATTS):
CHIP NO4: 57.35 53. POWER (WATTS):
                  53.88
                                               49.46
                                                        59.05
                             54.52
                                      54.33
                       2.969
CHIP NO5: 58.98 57.68
                             58.44
                                      59.12
                                               56.79
                                                        60.69
    POWER (WATTS): 2.978
CHIP NO6: 61.17 55.49
                                               59.33
                                                        62.89
                             00.00
                                      55.89
    POWER (WATTS): 2.993
CHIP NO7: 52.97 51.59
                             53.54
                                               43.41
                                                        54.68
                                      53.26
                      2.984
    POWER (WATTS):
CHIP NO8: 60.57 57.20 59.10 POWER (WATTS): 2.985 CHIP NO9: 60.45 53.52 46.33
                                      00.00
                                               54.37
                                                        62.28
                                      56.95
                                               56.66
                                                        62.17
    POWER (WATTS):
                       2.984
    HEAT EXCHANGERS TEMPERATURES: RIGHT
                                               CENTER
                                                         LEFT
          BOTTOM:
                                      09.783
                                               10.022
                                                        10.176
          TOP:
                                      09.816
                                               00.000
                                                        10.063
    BACK PLANE TEMPERATURES 1(55): 32.35
    1(56):
              34.45
    T(74):
             35.59
    T(75):
             35.08
    1(76):
             35.20
    1(77):
             33.52
    SOURCE VOLTAGE: 6.715
    VOLTAGE TO THE HEATERS:
    CHIP #1:
CHIP #2:
CHIP #3:
                 5.339
                  5.633
                  5.611
    CHIP #4:
                  5.615
    CHIP #5:
                  5.314
    CHIP #6:
                  5.603
    CHIP #7:
                 5.608
    CHIP #8:
                  5.607
    CHIP #9:
                  5.608
```

# REDUCED DATA FOR INPUT POWER 0.1 W CHAMBER WIDTH = 9 mm

- 1	HE PI	AW Emf DHER SI ISTANCI	ETTING	PER	CHIP	WAS:	Ð	1109 .1 W 9 MM	50021
CH	IP	ONETCI	1) Ia	Ng-T	5	Nu 1		Hu2	
1	AVE	.11 K BASEI RAGE TI K TEMPI	EMPERA	ITURE	: 14.	242	9 E-9 :	7.11 IS:	.30
2	AVE	RAGE TI C TEMPE	EMPERA ERATUR	TURE E: 1	: 14. 0.139	221		7.19 IS:	
3	FLUX	.1( BASE[ RAGE TE TEMPE	EMPERA	TURE	: 14.	14.4 ER * 1 525	3 E-9 ]	6.75 (S:	.31
4	HVE	.11 BASET RAGE TE TEMPE	:MPERA	TURE	: 14.	15.5 ER * 6 208	4 E-9 1	7.27 (S:	.31
5	AVEF	.1( BASEL RAGE TE TEMPE	MPERA	TURE	: 14.	497	2 - 9 ]	.s:	.31
6	-HVt.H	.10 BASEL RAGE TE TEMPE	MERN	TURE	: 14.	14.70 ER * E 473	) E-9 I	6.88 S:	.31
7	AVER	.10 BASED RAGE TE TEMPE	MPERA	TURE	: 14.	15.86 ER * E 153	S -9 1	7.42 5:	.31
8	AVER	.10 BASED AGE TE TEMPE	MPERA	TURE	: 14.4	14.67 [R * E 471	, 9 I	6.86 S:	.31
9	HVER	.10 BASED AGE TE TEMPE	TILEKH	LOKE	: 14.1	14.00 R * E 660	9 I	6.55 S:	.31

# REDUCED DATA FOR INPUT POWER 0.7 W CHAMBER WIDTH = 9 mm

11 11	HE RA HE PU HE DI	H Em HER STAN	F DI SET ICE	ATA TINC TO T	ARE PE HE	FR R ( FR)	ROH CHIP DNT	THE MAS	FILE: : 0 : NAS	.7 I 9 MM	110 1	6205
CH1	P	OHE T	(H)	Ta	ı∧å	ĪĢ		Nu	1	1	lu2	
1	FLUX AVER SINK	AGE	TEM	PERF	HUF	₹E:	23.	174	38 E-9	16 15:	5.08	2.41
2	FLUX AVER SINK	AGE	TEM	PERF	HUL	₹ :	23.	251	42 E-9	16 IS:	5.10	2.43
3	FLUX AVER SINK	AGE	TEM	PERF	<b>YTUF</b>	₹[:	24.	456	75 E-9	15:	4.86	2.48
4	FLUX AVER SINK	AGE	TEM	PER	TUF	₹E:	23.	219	.63 E.E9	16 IS:	5.20	2.44
5	FLUX AVER SINK	AGE	TEM	PERF	TUF	₹E:	24.	451	.75 E-9	14 IS:	4.86	2.48
6	FLUX AVER SINK	BAS INGE	ED TEM	RAYL PERI	TEJO TUTE	3H ∃ ₹E :	NUMB 24.	ER + 794	20 E-9	15:	4.60	2.50
7	FLUX AVER SINK	AGE	TEM	PERA	TUF	RE:	22.	933	62 FE-9	16 IS:	6. <b>6</b> 6	2.44
8	FLUX AVER SINK	RAGE	TEM	PERA	4 I UI	₹Ε:	24.	313	16 E-9	15:	5.04	2.48
9	AVER	BNS	ED TEM	RAYL PERI	_E J (	GH RE:	NUMB 23.	ER + 266	.64   E-9	19:	6.21	2.45

### REDUCED DATA FOR INPUT POWER 1.1 W CHAMBER WIDTH = 9 mm

- THE RAW Emf DATA ARE FROM THE FILE: 11022255
  THE POWER SETTING PER CHIP WAS: 1.1 W
  THE DISTANCE TO THE FRONT WALL WAS 9 MM

  CHIP OMET(W) Tavg Ts Nut Nu2
- 1 1.08 18.18 38.87 18.19 FLUX BASED RAYLEIGH NUMBER \* E-9 IS: 4.02 AVERAGE TEMPERATURE: 28.377 SINK TEMPERATURE: 10.193
- 2 1.08 18.53 38.19 17.87
  FLUX BASED RAYLEIGH NUMBER \* E-9 IS: 4.07
  AVERAGE TEMPERATURE: 28.825
  SINK TEMPERATURE: 10.193
- 3 1.09 19.71 36.38 17.02 FLUX BASED RAYLEIGH NUMBER \* E-9 IS: 4.14 AVERAGE TEMPERATURE: 29.838 SINK TEMPERATURE: 10.193
- 4 1.09 18.29 39.06 18.28 FEUX BASED RAYLEIGH NUMBER \* E-9 IS: 4.07 AVERAGE TEMPERATURE: 28.480 SINK TEMPERATURE: 10.193
- 5 1.09 20.35 35.26 16.49 FLUX BASED RAYLEIGH NUMBER \* E-9 IS: 4.17 AVERAGE TEMPERATURE: 30.538 SINK TEMPERATURE: 10.193
- 5 1.10 20.24 35.66 16.68
  FLUX BASED RAYLEIGH NUMBER \* E-9 IS: 4.19
  AVERAGE TEMPERATURE: 30.429
  SINK TEMPERATURE: 10.193
- 7 1.10 17.88 40.23 18.82
  FLUX BASED RAYLEIGH NUMBER \* E-9 IS: 4.08
  AVERAGE TEMPERATURE: 28.076 \$
  SINK TEMPERATURE: 10.193
- B 1.10 20.13 35.76 16.73
  FLUX BASED RAYLEIGH NUMBER \* E-9 IS: 4.18
  AVERAGE TEMPERATURE: 30.321
  SINK TEMPERATURE: 10.193
- 9 1.09 19.19 37.43 17.51 FLUX BASED RAYLEIGH NUMBER \* E-9 IS: 4.13 AVERAGE TEMPERATURE: 23.382 SINK TEMPERATURE: 10.193

### REDUCED DATA FOR INPUT POWER 1.5 W CHAMBER WIDTH = 9 mm

- THE RAW Emf DATA ARE FROM THE FILE: 11091225
  THE POWER SETTING PER CHIP WAS: 1.5 W
  THE DISTANCE TO THE FRONT WALL WAS 9 MM
- CHIP ONET(W) Taya-Is Not 11/12
- 1 1.47 25.92 37.30 17.45 FLUX BASED RAYLEIGH NUMBER \* E-9 IS: 5.96 AVERAGE TEMPERATURE: 36.108 SINK TEMPERATURE: 10.186
- 2 1.47 25.87 37.60 17.59 FLUX BASED RAYLEIGH NUMBER \* E-9 IS: 6.00 AVERAGE TEMPERATURE: 36.053 SINK TEMPERATURE: 10.186
- 3 1.49 27.17 36.12 16.90 FLUX BASED RAYLEJGH NUMBER \* E-9 IS: 6.13 AVERAGE TEMPERATURE: 37.353 SINK TEMPERATURE: 10.186
- 4 1.48 25.44 38.39 17.96 FLUX BASED RAYLEIGH NUMBER \* E-9 IS: 5.99 AVERAGE TEMPERATURE: 35.625 SINK TEMPERATURE: 10.186
- 5 1.49 27.48 35.69 16.70 FLUX BASED RAYLEIGH NUMBER \* E-9 IS: 6.15 AVERAGE TEMPERATURE: 37.664 SINK TEMPERATURE: 10.186
- 6 1.49 27.26 36.16 16.32 FLUX BASED RAYLEIGH NUMBER \* E-9 IS: 6.17 AVERAGE TEMPERATURE: 37.450 SINK TEMPERATURE: 10.186
- 7 1.49 24.25 40.46 18.93
  FLUX BASED RAYLEIGH NUMBER \* E-9 IS: 5.95
  AVERAGE TEMPERATURE: 34.440
  SINK TEMPERATURE: 10.186
- 8 1.49 27.02 36.36 17.01 FLUX BASED RAYLEIGH NUMBER \* E-9 IS: 6.13 AVERAGE TEMPERATURE: 37.211 SINK TEMPERATURE: 10.186
- 9 1.49 25.41 38.61 18.07 FLUX BASED RAYLEIGH NUMBER \* E-9 IS: 6.02 AVERAGE TEMPERATURE: 35.532 SINK TEMPERATURE: 10.186

### REDUCED DATA FOR INPUT POWER 2.5 W CHAMBER WIDTH = 9 mm

THE RAN Emf DATA ARE FROM THE FILE: 11082020 THE POWER SETTING PER CHIP WAS: 2.5 WITHE DISTANCE TO THE FRONT WALL WAS 9 MM CHIP ONEI(W) Tavg-Is Nu1 Nu2 2.47 35.42 46.27 21.65 FLUX BASED RAYLEIGH NUMBER \* E-9 IS: 11.15 AVERAGE TEMPERATURE: 45,692 SINK TEMPERATURE: 10.271 2.49 35.23 46.82 21.90 FLUX BASED RAYLEIGH NUMBER \* E-9 IS: 11.20 AVERAGE TEMPERATURE: 45,503 SINK TEMPERATURE: 10.271 2.50 37.54 44.23 FLUX BASED RAYLEIGH NUMBER \* E-9 IS: 11.58 AVERAGE TEMPERATURE: 47.908 SINK TEMPERATURE: 10.271 34.33 48.22 2.50 FLUX BASED RAYLEIGH NUMBER \* E-9 IS: 11.14 AVERAGE TEMPERATURE: 44.605 SINK TEMPERATURE: 10.271 2.50 37.68 44.17 FLUX BASED RAYLEIGH NUMBER \* E-9 IS: 11.58 AVERAGE TEMPERATURE: 47.946 SINK TEMPERATURE: 10,271 2.52 37.02 45.18 FLUX BASED RAYLEIGH NUMBER \* E-9 IS: 11.56 AVERAGE TEMPERATURE: 47.287 SINK TEMPERATURE: 10.271 32.27 51.53 2.51 24.11 FLUX BASED RAYLEIGH NUMBER \* E-9 IS: 10.96 AVERAGE TEMPERATURE: 42.536

FLUX BASED RAYLEIGH NUMBER \* E-9 IS: 11.53 AVERAGE TEMPERATURE: 47.355

44.97

37.08

SINK TEMPERATURE: 10.271

SINK TEMPERATURE: 10.271

2.51

### REDUCED DATA FOR INPUT POWER 3.0 W CHAMBER WIDTH = 9 mm

THE RAW Emf DATA ARE FROM THE FILE: 11072058
THE POWER SETTING PER CHIP WAS: 3.0 W
THE DISTANCE TO THE FRONT WALL WAS 9 MM

CHIP QNET(W) Tavg-Ts Nut Nu2

- 1 2.90 44.40 43.64 20.42 FLUX BASED RAYLEIGH NUMBER \* E-9 IS: 14.41 AVERAGE TEMPERATURE: 54.762 SINK TEMPERATURE: 10.362
- 2 2.92 46.34 42.14 19.72 FLUX BASED RAYLEIGH NUMBER \* E-9 IS: 14.79 AVERAGE TEMPERATURE: 56.697 SINK TEMPERATURE: 10.362
- 3 2.94 47.28 41.61 19.47
  FLUX BASED RAYLEIGH NUMBER \* E-9 IS: 15.04
  AVERAGE TEMPERATURE: 57.639
  SINK TEMPERATURE: 10.362
- 4 2.93 44.68 43.84 20.51 FLUX BASED RAYLEIGH NUMBER \* E-9 IS: 14.61 AVERAGE TEMPERATURE: 55.040 SINK TEMPERATURE: 10.362
- 5 2.94 48.33 40.74 19.06 FLUX BASED RAYLEIGH NUMBER \* E-9 IS: 15.20 AVERAGE TEMPERATURE: 58.691 SINK TEMPERATURE: 10.362
- 6 2.96 48.31 40.97 19.17 FLUX BASED RAYLEIGH NUMBER \* E-9 IS: 15.28 AVERAGE TEMPERATURE: 58.676 SINK TEMPERATURE: 10.362
- 7 2.95 42.01 46.78 21.89 FLUX BASED RAYLEIGH NUMBER \* E-9 IS: 14.29 AVERAGE TEMPERATURE: 52.372 SINK TEMPERATURE: 10.362
- B 2.95 48.82 40.44 18.92 FLUX BASED RAYLEIGH NUMBER \* E-9 IS: 15.31 AVERAGE TEMPERATURE: 59.183 SINK TEMPERATURE: 10.362
- 9 2.95 44.89 43.86 20.52 FLUX BASED RAYLETGH NUMBER \* E-9 IS: 14.71 AVERAGE TEMPERATURE: 55.253 SINK TEMPERATURE: 10.362

#### APPENDIX D

#### SOFTWARE LISTING

```
! PROGRAM CalcDiel
1.11
            ! EDITED BY LT E. TORRES. FROM URIGINALS OF
 30
            ! PAMUK [REF.12] AND BENEDICT [REF. 13]
 31
 411
           ! THIS PROGRAM ANALYSES THE DATA READ FROM • ! A DATA FILE DESIGNATED BY THE OPERATOR.IT•! REDUCES THE DATA TO CALCULATIONS OF MET • ! POWER. PAYLETCH NUMBER AND MUSELT NUMBER.•
 50
 70
 200
 26
           VARIABLE: USED ARE:
! EMF : VOLTAGE FROM THE THERMOLOUPLES.
! POWER : POWER DISTIPATED BY THE MEATER
9E
            ! T(I) : TEMPERATURE CONVERTED FROM THERMOCOU
97
                             PLES VOLTAGE.
98
49
           ! TAVG : IS THE AVERAGE TEMPERATURE OF THE CHIP. IT IS OBTAINED MULTIPLYING THE TEMPERATURE FOUND IN EACH FAIL BY THE AREA AND DIVIDING BY THE IC-
 1(1)
101
           THE MEEN HAD STYLDING SO ON THE AREA.

TO SHIP BACK SURFACE TEMPERATURE.

THIM: FILM TEMPERATURE OF THE FOLIS.

ONET: ELECTRIC POWER MINUS CONDUCTOR

TISINK: AVERAGE OF THE 6 THERMOODIS.
102
194
1115
1 HE.
197
                           THE UPPER AND LONER HEAT EXC
           ! NUT : VERTICAL LENGTH BASED NUSSELT
! NUZ : AREA-PERIMETER BASED NUSSELT WHITE
! OTHER VARIABLES ARE SELF EXPLANATOR ES.
100
1.111
                                                                            анны ,
111
117
114
115
           50M /Co/ DI71
115
1.10
           DIM Ent(76), Power(3), I(76), Tava(3), Is ()
1.30
           Olm Trilm(3), Onet(3), H(3), P(9), Rho(3), p.
140
           DIM M(9). Ng(9), Ra(9), Delt(9), Alta(9), f (0)
:51
           DIM Gr(9), Beta(9), Doow(9), Dts(9), Rp(6)
150
           CORRELATION FACTORS TO CONVERT Ent IT 3 STATES CELSIUS. DATA 0.10086091.25707.9.-767045.0.73025 5 5044 -9247486589.6.38611.-2.56610.3.246 DATA 2.50.2.06.2.00.2.08.2.50.2.00.2.0
120
100
199
1 11
=\frac{\bar{n}_{11}}{n}
           GEAD DIEL
214
229
250
270
230
230
230
           READ ROLL
           PRINTER IS TOT
           BEEF
           BEEP
200
           THE UT "ENTER THE MAME OF THE FILE . AINING DATA". Oldfiles
391
 (19
          PRINT USING "10X.""THE RAW Em+ DARA RE FROM THE FILE: "", 10A":01d+:1e3
317
           IMPUT "ENTER THE POWER SETTING ". P. 915
3.50
```

```
PRINT HISTING "9X."" THE POWER SETTING PER CHIP WAS: "".THA":Power=
240
34 i
34 j
       PRINT USING "TOX, ""THE DISTANCE TO THE FRONT WALL WAS 3 MM """
344
150
270
280
        PRINT
        BEEF
        BEER
ASSIGN @File TO Oldfile$
990
400
401
        ENTER @File:Emt(+)
410
420
        1 CONVERT Emf TO DEGREES CELSING ...
436
4.34
4...
4411
        FOR I=0 TO 60
45.11
        Super
        FOR 3=0 TO 7
JHU
479
        Sum = Sum + D(J) + Emf(I)^{-}J
480
        MEKT J
4911
        T(I)=Sum
500
        HEXT I
502
5113
        FOR I=71 TO 76
        Sum=U
        FOR J=4 10 7
5.(14
        Fum=Sum+D(J)+Em+(()))
NEXT J
ĒĠE
500
        T(I)=Sum
MEXT I
509
10-30-100
11-30-100
11-30-100
        ! CONVERT Emf TO POWER . .
        1=1
540
        Volt=Emf(51)
ēc a
        FOR 1-62 TO 70
550
        Power(J)=Enf(I)+(Volt-Enf(I)) (Ro+I-52)
534
         10 .41
5 an
5 a :
        MEKT I
dan.
42.11
        I AREA OF THE BLOCK FACES +
1.1
-, 1 _
- 19
6 (b)
       Alenei, 905-4
Alenei, 445-4
Ariget, 445-4
بالمدت
유통하
        Atob=4.3E-5
550
570
571
        460+=4.3E-5
        Atot=5.76E-4
530
        !CALCULATE THE AVERAGE TEMPERATURES OF THE BLOCK FACES * !IF A THERMOCOUPLE IS FOUND OPENED.IT SHOULD BE TAKEN OFF.*
630
531
790
701
519
        Tavg(I)=(T(0))*Acen+I(1)*Atop+I(2)*Arig+T(3)*Alet+I(4)*Abot1/Atot
Tavg(2)=(T(6)*Acen+I(7)*Atop+I(8)*Arig+I(9)*Ale***(18)*Abot1/Atot
 729
```

```
Tavg(4) = (I(18) * Acen * I(19) * Atop * I(20) * Arig * I(21) * Alef * I(22) * Abo* I/Ato*
Tavg(5) = (I(24) * Acen * I(25) * Atop * I(26) * Arig * I(27) * Alef * I(29) * Abo* I/Ato*
Tavg(6) = (I(30) * Acen * I(31) * Atop * I(33) * Alef * I(23) * Abo* I/(Ator * Alef * I(20) * Acen * I(27) * Atop * I(28) * Arig * I(29) * Alef * I(40) * Abo* I/Atop * I(20) * Alef * I(40) * Abo* I/Atop * I(20) * Alef * I(40) * Abo* I/Atop * I(20) * Alef * I(40) * Alef
  740
750
   250
770
  780
790
                     [avg(8)=([142]*Acen+[(43)*Atop+[(44)*Arig+[(45)*Abot)/(Atot-Alet)
                     Tava(9)=(T(48)*Acen+T(49)*Atop+T(50)*Arig+T(51)*Alef+T(52)*Abot1/Atot
  800
  850
                     ! RESISTANCE OF PLEXIGLASS. FOUND WITH A CONDUCTIVITY OF + 1 0.195 H/m.K AND A LENGTH OF 19.5 MM.
 852
853
  960
                    Rc=520.83
  330
  331
  330
                     ! CHIP BACK SURFACE TEMPERATURES +
  391
  900
                     15111-7/51
                    Te(2)=[(1))
Te(2)=[(1))
  211
  920
  230
                   fa(4)=1(2);
fa(5)=1(29)
 940
                   Is(5)=1(35)
I=(7)=1(41)
 350
  96n
  470
                    Is(3)=1(47)
                    Ts(9)=[153)
 980
 3.40
                    [sium=0
 1000
                   FOR J=1 TO 9
 10:0
                  Tseum=Tesum+Te(J)
NEXT J
 1020
 1970
 11)40)
                   Tsavg=Tssum/9
 1041
 t UE it
 1060
                   ! CONDUCTION LOSS CALCULATION. *
 1961
 1062
                  010==3=:T(17)=T(75))/Rc
 1070
                   Dloss5=(1(29)-1(55))/Rc
 1030
 thận:
                  Oloss/-(1(41)-1(54))/Rc
 1300
                  010ss=(010ss3+010ss5+010ss7)/3
 1110
 1:19
 1130
                   * AVERAGE SINK TEMPERATURE CALCULATION .
 · • `
1.11
                  <sup>†</sup>T:OK=(1(52)+1(53,+1(53)+1(60)+1(†(1+1(72))/6
· • 50

· • 52

· • 53
                  TWO CHARACTERISTIC CEUGTHOLWILL BE USED TOCALCULATE NURSELT HUMPERS: 1 L1 BASED IN THE VERTICAL DIMENSION OF THE CHIE 124.MM
1 AND L2 BASED IN THE RUMATION OF THE AREASDIVIDED BY THE FERIMETER.
 : : € 4
 1155
1160
                [1+3,405+3
[2+(2,46,424,750,)+2,4(8,46,728,1+8,424,754,14,091
1151
1170
1171
1173
                  ! *****************
                  ! TO PRINT THE OUTPUT HEADINGS. *
1174
1175
1175
tigó PRINT USING "9X.""CHIP QNET(W) Tavg-Ts
                                                                                                                                                         ¹lu l
                                                                                                                                                                                            Nu2
                                                                                                                                                                                                                 "".1BA"
12HB PRINT
1310
```

```
1220
1230
1221
1240
       ! CALCULATION OF NET POWER, No AND Ra. >
      FOR J=1 TO 3
1250
1260
       ! CALCULATION OF Unet
1270
1290
      Unet(J)=Power(J)-Qloss
1300
       ! CALCULATION OF Tfilm
1310
       Tfilm(J)=(Tavg(J)+Tsink)/2
1330
1340
       ! CALCULATION OF A DELTA TEMPERATURE
1350
      Delt(J)=Tavg(J)-Tsink
1370
1080
       ! CALCULATION OF CONVECTION COEFFICIENT
1290
      H(J)=Qnet(J)/(Atot+Delt(J))
1410
1420
       ! CALCULATION OF FC-75 THERMAL CONDUCTIVITY.
14311
      K(J) = (.65-7.89474E-4+Tf_1Im(J))/10
1440
1450
       ! CALCULATION OF FC-75 DENSITY
1460
      Rho(J)=(1.825-.00246*Tfilm(J))*1000
1470
      ! CALCULATION OF FC-75 SPECIFIC HEAT Cp(J)=(.241111+3.7037E-4*I+11m(J))*4130
1480
1490
1500
       ! CALCULATION OF FC-75 VISCOSITY
1510
1520 N(J)=1,4074-
1679E-9+Tfilm(J)'4
      4(J)=1.4074-2.964E-2*Tf_11m(J)+3.8018E-4*Tf_11m(J)+2-2.7308E-6*J+_1im(J)+3+8.
1500 N(J)=N(J)+1.E-6
1540
       ! CALCULATION OF THE COEFFICIENT OF THERMAL
1550
1551
       ! EXPANSION (BETA)
1560
      Beta(J)=.00246/(1.825-.00246+Ifilm(J))
15.70
1580
      ! CALCULATION OF ALPHA
1590
      Alfa(J)=K(J)/(Rho(J)*Cp(J))
1500
1510
       ! CALCULATION OF PRANDIL NUMBER.
1620
      Pr(J)=N(J)/Alfa(J)
1630
1640
       ! CALCULATION OF NUSSELT NUMBERS
1650
      Nu1(J)=H(J)+L1/K(J)
1551
      Nu2(J)=H(J)+L2/K(J)
1670
1710
       ! CALCULATION OF GRASHOF NUMBER.
1720
      Gr(J)=9.81*Beta(J)*(L1:3)*De[+(J)/H(J):2
1700
1750
       ! CALCULATION OF RAYLEIGH NUMBER.
1760
      Ra(J) = Gr(J) + Pr(J) + 1.5 - 7
1780
1774
       ! CALCULATION OF FLUX BASED RAYLEIGH NUMBER
1810
      Raf(J)=((3.81*Beta(J)*L1*4*Onet(J))/(K(J)*N(J)*Al+a(J)*Ato+i)+1.E-3
1830
1370
1880
      PRINT USING "10X.D.1X.5($X.DD.DD.)":J.Qnet(J).Delt(J).Nu1(J).Nu2(J)
1890
      PRINT USING "12X.""FLUX BASED RAYLEIGH NUMBER + E-9 IS: 4".DDD.DD":Raf()
PRINT USING "12X.""AVERAGE TEMPERATURE:"".DDD.DDD":Tavg(J)
PRINT USING "12X.""SINK TEMPERATURE:"".DDD.DDD":Tsink
1900
1940
```

t

1950 NEXT J 1970 ASSIGN ⊕File TO ► 1980 END

```
10
         ! PROGRAM FASTSCAN +
         PROGRAM TO SCAN THE THREE UPPERMOST THERMOCOUPLES.
! IT SCANS 3 CHANNELS FOR TEMPERATURE VARIATION MEASUREMENTS.
! CHANNELS ARE 13,31 AND 49
 30
40
41
51)
50
70
         Ipass *599
         Pass=1)
         N = \Omega
30
         DIM T1(599), V1(2), Y1(599)
         DIM 12(599). V2(2). Y2(599)
DIM 12(599). V3(2). Y2(599)
31
82
         CLEAR 701
CLEAR 722
90
100
101
         ! THE THREE FILE NAMES THAT ARE REDUIRED FOLLOWING ! ARE TO STORE THE READINGS FROM THREE THERMOCOUPLES.
102
405
104
196
         BEEP
107
         PRINTER IS 701
108
         BEEP
        INPUT "ENTER THE FIRST FILE NAME: ".Newtile13
INPUT "ENTER THE SECOND FILE NAME: ".Newfile28
INPUT "ENTER THE THIRD FILE NAME: ".Newfile38
INPUT "ENTER THE VOLTMETER READING: ".VT
PRINT USING "15X."" RESULTS ARE STORED ON DISK FASTSCAN" "".10A"
109
110
112
114
         PRINT
115
         PRINT USING "25%.""FILE: "".10A": Newfile1s
         PRINT
         PRINT USING "25X, ""FILE: "". 10A": Newfile2$
118
119
         PRINT
120
121
123
         PRINT USING "25X.""FILE: "".10A":Newfile3$
         PRINT
WAIT :
124
125
131
131
         BEEP
         OUTPUT 709: "AE!"
         WAIT I
         BEEF
120
         OUTPUT 722: "T4 FT R1 P0 Z0 15TT 501 15TN"
141
4)
144
         ! LOOP NUMBER ONE ...
145
         45
         1 START SCANNING CHANNEL # 13 +
147
         OHTPHT 709: "AF13 AL13"
150
TŘÍ
         OUTPUT 709: "AS
176
         BEEb
1 7 E,
         Timedatel=TIMEDATE
        FOR Jy=0 TO Ipass
OUTPUT 722:"T3"
130
200
210
230
250
         ENTER 722:V1(+)
         71(Pass)=91(1)
        Pass=Pass+1
25)
250
251
         11=11+1
         NEXT Ut
         Timedate2=TIMEDATE
253
         即は目的ないのをときもpegate2-Timedate1
```

l

```
Pass≈‼
        ! LOOP NUMBER TWO
        ! START SCANNING CHANNEL 31 ...
       OUTPUT 709: "AF31 AL31"
OUTPUT 709: "AS"
       BEEP
       BEEP
       FOR Jj=0 TO 1pass
OUTPUT 722:"T3"
ENTER 722:V2(+)
282
283
284
284
285
        T2(Pass)=V2(1)
       Pass≈Pass+;
NEXT U:
       OUTPUT 732: "AC31"
Passell
       ! LOOP NUMBER THREE
       ! START SCANNING CHANNEL 49 *
197
298
299
       OUTPUT 709: "AF49 AL49"
       OUTPUT 709: "AS"
       BEEP
300
       BEEF
30 i
       BEEP
       FOR J<sub>J</sub>=0 TO [pass OUTPUT 722:"13" ENTER 722:V3(+)
302
303
304
305
305
307
       T3(Pass)=V3(1)
       Pass=Pass+1
NEXT Jr
308
309
310
       ! END LOOPS
311
       PRINT USING "15X.""THE TOTAL TIME ELAPSED (SECONDS):"".2X.(DHD.DD)":To+al
time1
212
213
214
       PRINT USING "15%.""THE TOTAL NUMBER OF SCANS : "".2%. 0000.0.2%:"!N
عَ إِنَّ وَ
       PRINT USING "IFX.""THE VOLTMETER READING : 1",194.1:93
115
       PRINTER (C 1
-13
       I TRANSFER FIRST SCAN DATA
       ! TRANSFERING THE SCAN DATA FROM CHANNEL 13
! TO THE FILE. THIS FILE WILL BE USED . WITH
! THE PROGRAM "PLOT". TO MAKE A PLOT OF TEM-
1 PERATURE VS TIME.
       CREATE BOAT Newfile15.20 ASSIGN OFFILE TO Newfile15
       OUTPUT @File:T1(*)
       FOR Isel TO Ipass
       Tt([i])=.10086091+25727.9*Tt([i])-767345.8*Tt([i])*C+78002556+Ft([i])*3
```

)

```
340
       NEXT IL
341
        ! TRANSFER SECOND SCAN DATA
342
344
        TRANSFERING DATA FROM CHANNEL 31*
345
346
        110 THE FILE
347
349
        CREATE BDAT Newfile23,20
        ASSIGN File TO Newfile25
OUTPUT File:T2(+)
FOR I:=0 TO Ipass
350
351
352
353
        T2(11)=.10086091+25727.9+T2(11)-767345.8+T2(11)*2+78002556+T2(11)*3...
3507 35
3507 35
3507 350
        MEXT II
        ! TRANSFER THIRD SCAN DATA ......
35.4
350
        ! TRANSFERING DATA FROM CHANNEL 31 + 1 TO THE FILE.
351
363
364
365
        -----
        CREATE BDAT Newfile35.20
ASSIGN *File TO Newfile35
OUTPUT *File:T3(*)
FOR I:=0 TO Ipass
355
367
        T3(II)=.10086091+25727.9*F3(I<sub>1</sub>)-767345.9*T3(I<sub>1</sub>)*2+78002556+F3(I<sub>1</sub>)*3
NEXT I<sub>1</sub>
STOP
358
 363
290
        END
400
```

```
11
     ! FILE NAME: PLOT
211
ăń
5.0
       ! THIS PROGRAM PLOTS THE DATA ACQUIRED BY
\frac{50}{20}
       ! PROGRAM "FASTSCAN".
30
        PRINTER IS 705
90
        BEEP
100
        Kwru=0
110
        Xmax = 200
120
130
        BEEP
        INPUT "ENTER MINIMUM AND MAXIMUM Y-VALUES". Ymin. Ymax
140
        BEEP
15.1
         Katep≂ 10
150
        BEEP
4.79
         Yatep=.2
130
        BEEP
        PRINT "IN:SP1:IP 2000.2000.8000.7000:"
PRINT "SC 0.100.0.100:TE 2.0:"
1.40
290
210
        5fx=100/(Xmax-Xmin)
220
230
        Sfy=100/(Ymax-Ymin)
PRINT "PU 0.0 PD"
240
250
250
270
        FOR Xa=Xmin TO Xmax STEP Xstep X=(Xa-Xmin)+Sfx
        PRINT "PA": X.".0: XT:"
        NEXT Xa
290
290
        PRINT "PA 100.0:PU:"
PRINT "PU PA U.O PD"
300
        FOR Ya=Ymin TO Ymax STEP Yster
        Y=(Ya-/min)+Sfy
PRINT "PA U.":Y."YT"
310
320
        NEXT Ya
PRINT 'PA 0.100 TL 0 2"
330
3411
 250
         FOR Xa=Xmin TO Xmax STEP Xstep
360
        %=(Xa-:(min)+Sfx
PRINT "PA";X.".100; XT"
 370
        NEXT Xa
PRINT "PA 100,100 PU PA 100,0 PD"
380
290
400
         FOR Ya=Ymin TO Ymax STEP Ystep
419
         Y = (Y_3 - Y_{min}) + Sfy
         PRINT "PD PA 100.".Y."YT"
4211
        HEXT Ya
PRINT "PA 100.100 PU"
PRINT "PA 0.-2 SR 1.5.2"
FOR Ka=(min JO Kmax STEP Xstep
4 11
440
45.11
46il
470
         X=(Xa-Xmin)*Six
        PRINT "PA":X.".0:"
PRINT "CP -2.-1:LB":Xa:""
450
444
        MEXT (a
PRINT "PU PA 0.0"
300
510
520
530
        FOR fa=fmin TO fmax STEP Ystep
         IF ABS(Ya)/1.E-5 THEN Ya=0
540
         Y=(Ya-Ymin)+Sfy
PRINT "PA 0.":Y.""
550
         PRINT "CP -5, -. 25:LB": Ya: ""
560
570
         NEXT Ya
53ñ
53ñ
         BEEP
         141=0
ទីពិប៉
         IF Idl=0 THEN
```

```
529
630
          (label%="Time (sec)"
          Ylabel5="Temperature (C)"
540
         PRINT "SR 1.5.2:PU PA 50.-10 UP":-LENCKlame151/2:"0:LB"::Xlame15:""
550
650
         PRINT "PA ~11.50 CP 0.":-LEN(Ylabel%)/2+5/6:"DI 0.1:LB":Ylabel%:""
END IF
570
680
         PRINT "CP 0.6"
630
         BEEP
700
         INPUT "ENTER THE NAME OF THE DATA FILE". 0 + 11es
710
720
         ASSIGN @File TO D_file$
730
740
750
750
         Md=n
         BEEP
         Noairs=600
         BEED
720
230
         PRINTER 15 1
         5ym=1
790
         PRINTER IS 705
ŝūù
         PRINT "PU DI"
810
         IF Sym=1 THEM PRINT "SM."
         IF Sym=1 THEN PRINT "SM+"
IF Sym=3 THEN PRINT "SMO"
IF Md 1 THEN
829
830
240
950
         FOR I=1 TO (Md-1)
350
         ENTER OF ile: Xa. Ya
370
         NEXT I
         END IF
330
         FOR %a=0 10 199 STEP .3338393
399
ាម
         ENTER MFile: Ya
310
         Ya=.10086031+25727.3+fa-767345.3+Ya:2+78002556+Ya:2
920
330
         X=(Xa-Xmin)*Sfx
         Y=17a-Ymin)+Sfy
         IF Symp3 THEN PRINT "SM"
IF Symp4 THEN PRINT "SR 1.4.2.4"
940
<u>450</u>
       PRINT "PA".X.Y."PD"

IF Sym2? THEN PRINT "SR 1.2.1.5"

IF Sym=4 THEN PRINT "UC2.4.39.0.-8.-4.0.0.5.4.0.:"

IF Sym=5 THEN PRINT "UC3.0.39.-7.-6.-2.5.2.5.3.-6:"

IF Sym=6 THEN PRINT "UC0.5.3.29.3.-8.-5.0.2.2:"

IF Sym=7 THEN PRINT "UC0.-5.3.39.-3.8 5.0.-7.-9:"

NEMT Ma
PRINT "BUJ"

REFE
960
         PRINT "PA" .X.Y. "PD"
970
986
390
1000
1910
1020
1021
        BÉÉP
HSSIGN PFile TO +
1030
1340
1050
        END
```

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